

FIG. 1

135
XG

FIG. 2(a)

FIG. 2(b)

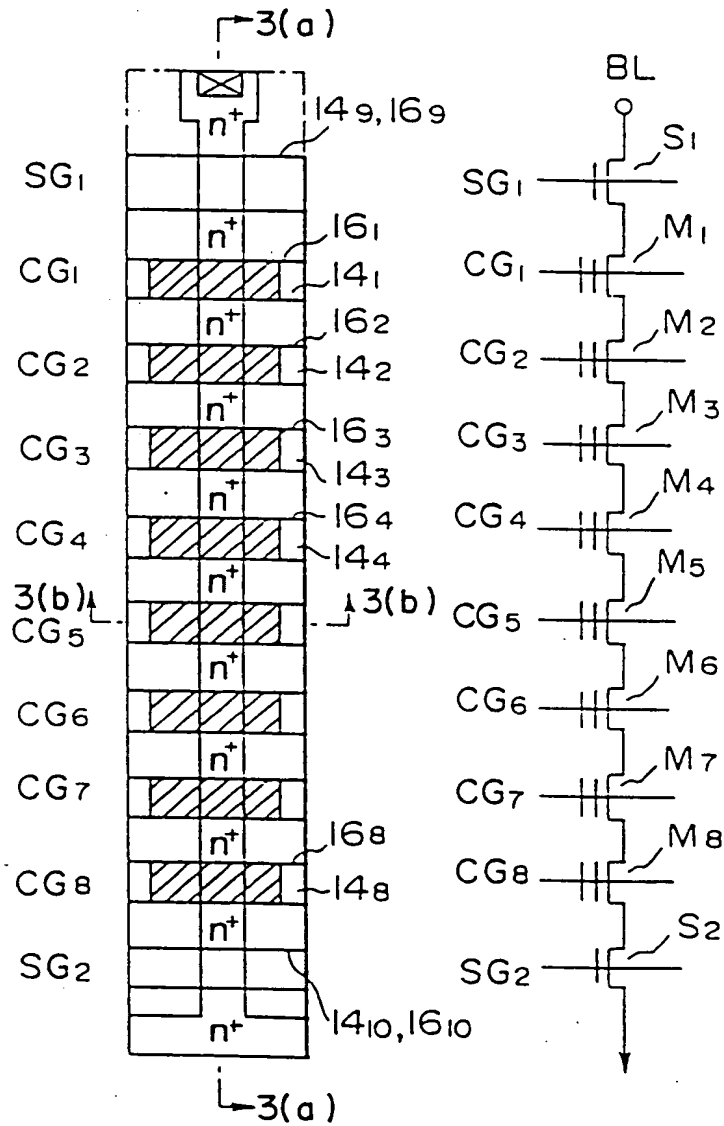


FIG. 3(a)

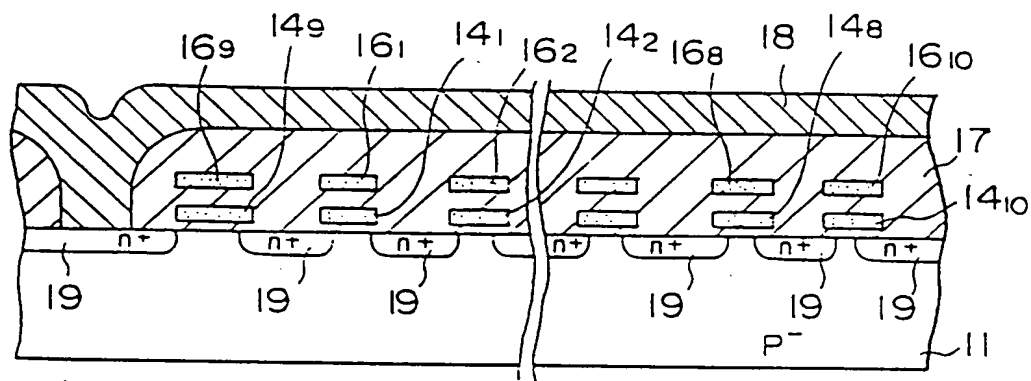
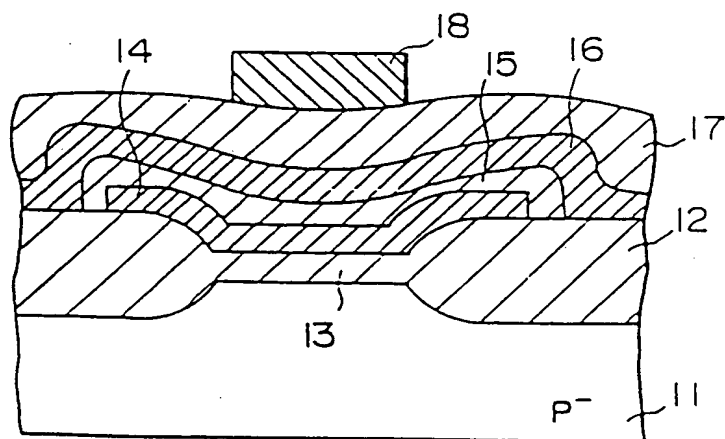


FIG. 3(b)



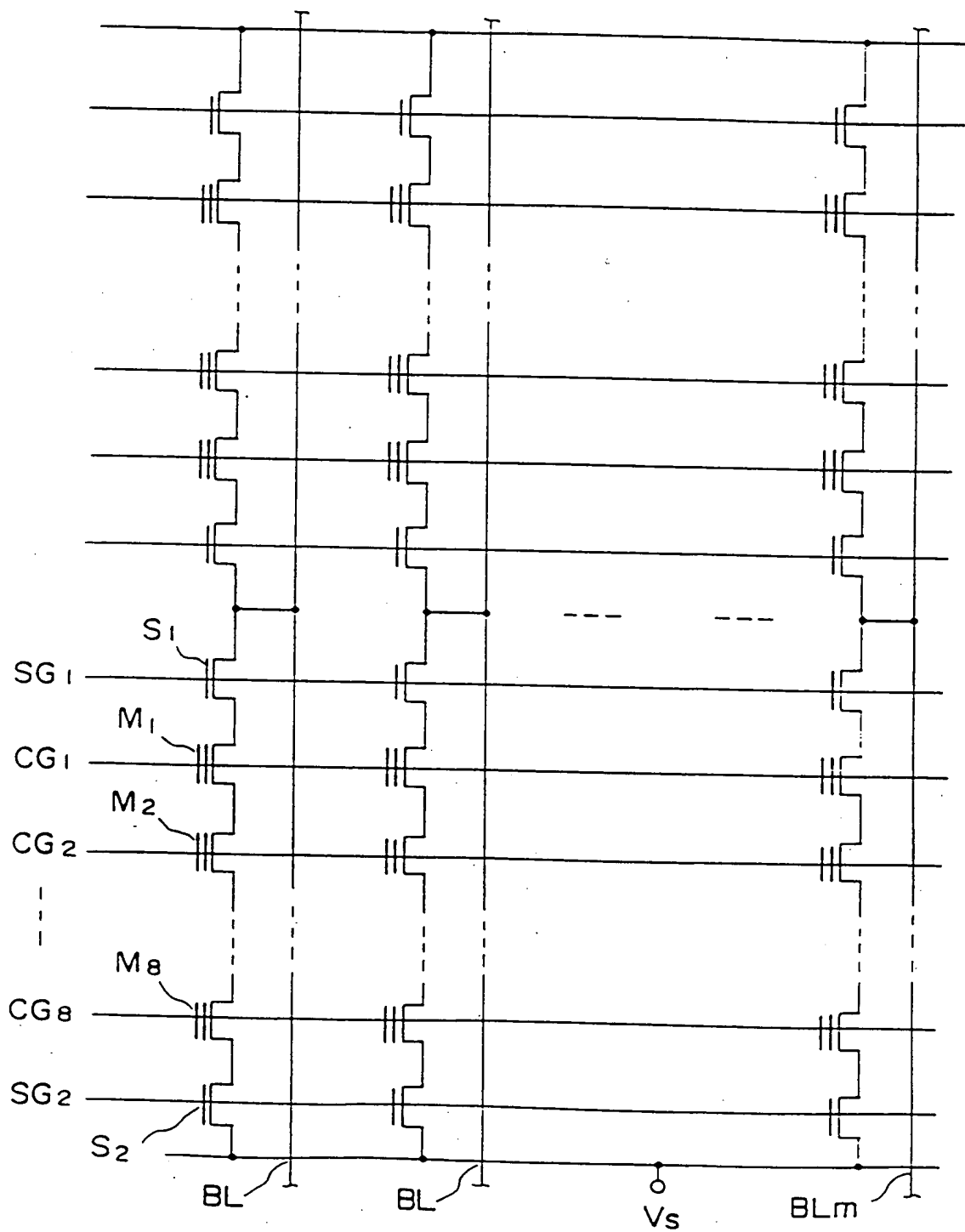


FIG. 4

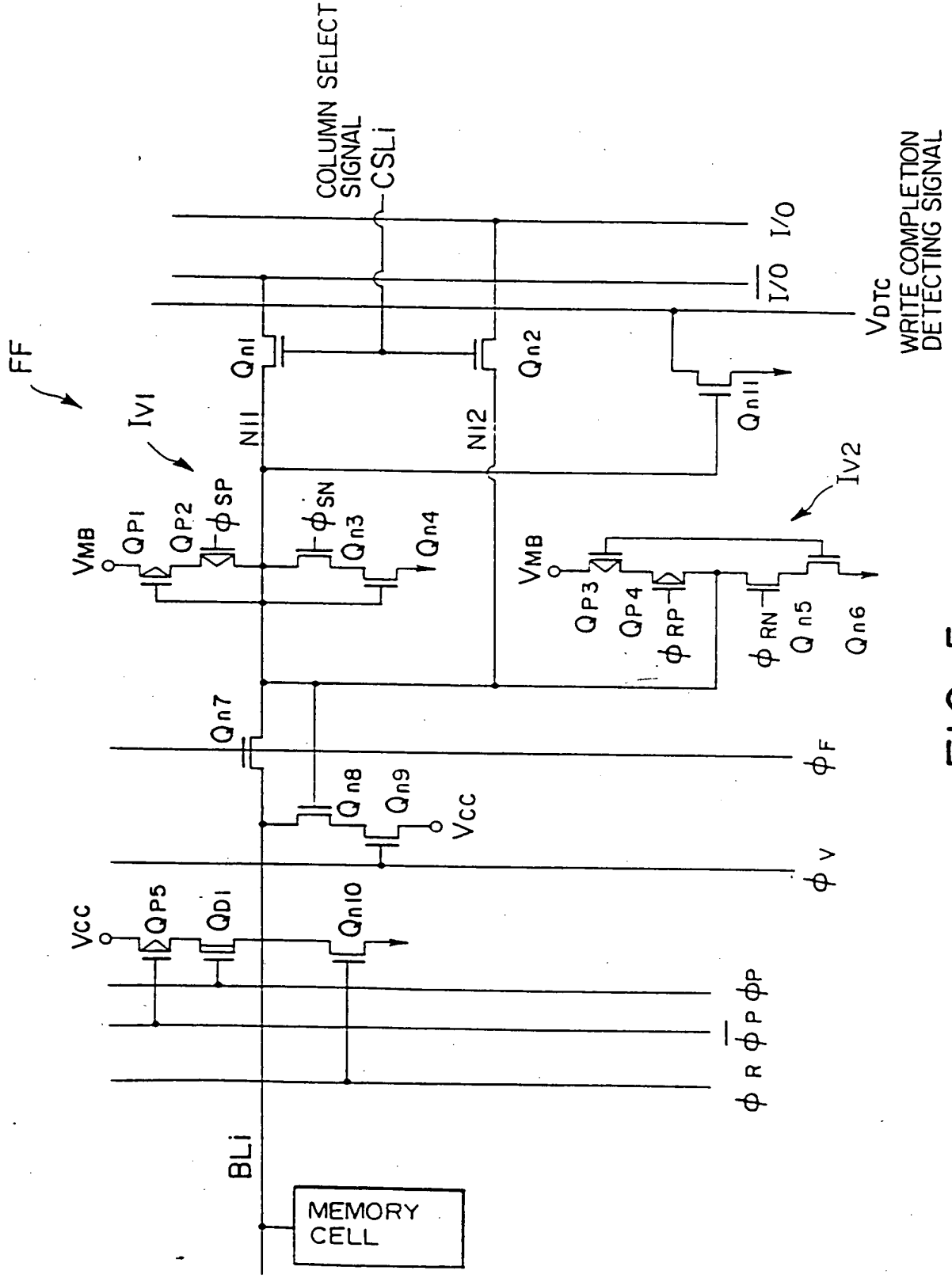


FIG. 5

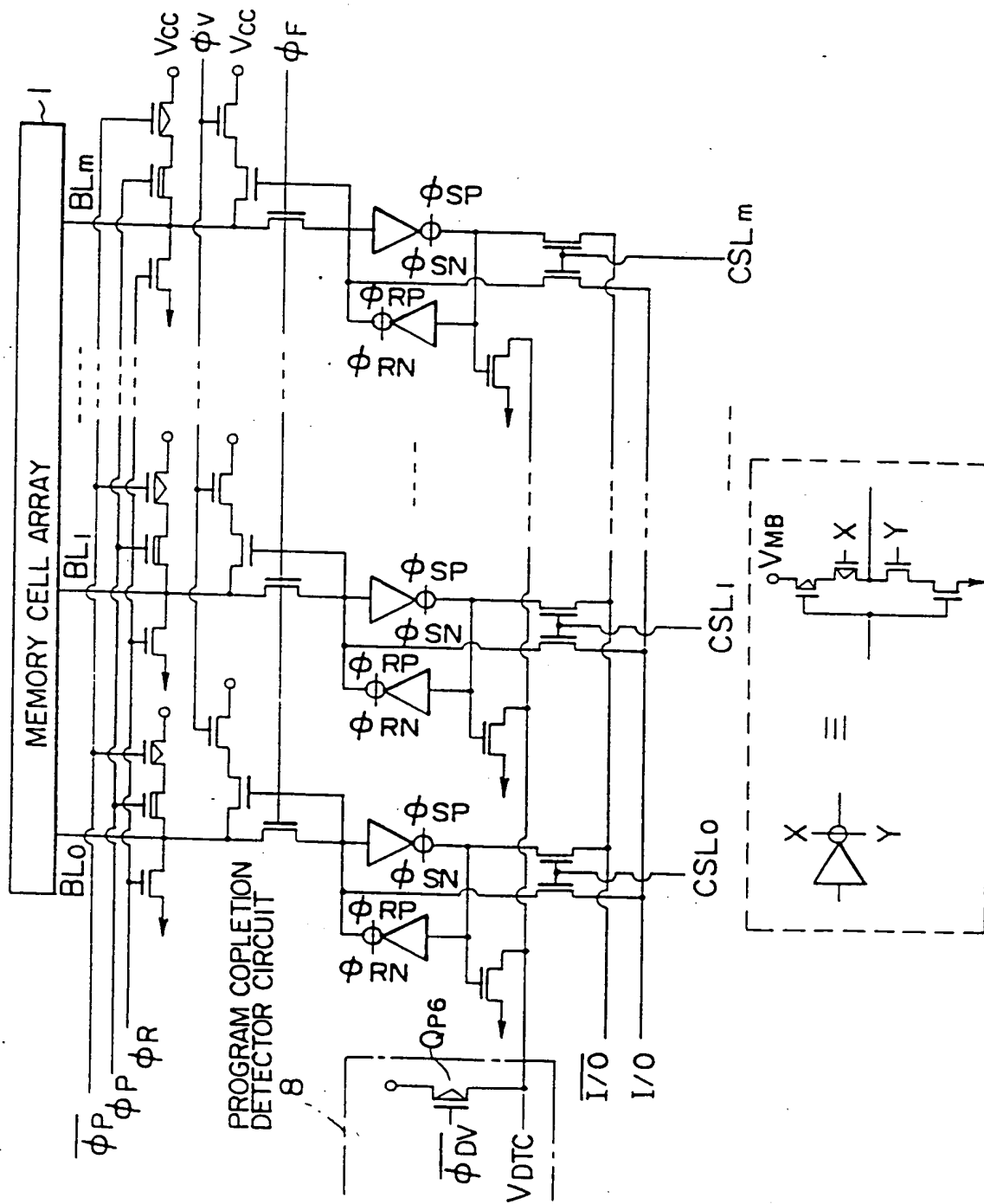


FIG. 6

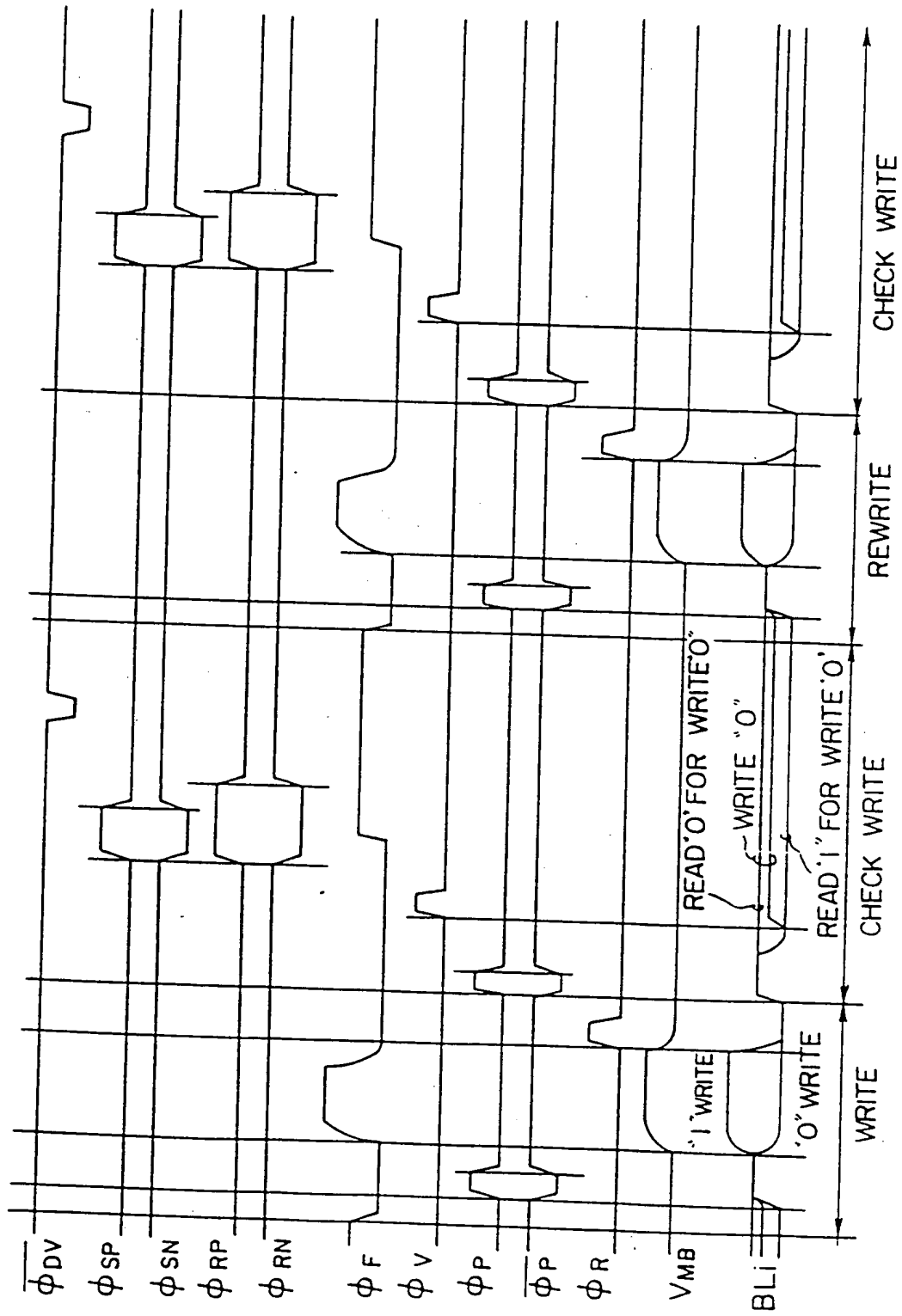


FIG. 7

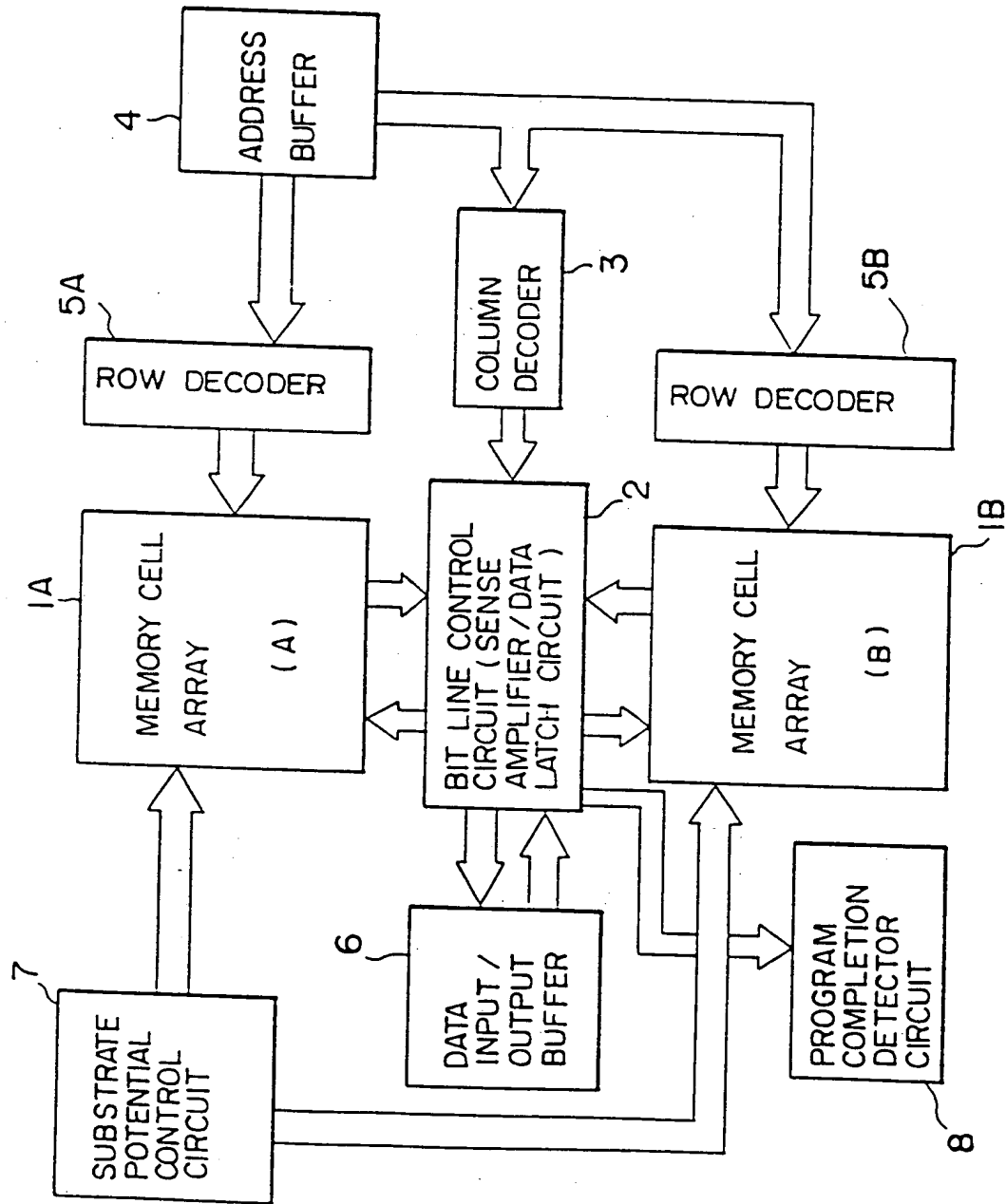


FIG. 8

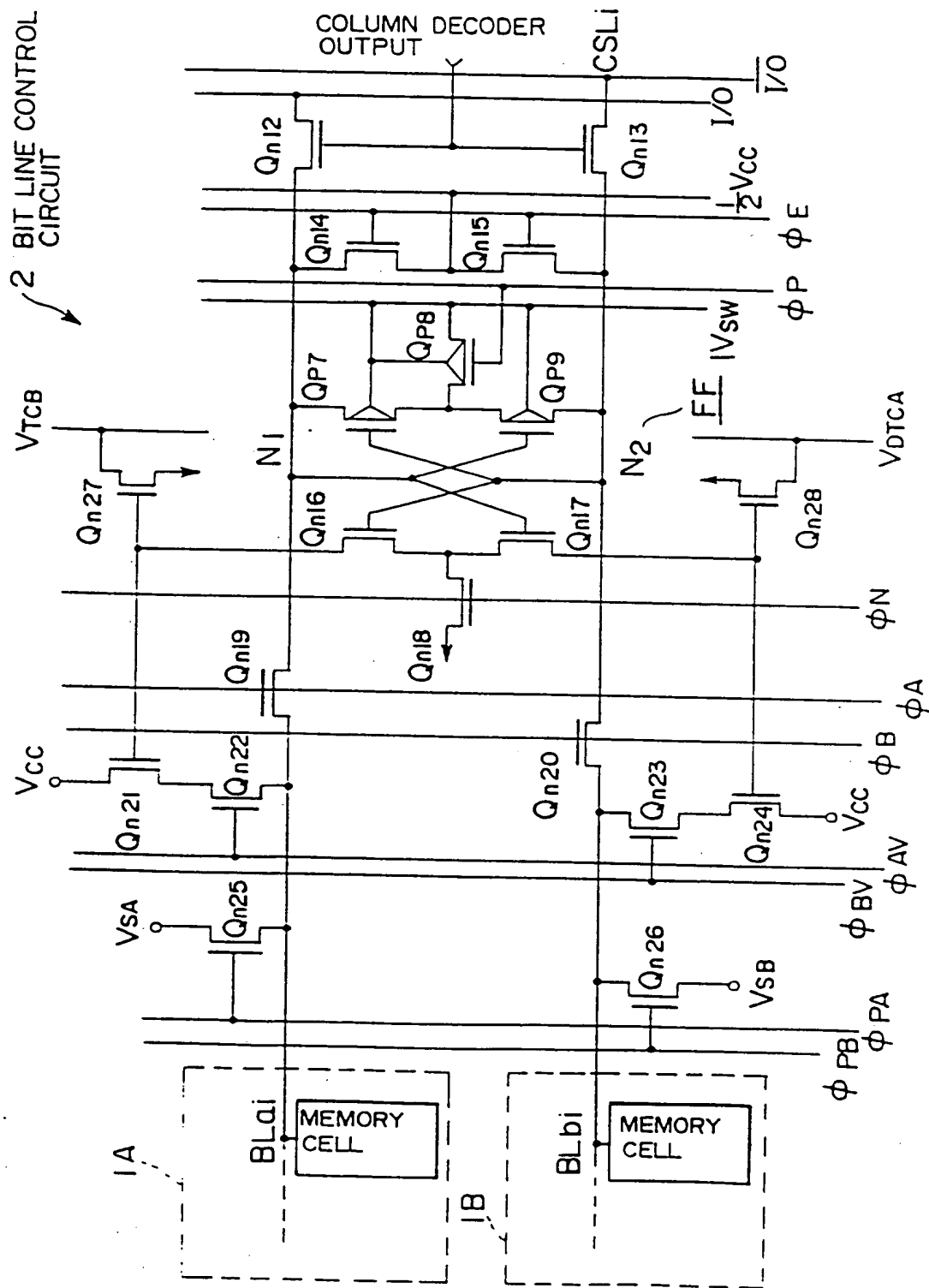


FIG. 9

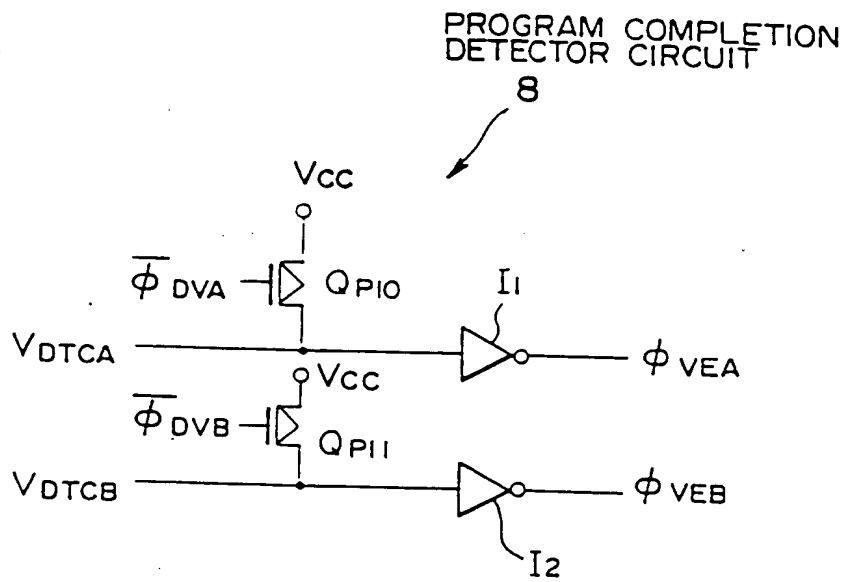


FIG.10

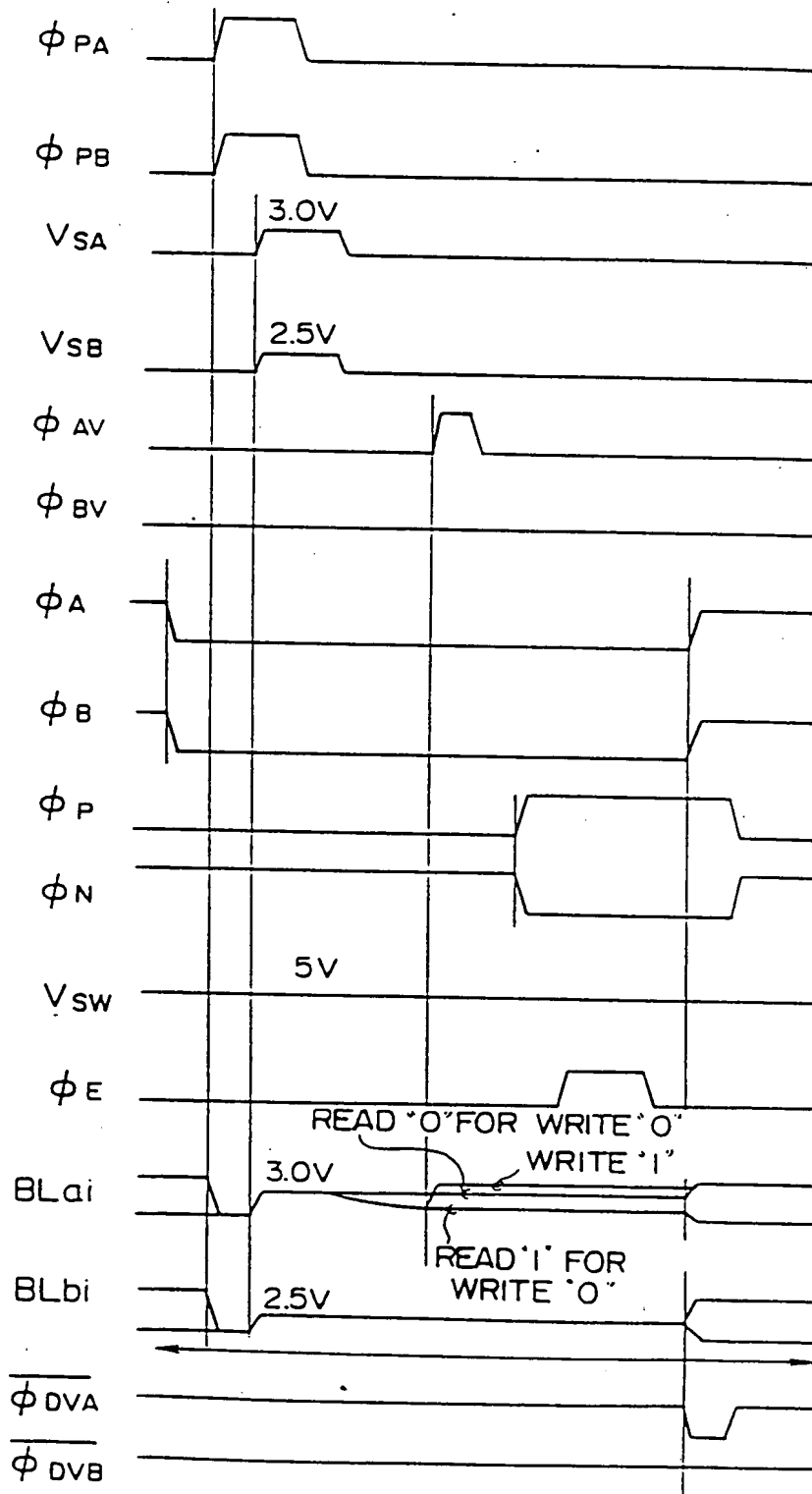


FIG.11

FIG. 12(a)

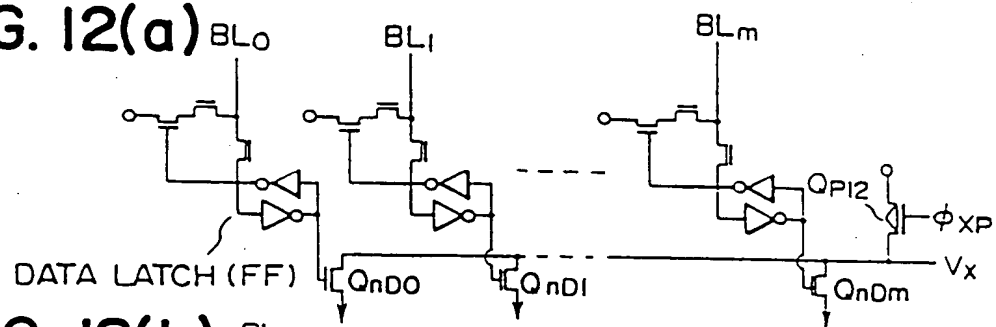


FIG. 12(b)

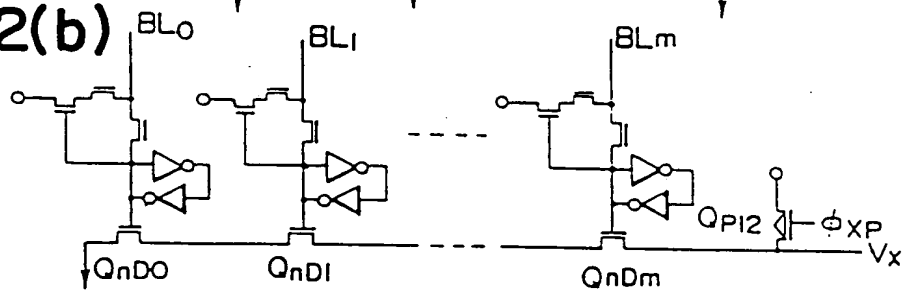


FIG. 12(c)

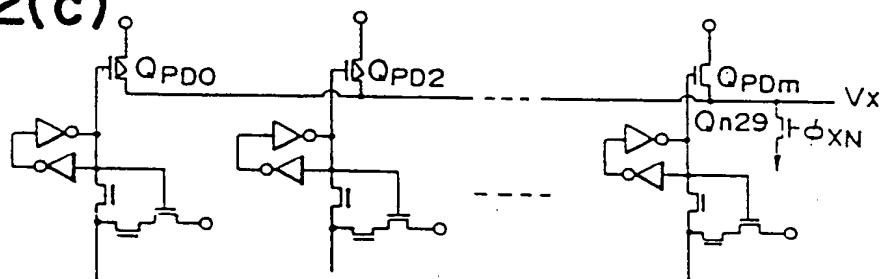


FIG. 12(d)

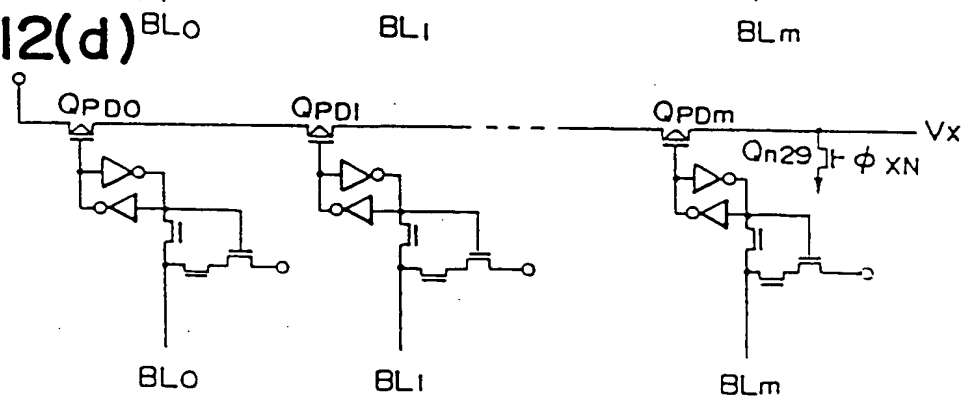


FIG. 13(a)

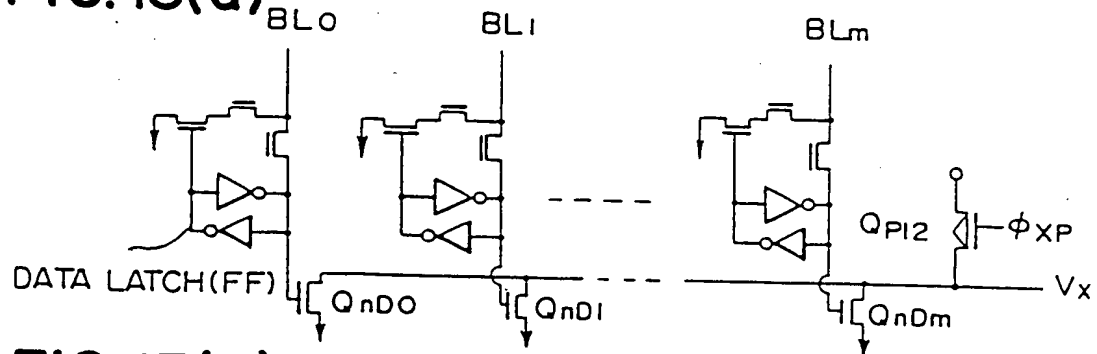


FIG. 13(b)

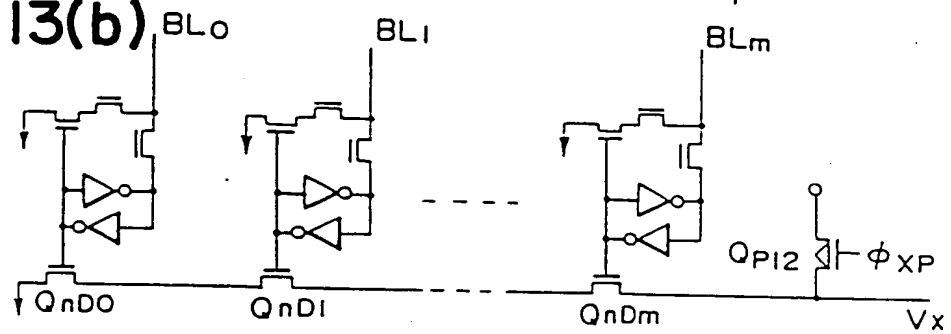


FIG. 13(c)

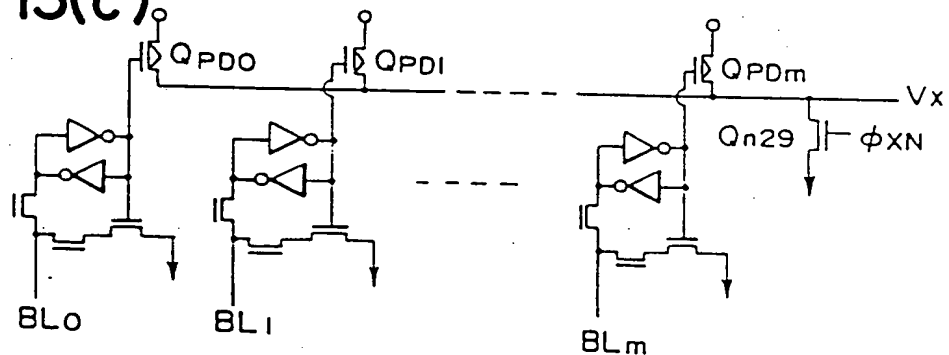
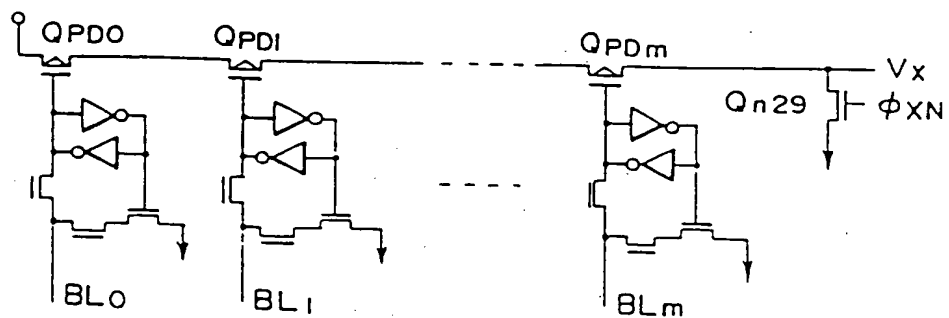


FIG. 13(d)



The diagram illustrates a 1T1R1C1 memory cell array. It features two columns of memory cells. Each cell is composed of a 1T1R1C1 structure. The top part of the cell is a 1T1R1C1 structure with a word line (WL) and a bit line (BL). The bottom part is a 1T1R1C1 structure with a word line (WL) and a bit line (BL). The diagram includes various control lines: PRE, PRECL, WL8, Vss, PRV, BLCD, DR, ERV, TVE, LVE, and VERT. The memory cell array is labeled 'MEMORY CELL BLOCK MCB'.

FIG. 14

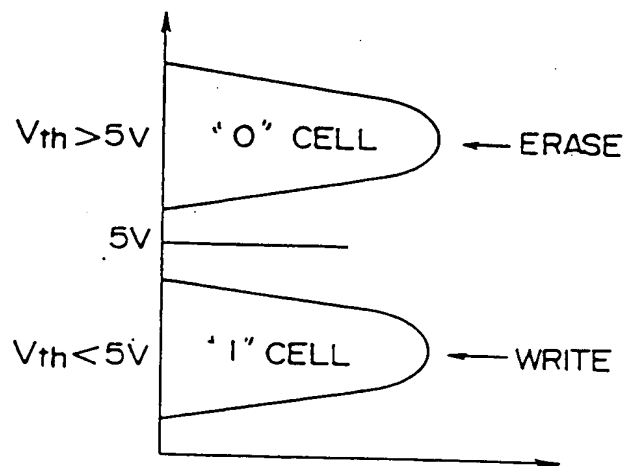


FIG. 15

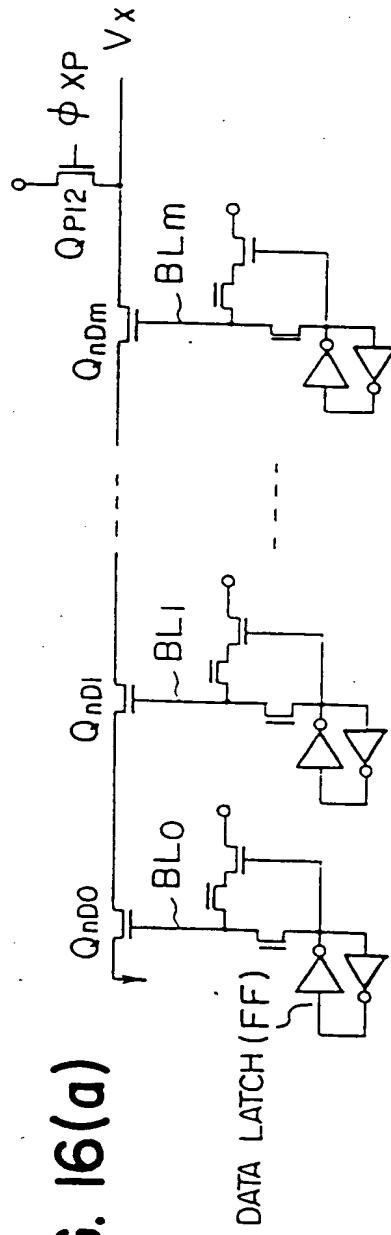


FIG. 16(a)

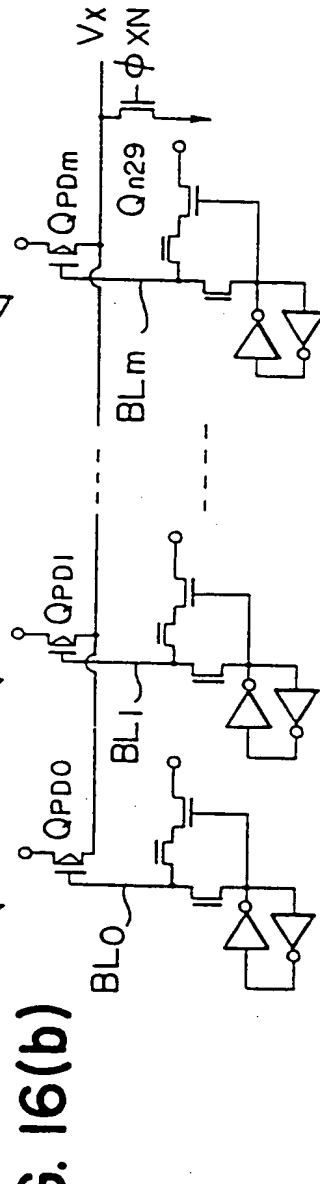


FIG. 16(b)

FIG. 17(a)

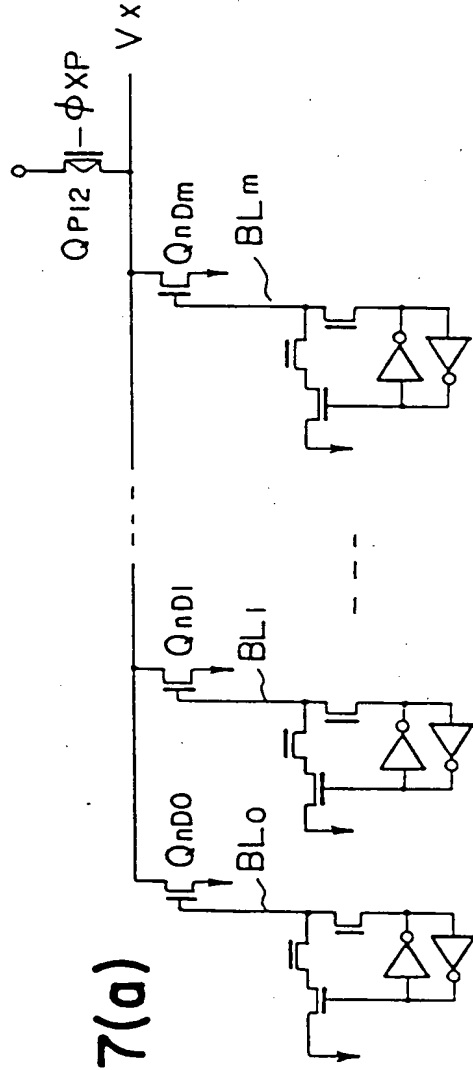


FIG. 17(b)

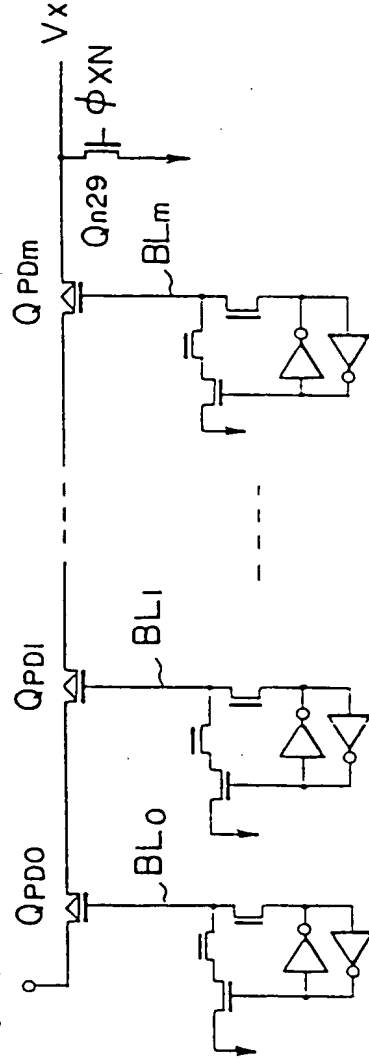


FIG. 18(a)

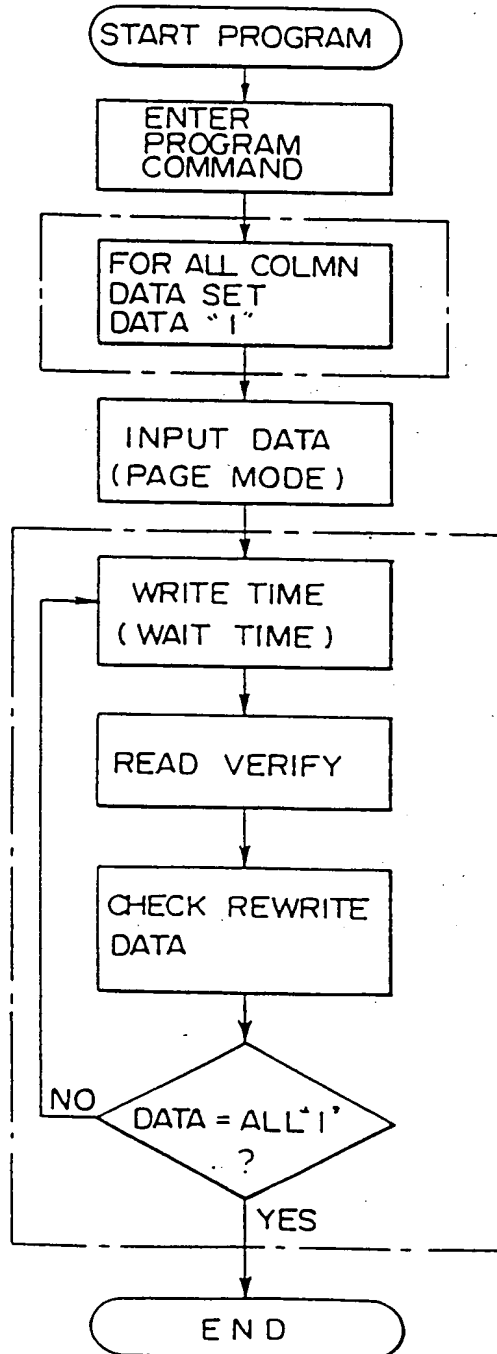


FIG. 18(b)

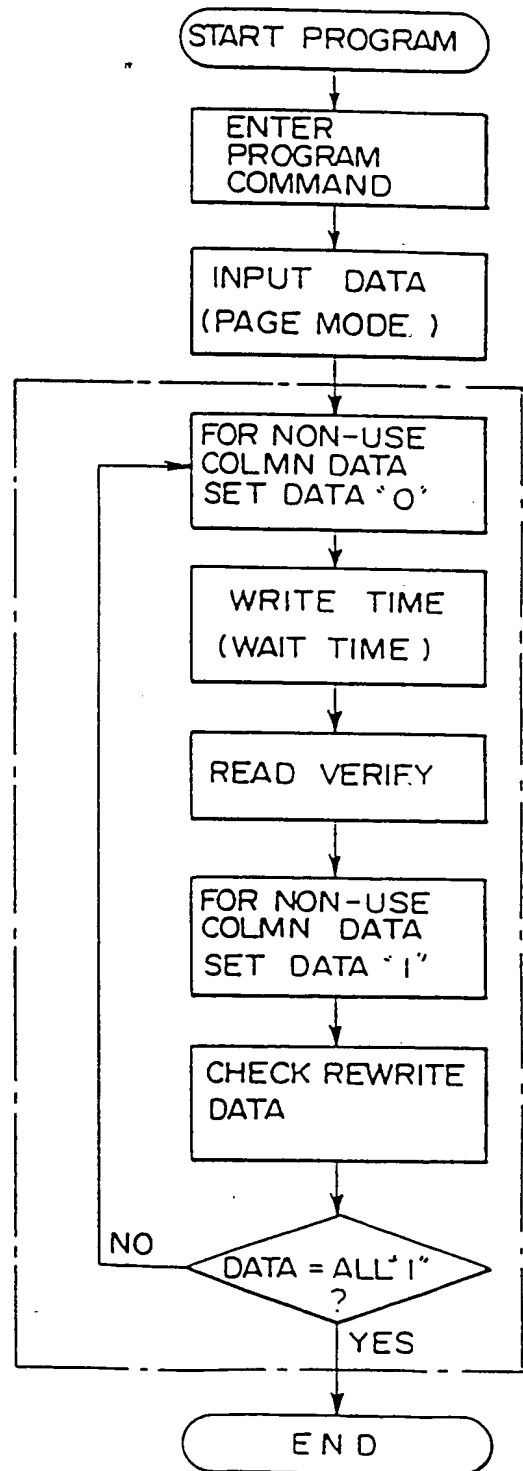


FIG. 19(a)

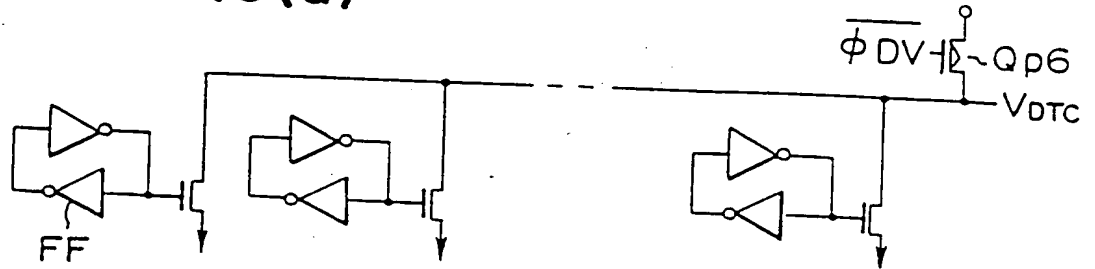


FIG. 19(b)

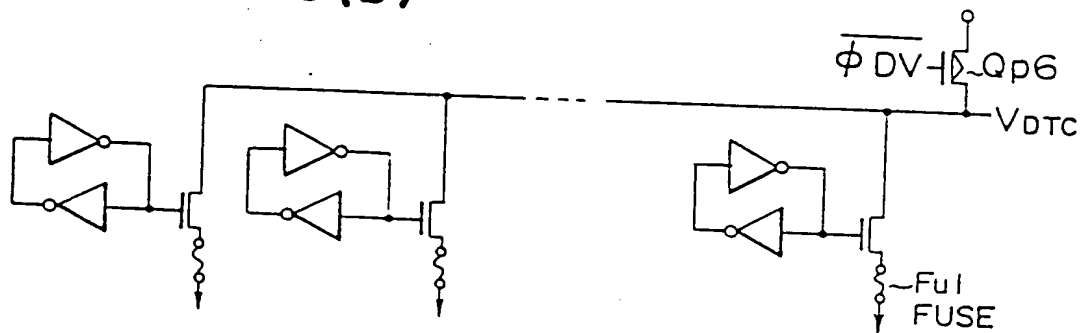


FIG. 19(c)

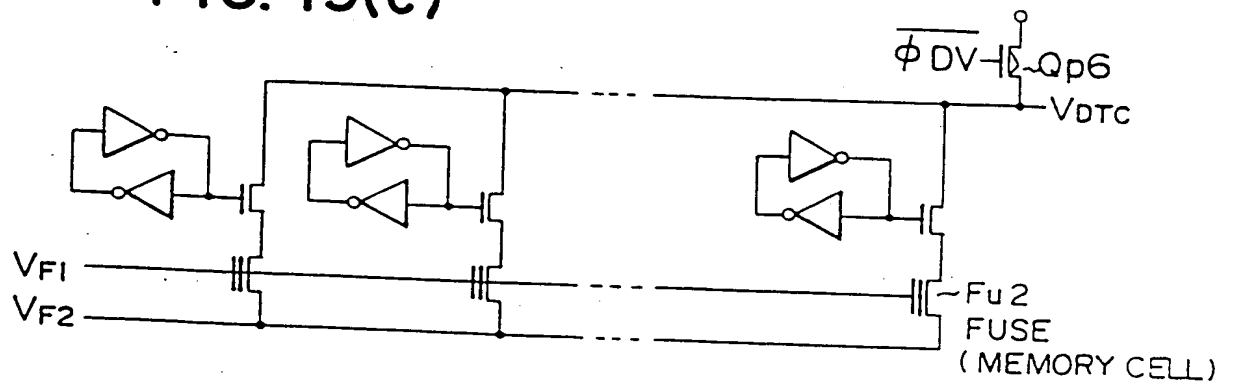


FIG. 20(b)

FIG. 20(a)

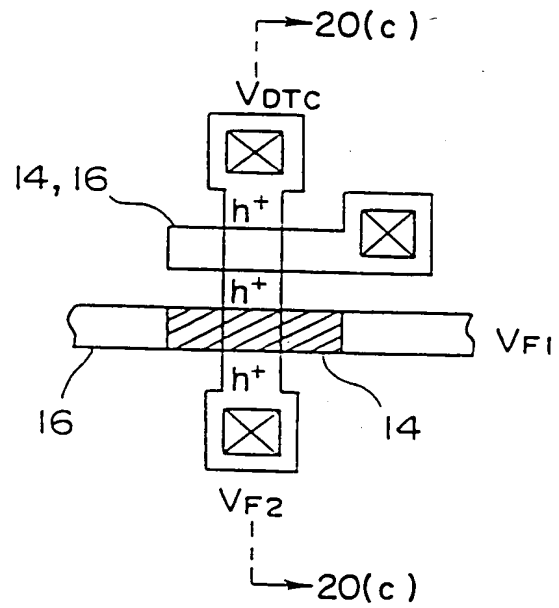
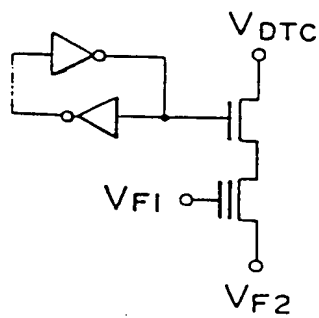


FIG. 20(c)

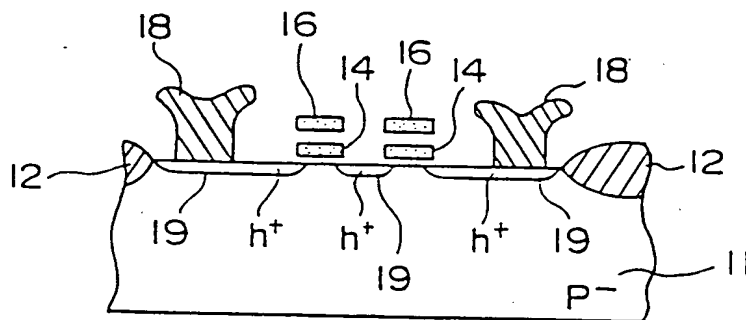


FIG. 21(a)

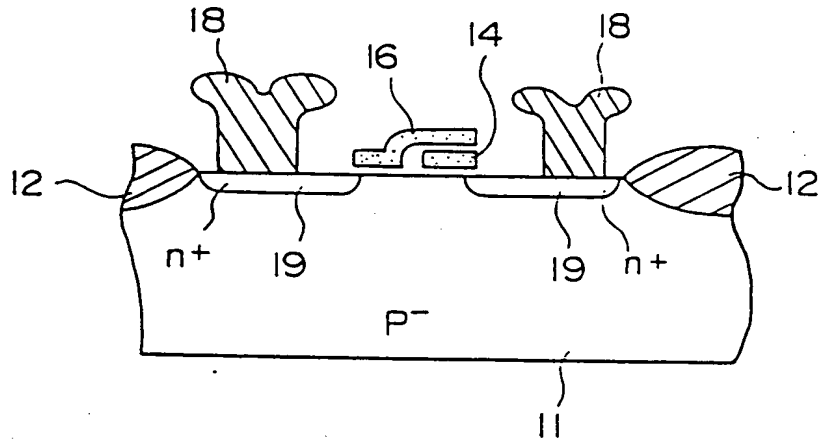


FIG. 21(b)

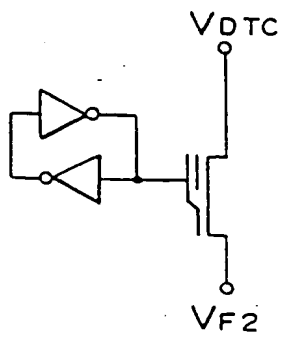
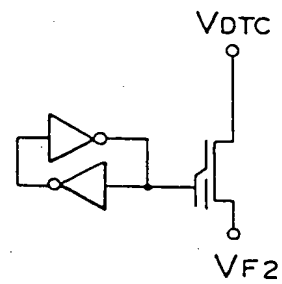


FIG. 21(c)



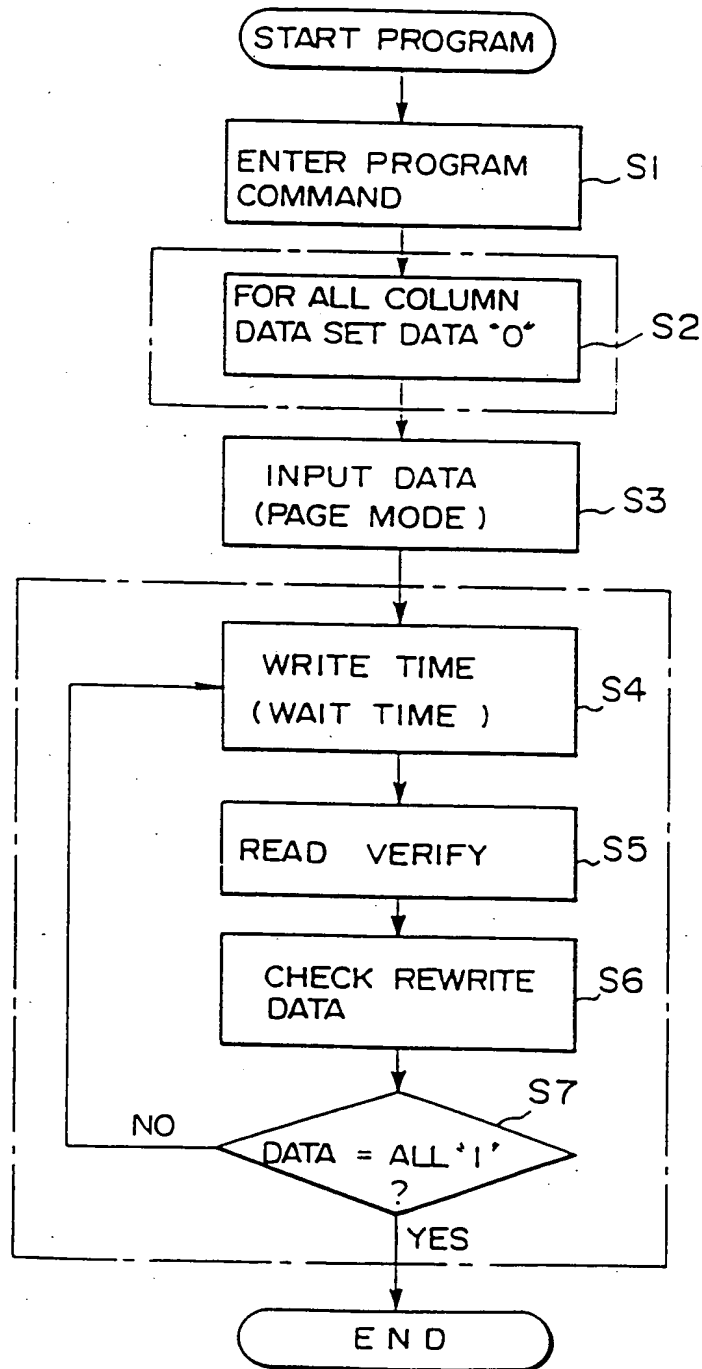


FIG. 22

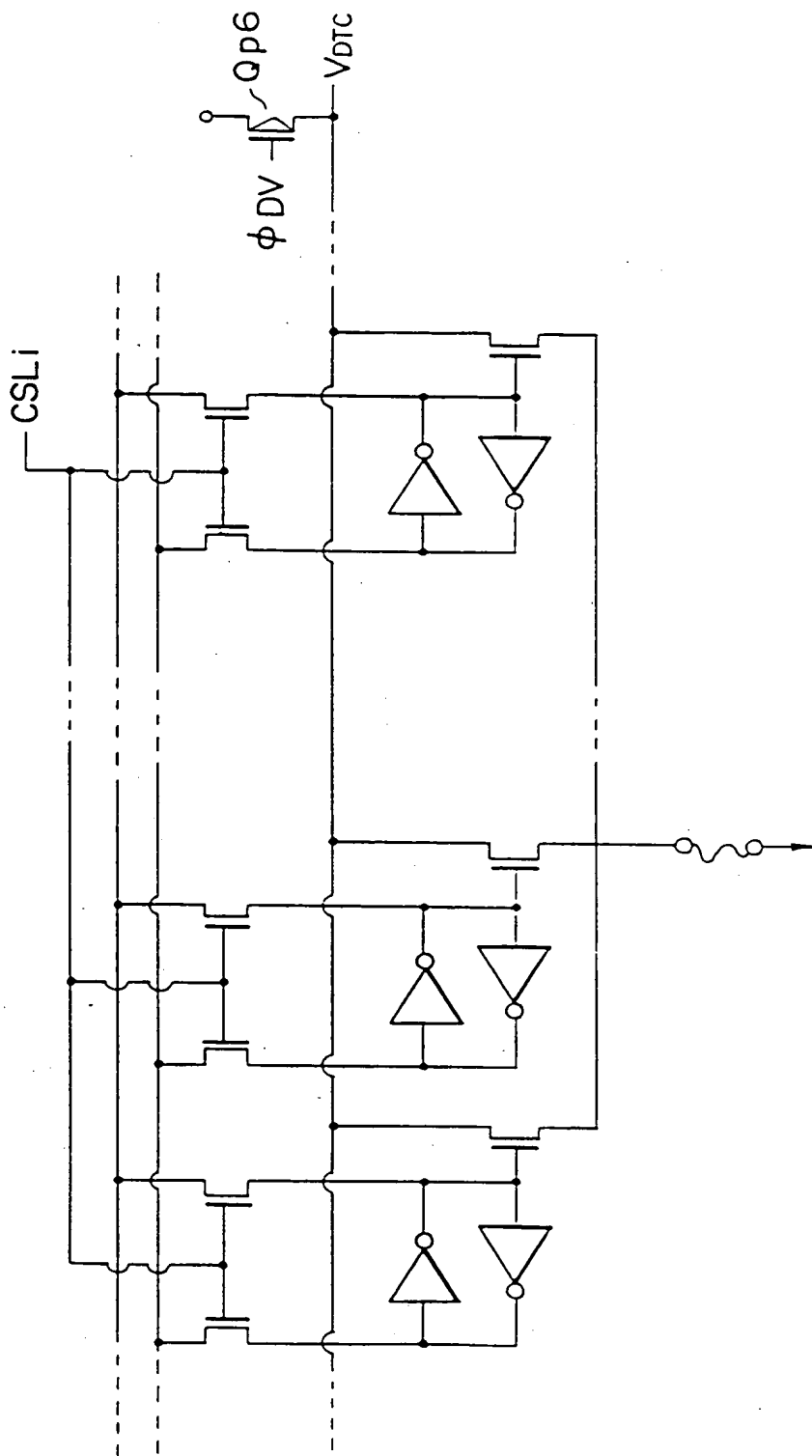


FIG. 23

The diagram shows a differential pair of NMOS transistors, Q_{n27} and Q_{n28} , connected to a common source. The gates of Q_{n27} and Q_{n28} are cross-coupled through two inverters. The drains of Q_{n27} and Q_{n28} are connected to a common drain node, which is also connected to the V_{DTCB} supply. The V_{DTCB} supply is also connected to the gates of Q_{n27} and Q_{n28} . The V_{DTCB} supply is also connected to the gates of Q_{n27} and Q_{n28} . The V_{DTCB} supply is also connected to the gates of Q_{n27} and Q_{n28} .

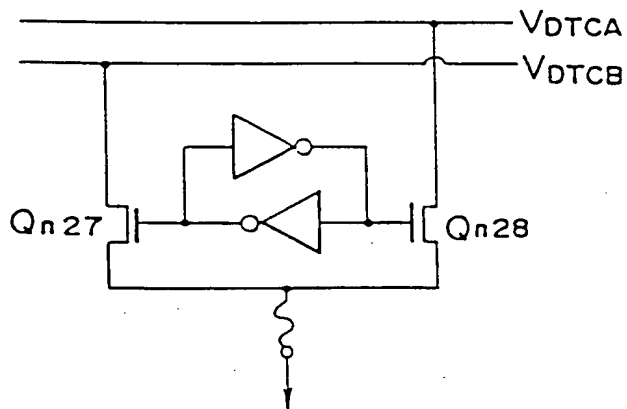


FIG. 25(a)

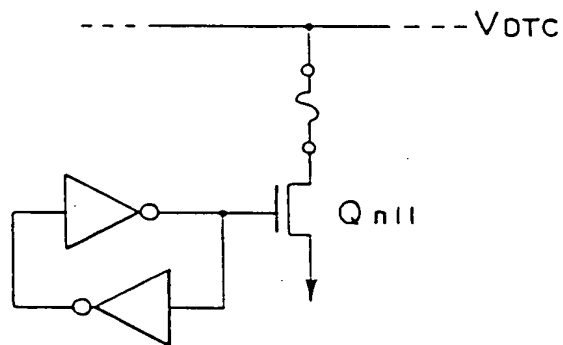


FIG. 25(b)

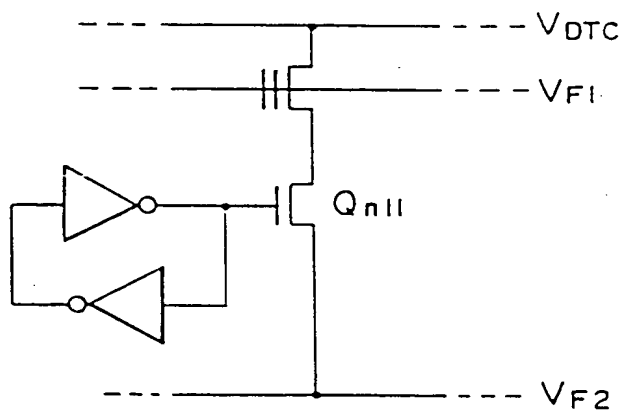


FIG. 26(a)

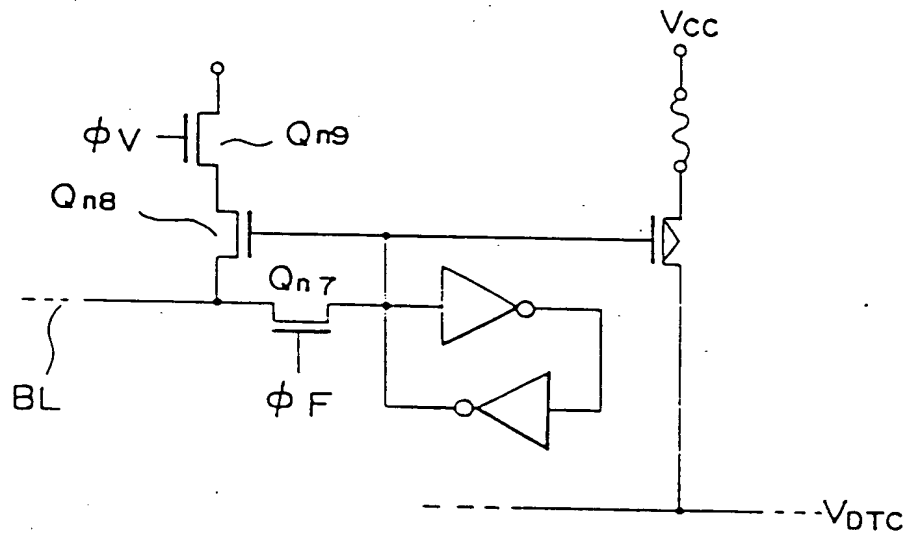


FIG. 26(b)

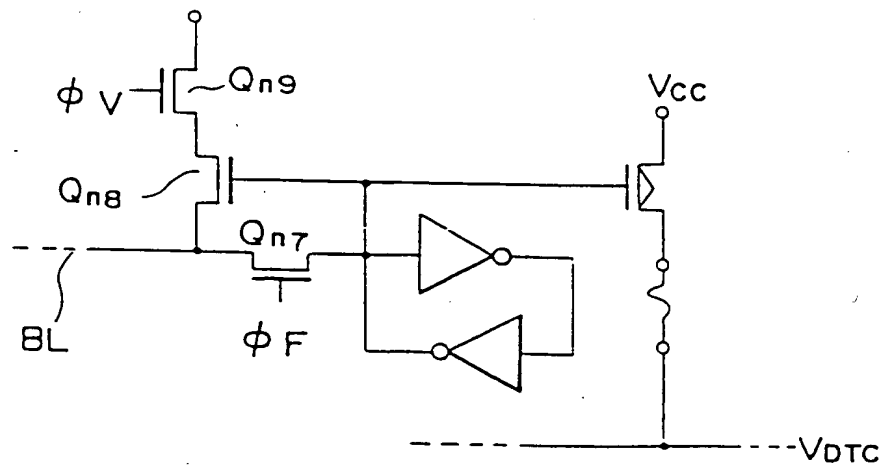


FIG. 27(a)

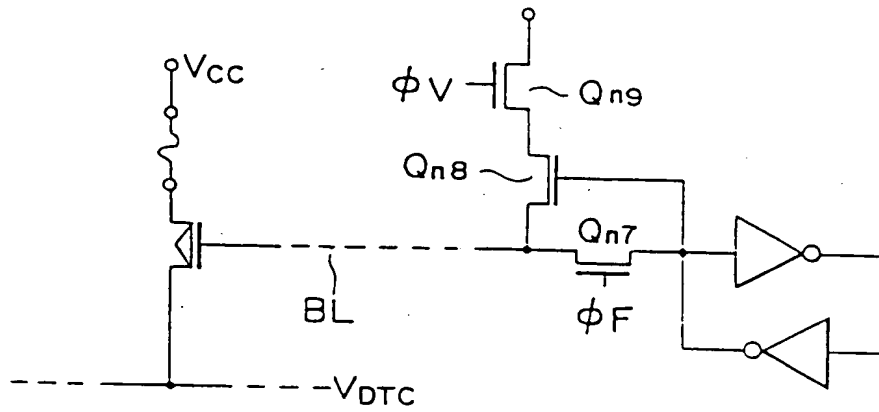


FIG. 27(b)

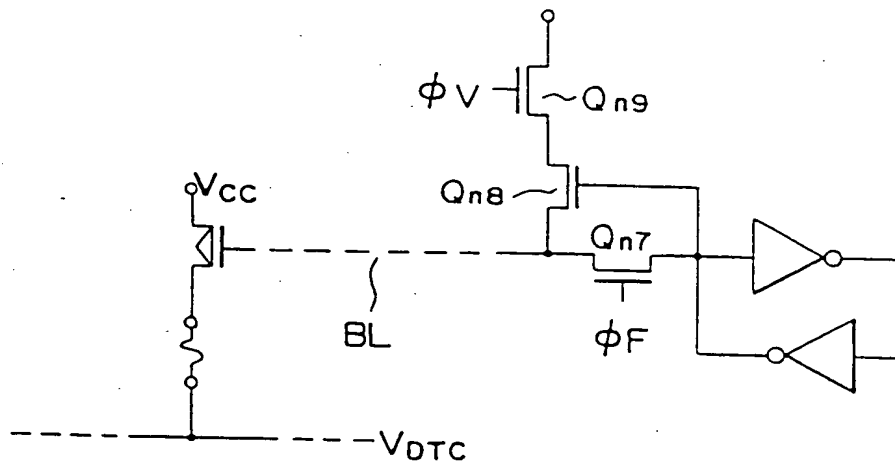


FIG. 28(a)

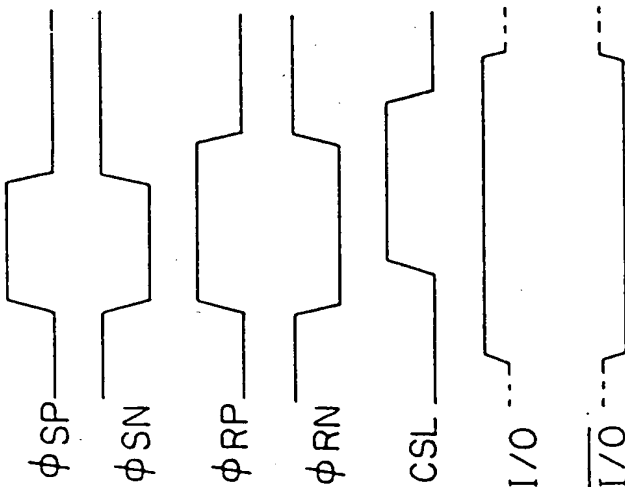
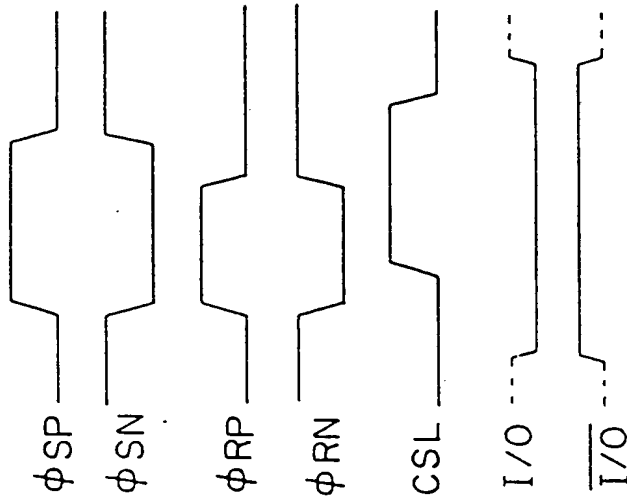


FIG. 28(b)



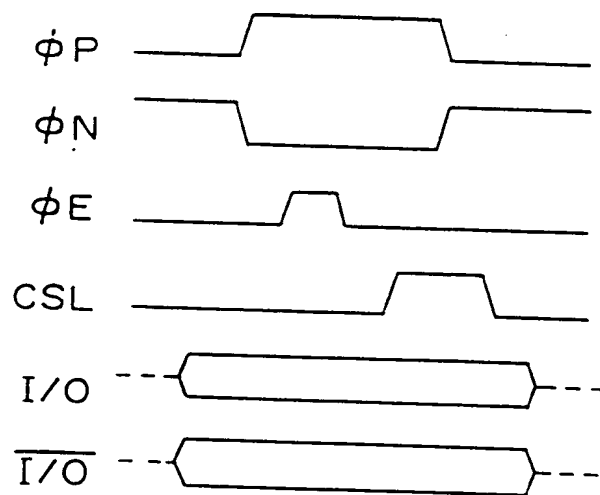
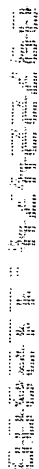
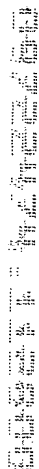


FIG. 29

[illegible][illegible]

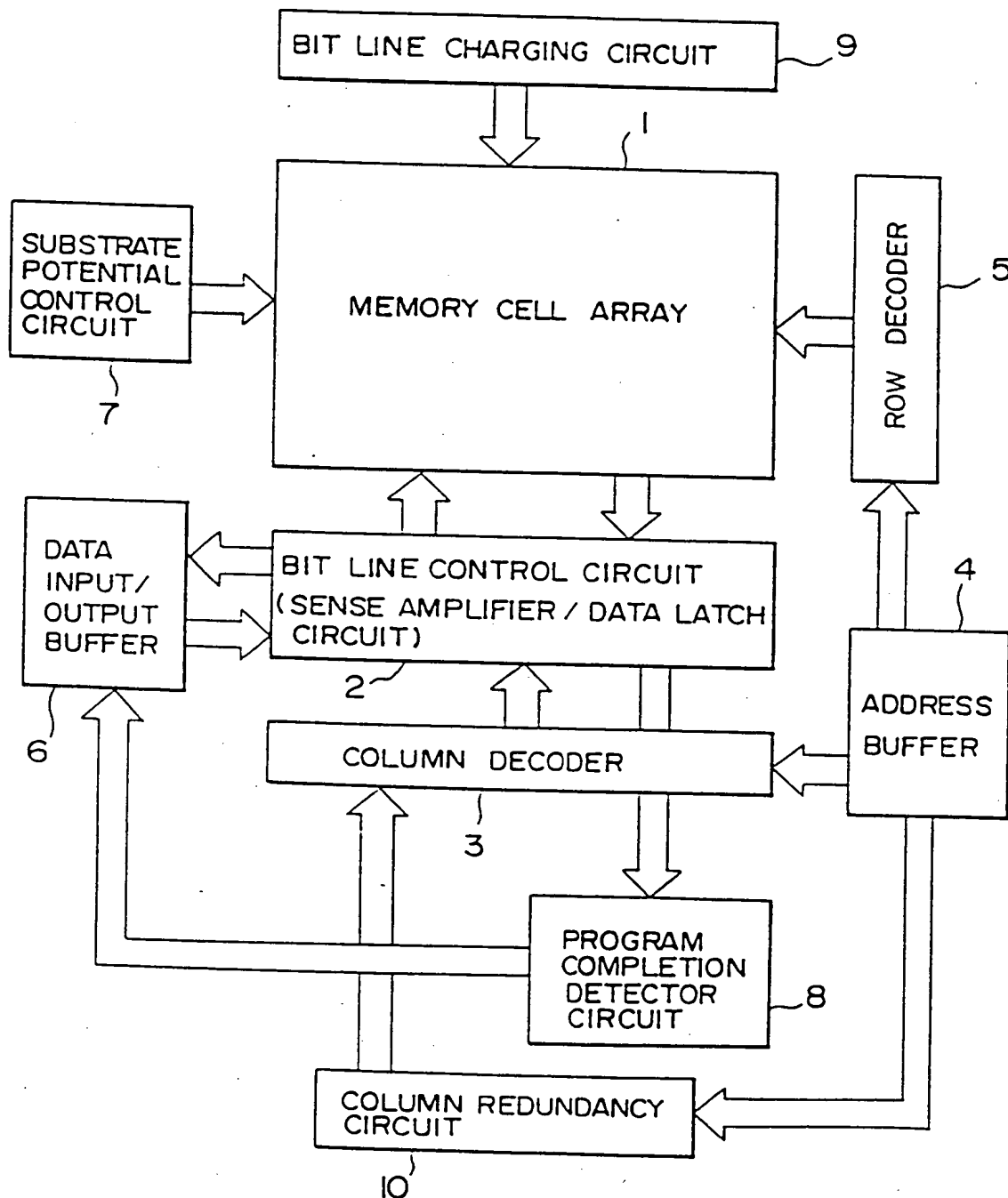


FIG. 32

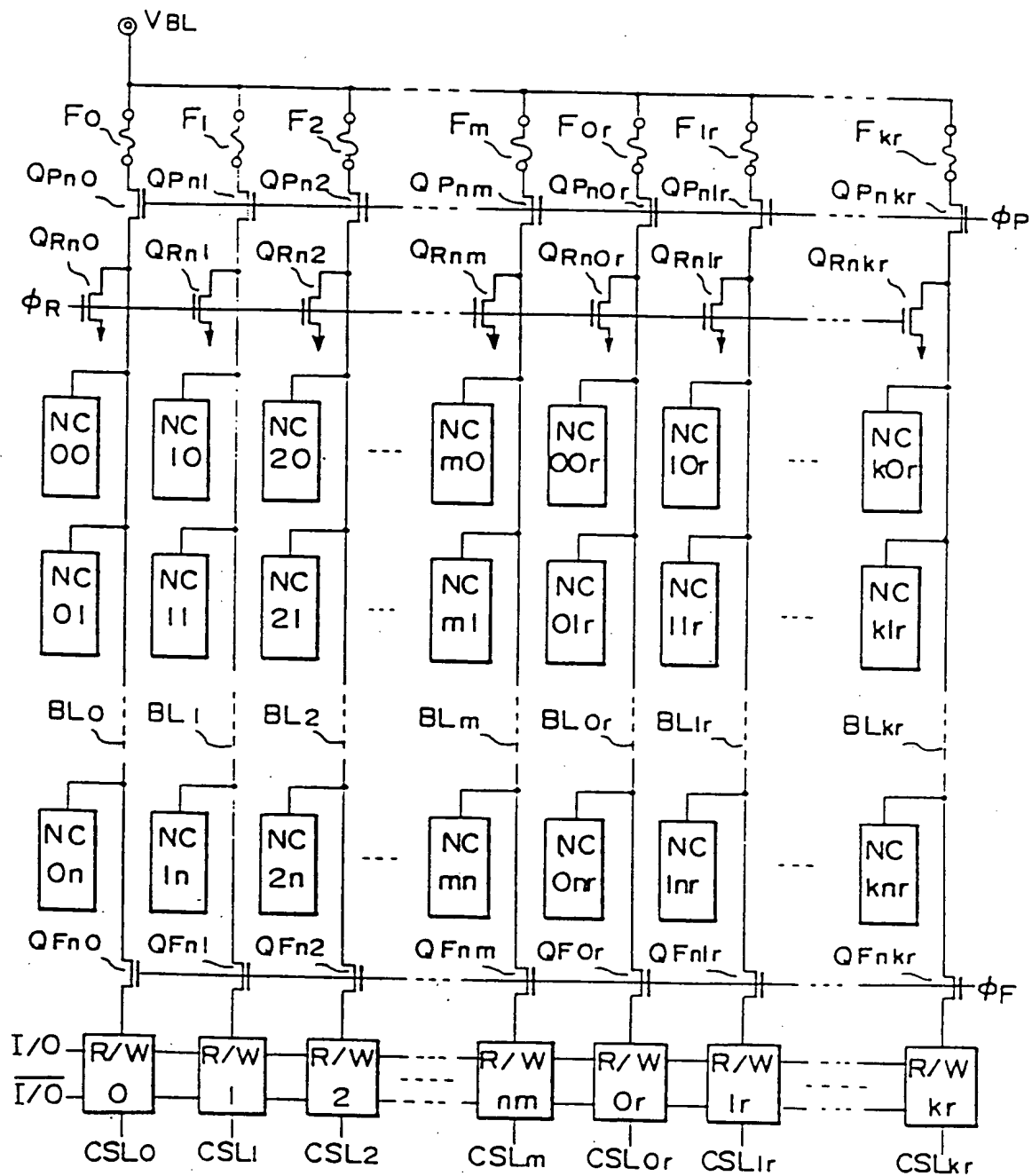


FIG. 33

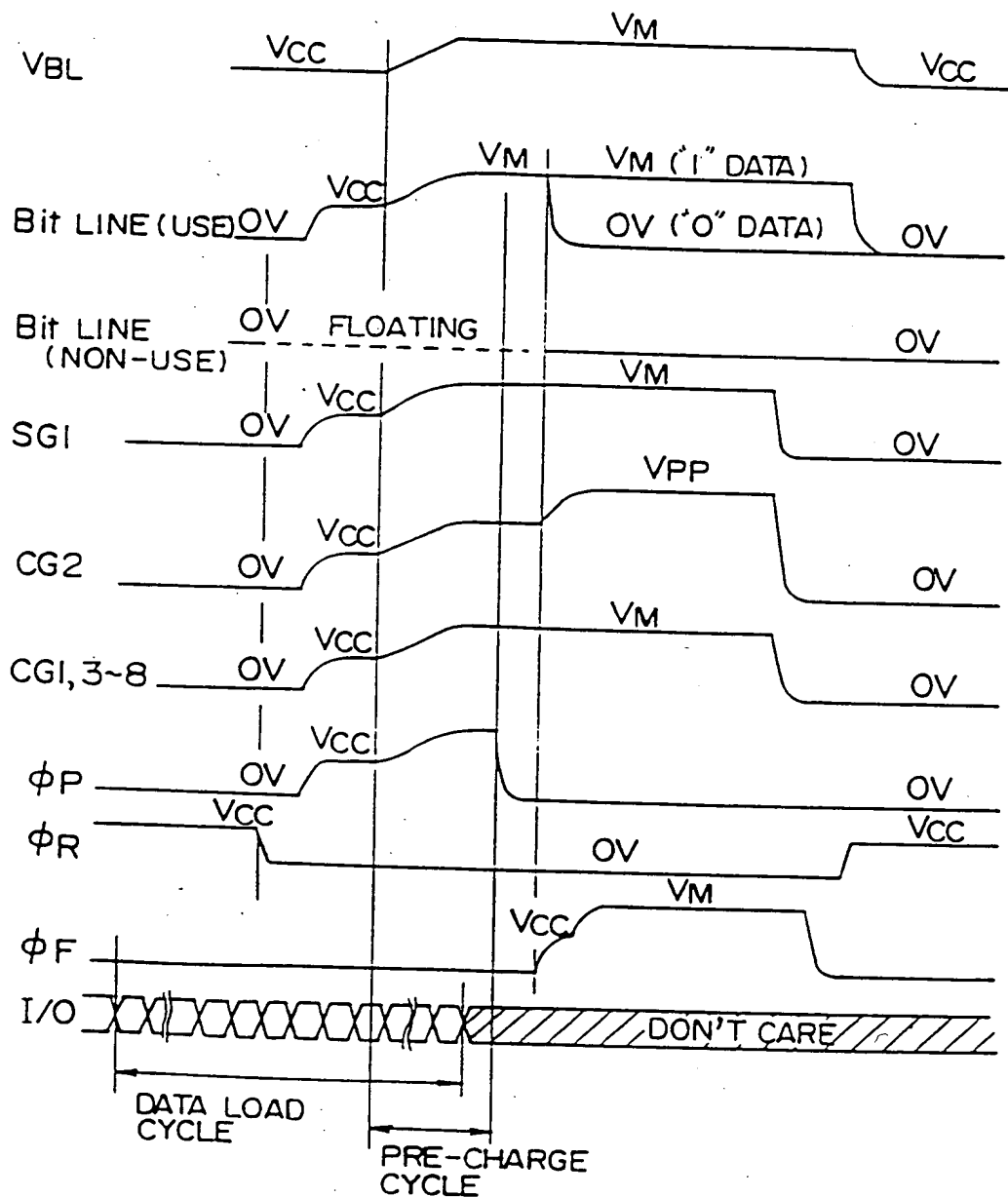


FIG.34

The diagram shows the timing of various signals over time. The signals are:

- Bit LINE (USE)**: A solid line that rises for a "0" READ and falls for a "1" READ.
- Bit LINE (NON-USE)**: A dashed line that remains at a low level.
- SG1,2**: A signal that rises during the "0" READ and falls during the "1" READ.
- CG2**: A signal that rises during the "0" READ and falls during the "1" READ.
- CG1,3~8**: A signal that rises during the "0" READ and falls during the "1" READ.
- ϕP** : A signal that rises during the "0" READ and falls during the "1" READ.
- ϕR** : A signal that rises during the "0" READ and falls during the "1" READ.
- ϕF** : A signal that rises during the "0" READ and falls during the "1" READ.
- I/O**: A signal that is marked "DON'T CARE" and is shown as a hatched area.

FIG. 35

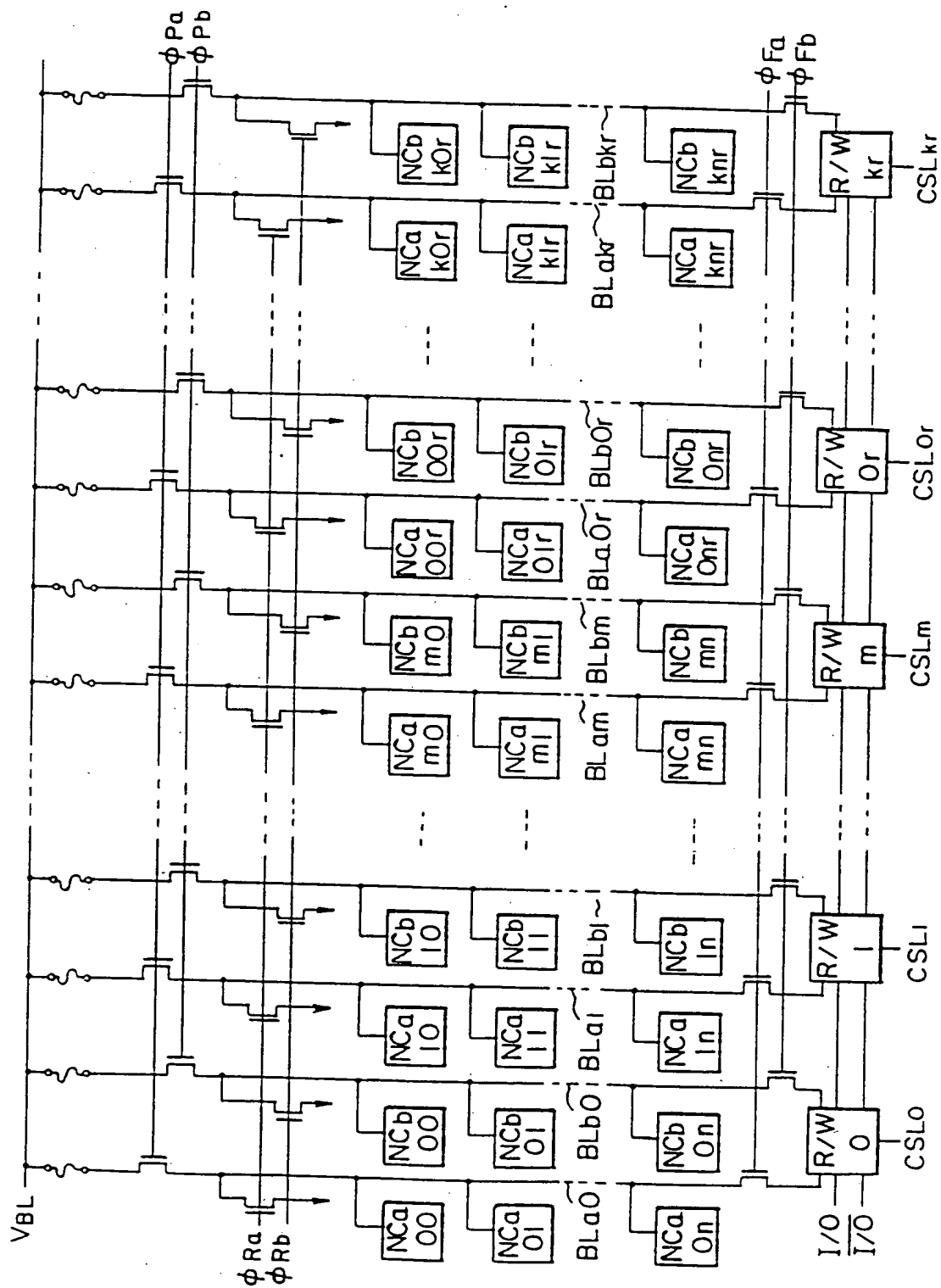


FIG. 36

The diagram shows the timing of various signals relative to the data load cycle and pre-charge cycle. The signals are:

- VBL**: Vertical blanking level, high during the data load cycle and low during the pre-charge cycle.
- Vcc**: Supply voltage, high during the data load cycle and low during the pre-charge cycle.
- VM**: Vertical sync signal, high during the data load cycle and low during the pre-charge cycle.
- BLa (USE)**: Horizontal sync signal, high during the data load cycle and low during the pre-charge cycle.
- BLb (USE)**: Horizontal sync signal, high during the data load cycle and low during the pre-charge cycle.
- BLa (NON-USE)**: Horizontal sync signal, high during the data load cycle and low during the pre-charge cycle.
- BLb (NON-USE)**: Horizontal sync signal, high during the data load cycle and low during the pre-charge cycle.
- SG1**: Sync gate 1, high during the data load cycle and low during the pre-charge cycle.
- CG2**: Sync gate 2, high during the data load cycle and low during the pre-charge cycle.
- CGI,3-8**: Sync gate 3-8, high during the data load cycle and low during the pre-charge cycle.
- phi Pa**: Phase 1 clock, high during the data load cycle and low during the pre-charge cycle.
- phi Pb**: Phase 2 clock, high during the data load cycle and low during the pre-charge cycle.
- phi Ra**: Phase 3 clock, high during the data load cycle and low during the pre-charge cycle.
- phi Rb**: Phase 4 clock, high during the data load cycle and low during the pre-charge cycle.
- phi Fa**: Phase 5 clock, high during the data load cycle and low during the pre-charge cycle.
- phi Fb**: Phase 6 clock, high during the data load cycle and low during the pre-charge cycle.
- I/O**: Input/output signal, high during the data load cycle and low during the pre-charge cycle.
- DON'T CARE**: Signal that is not used during the data load cycle and pre-charge cycle.

FIG. 37

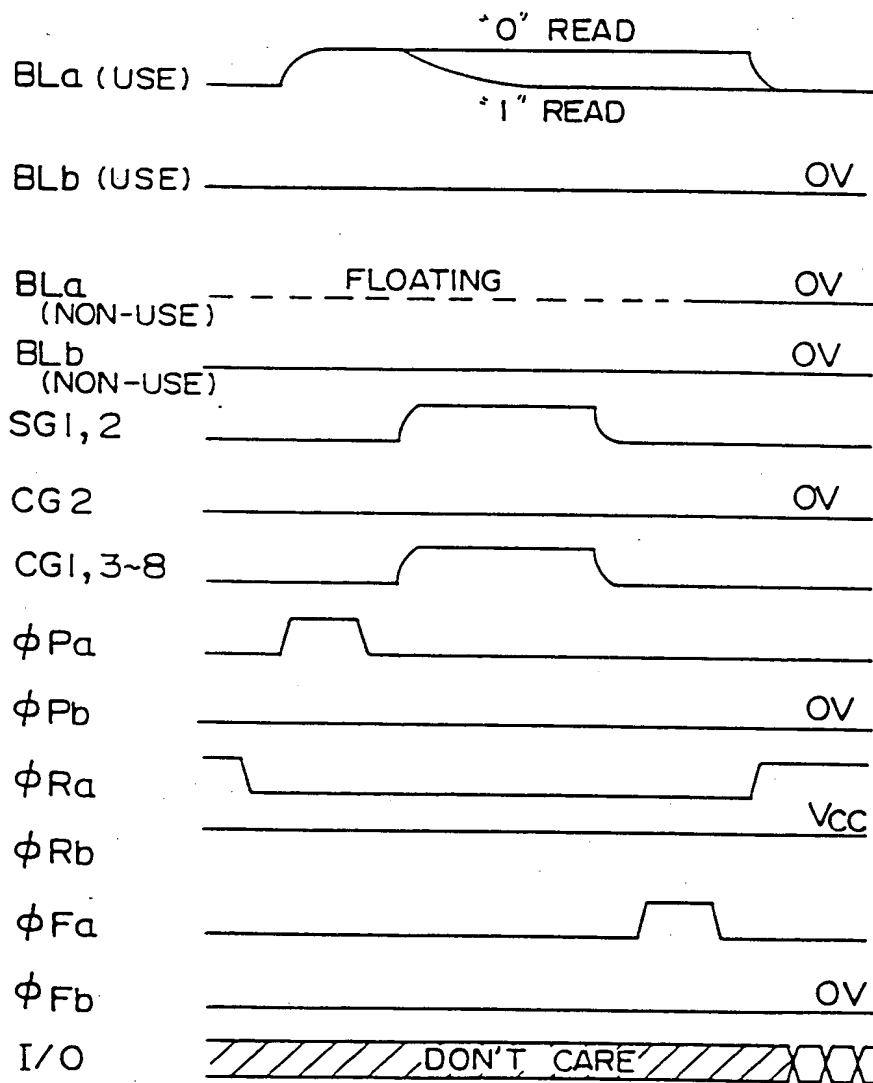


FIG. 38

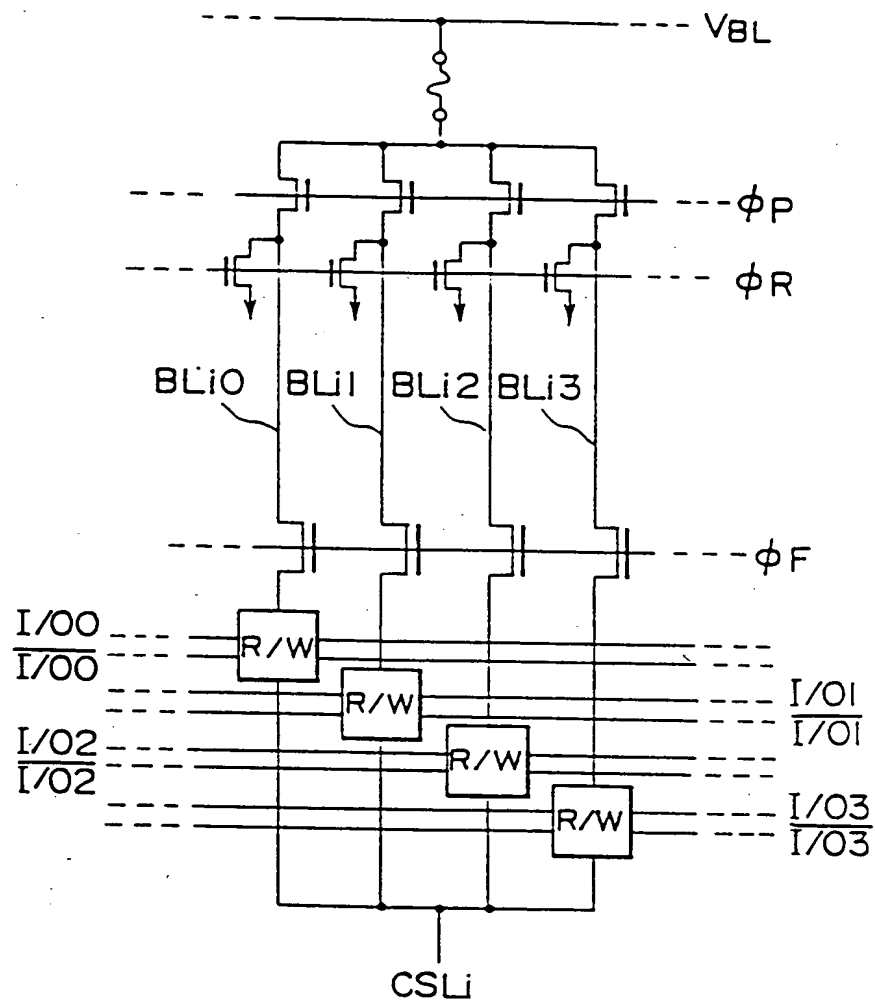


FIG. 39

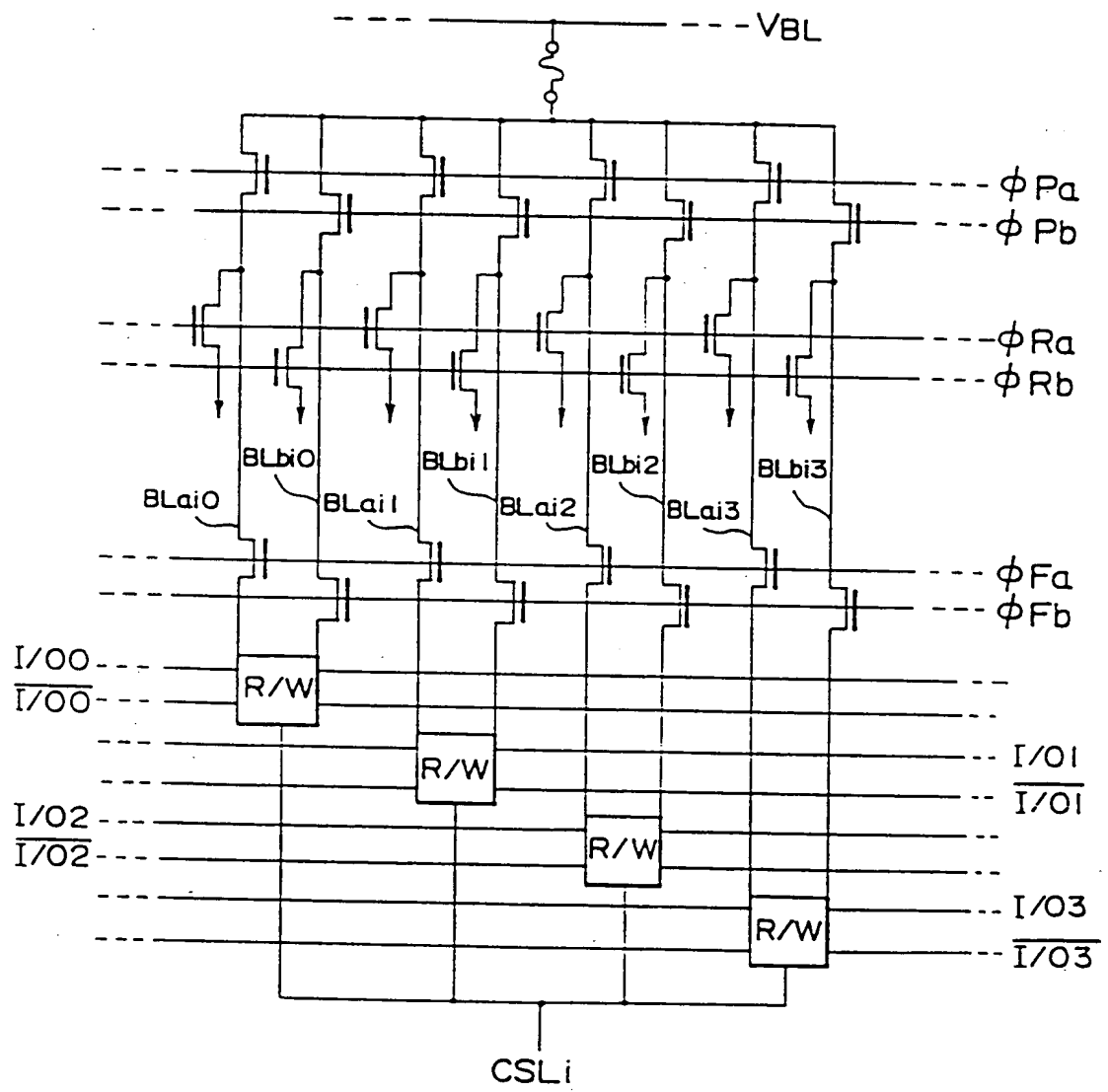


FIG. 40

2025 RELEASE

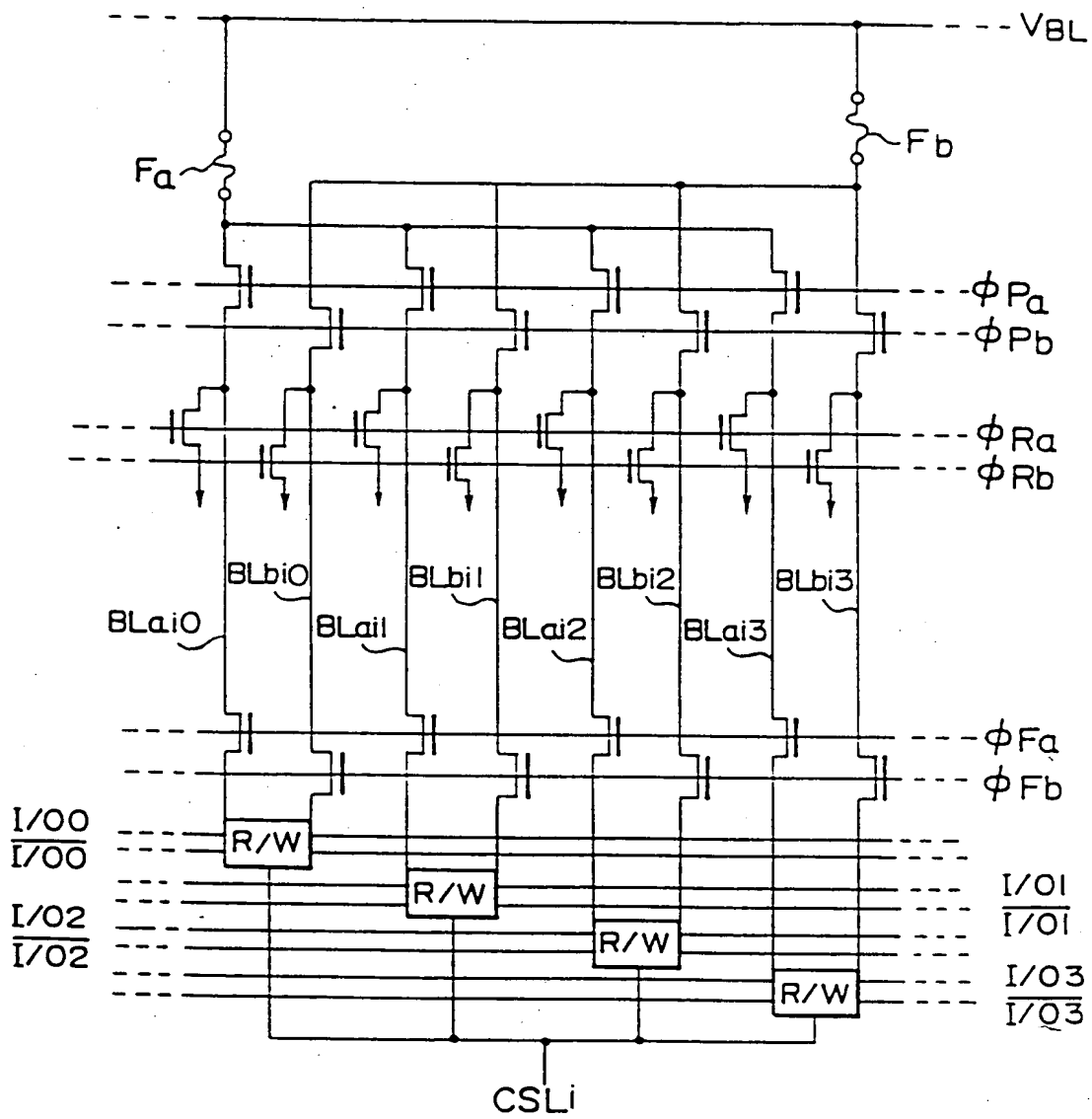
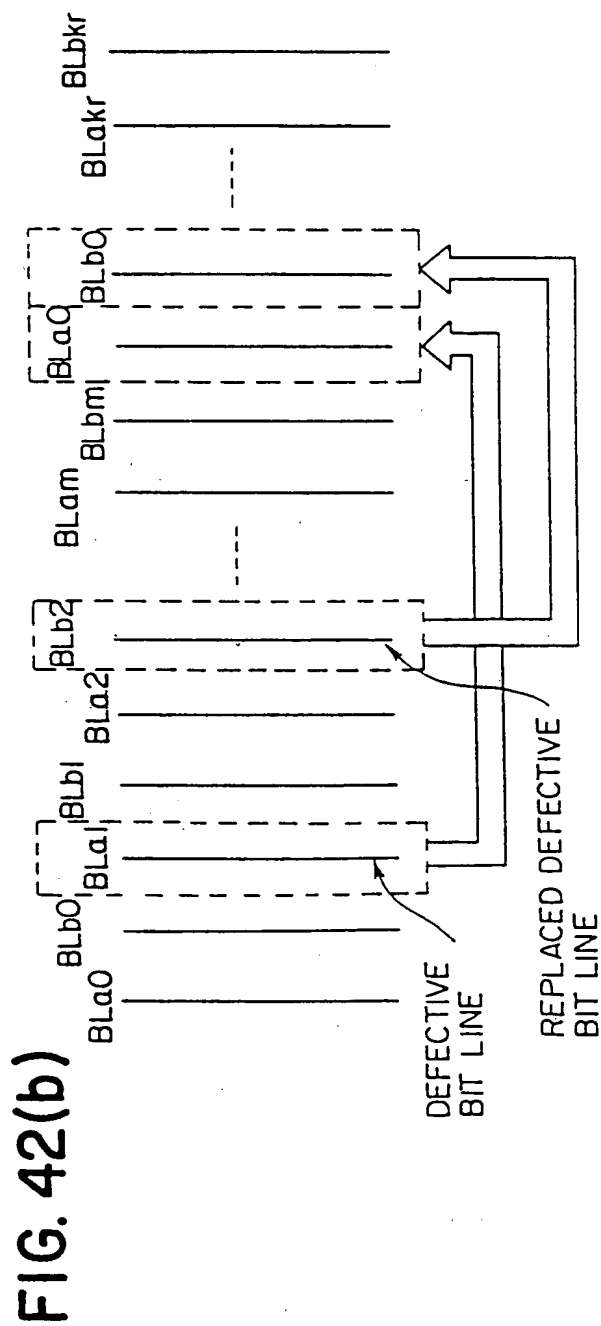
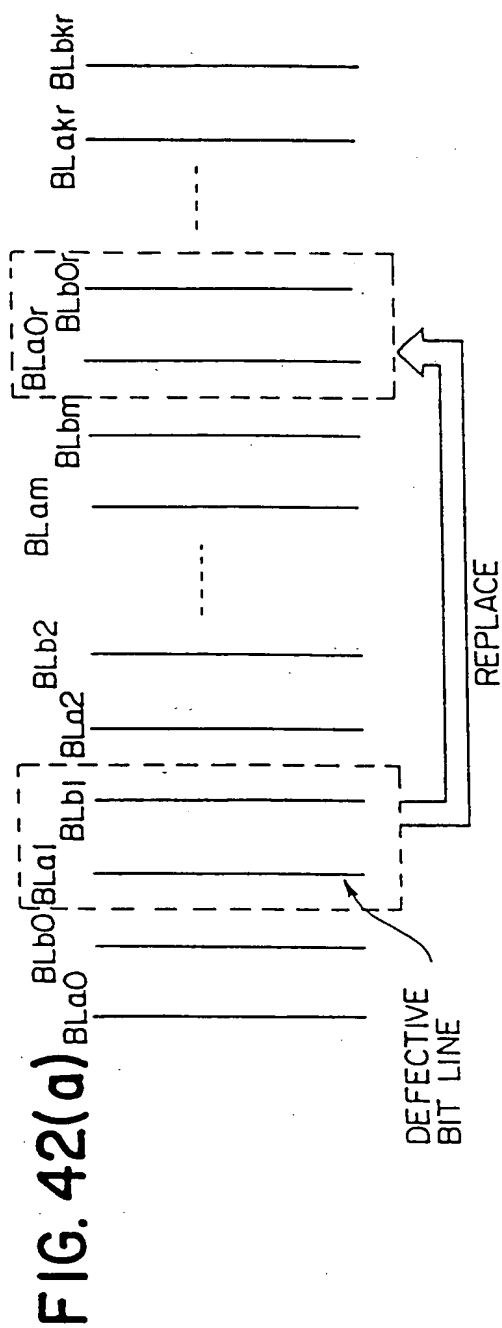


FIG. 41



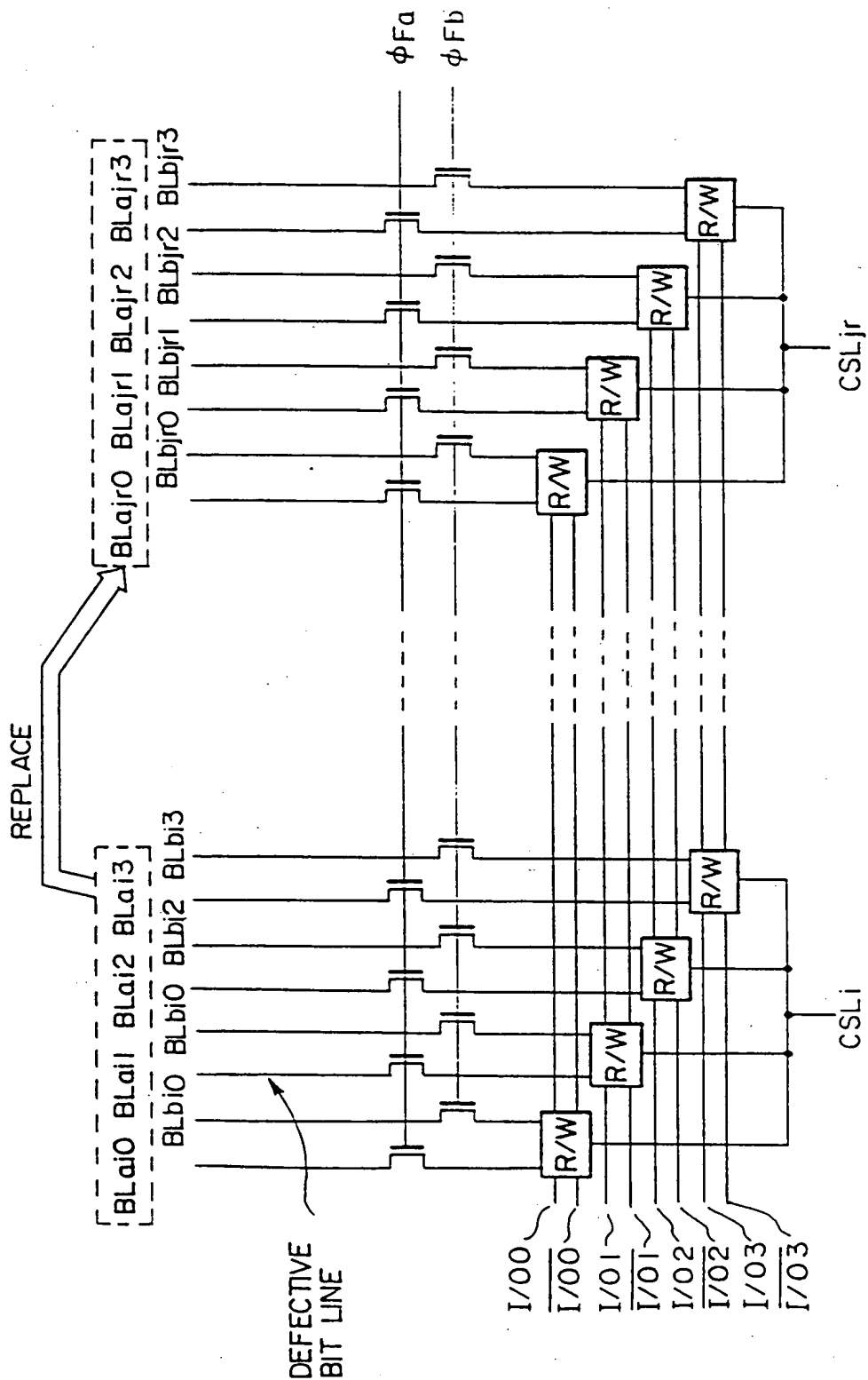


FIG. 43

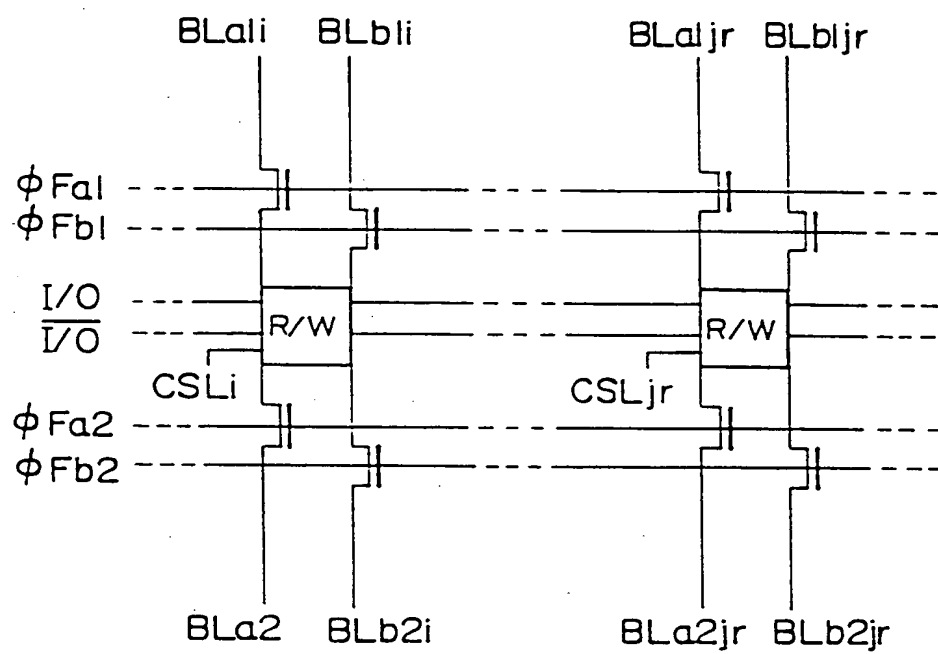


FIG.44

FIG. 45(a)

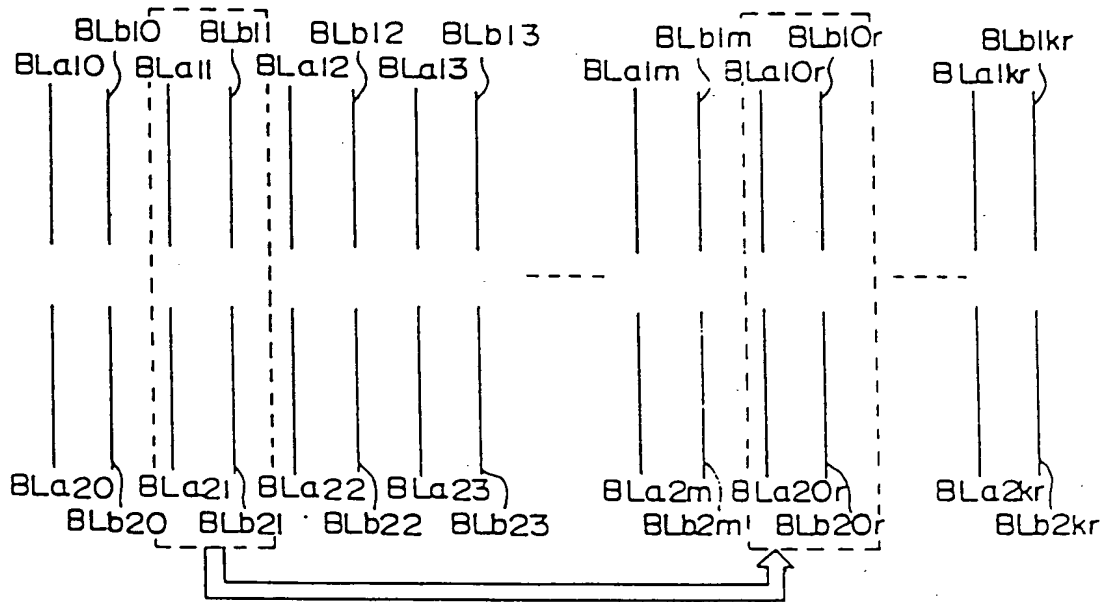


FIG. 45(b)

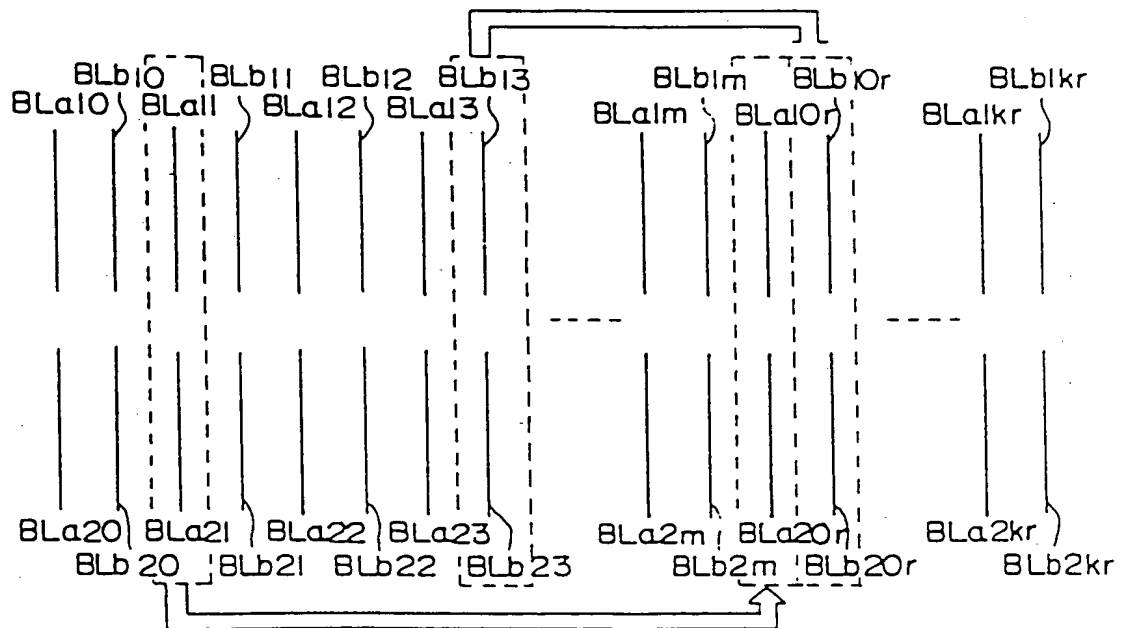


FIG. 46(a)

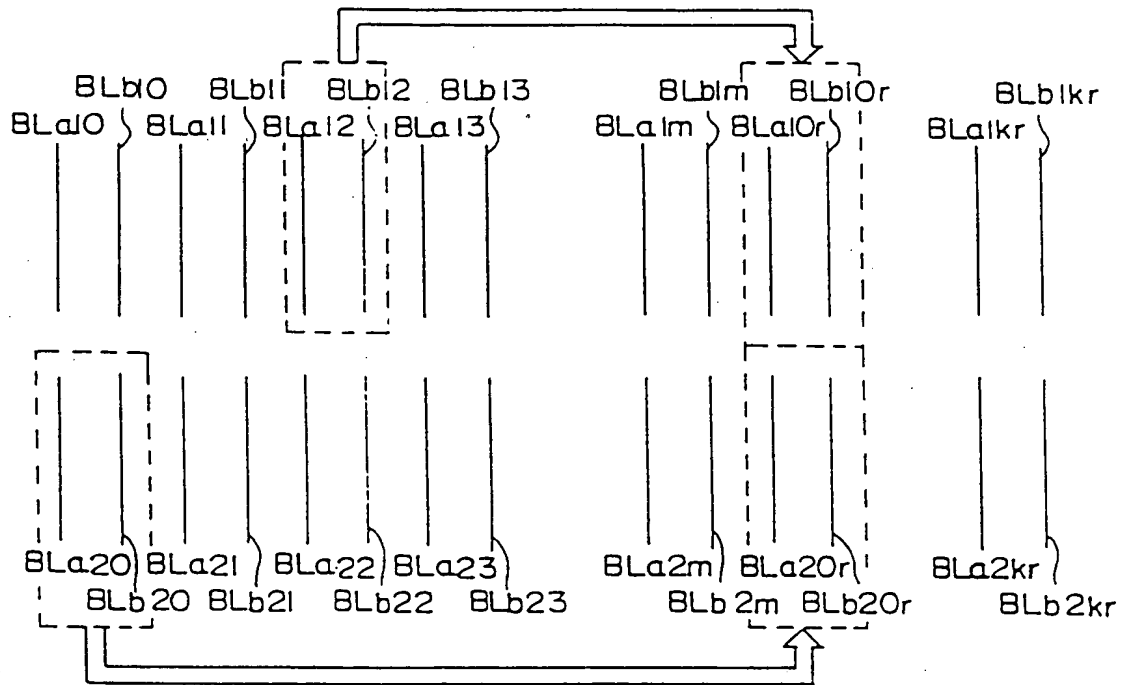
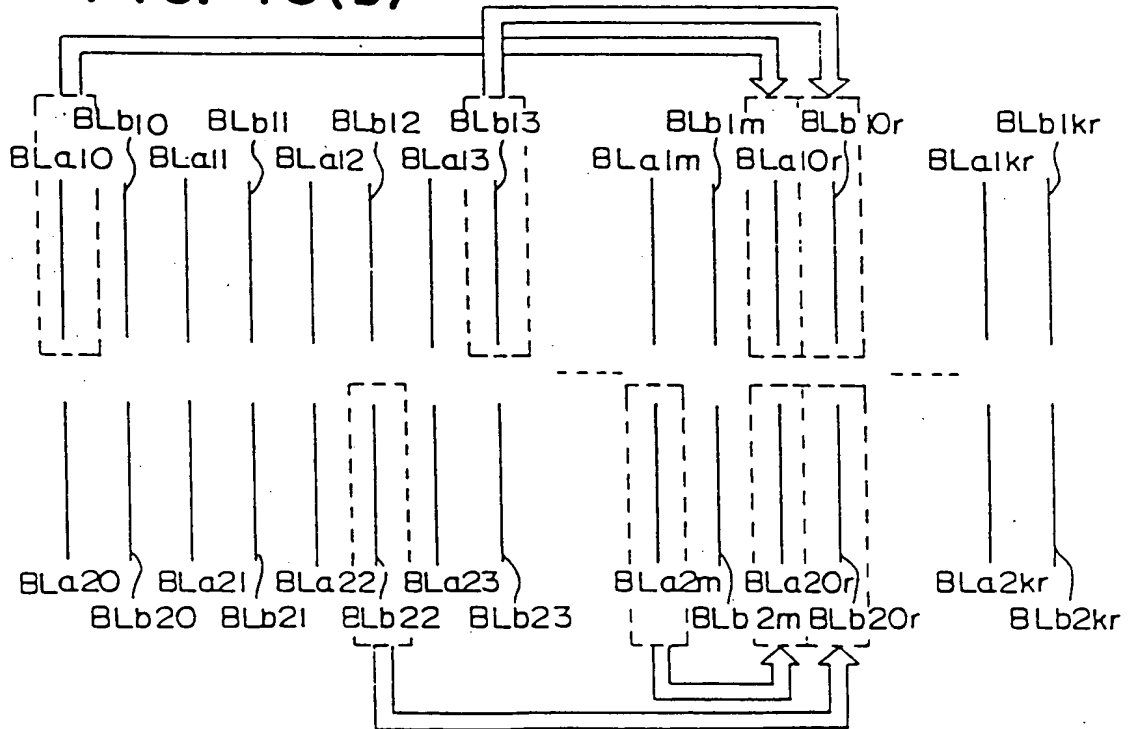


FIG. 46(b)



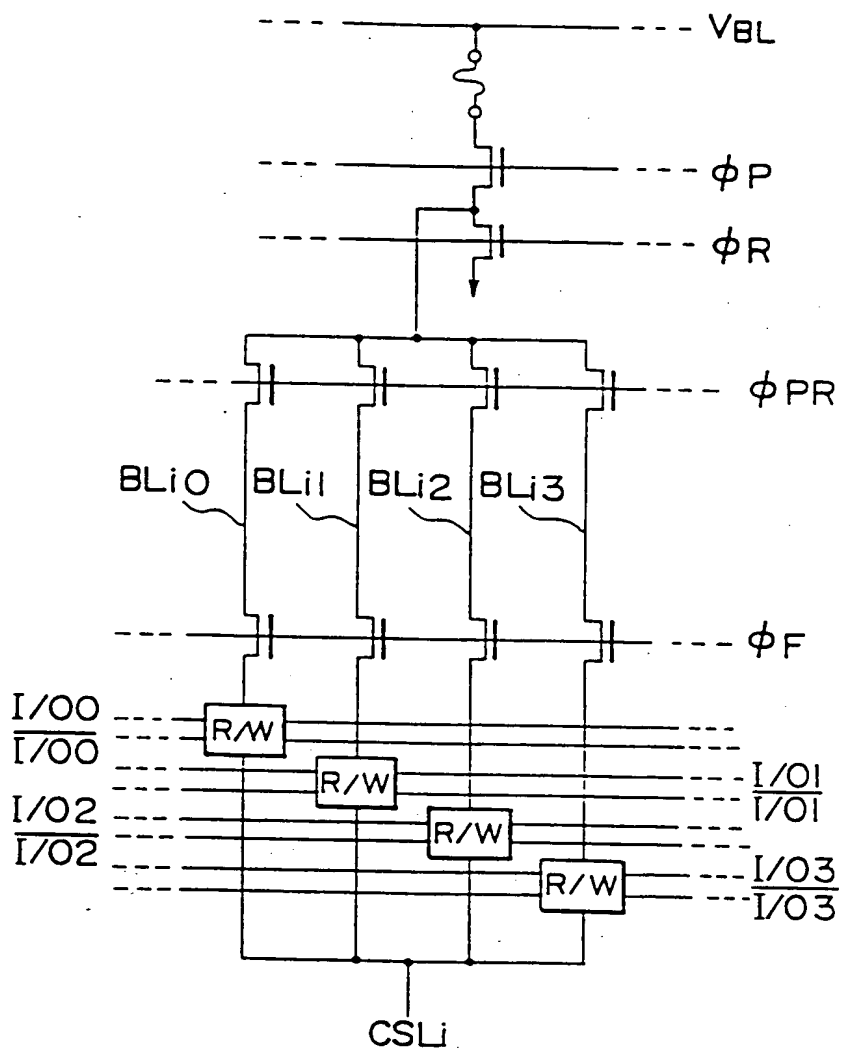


FIG. 47

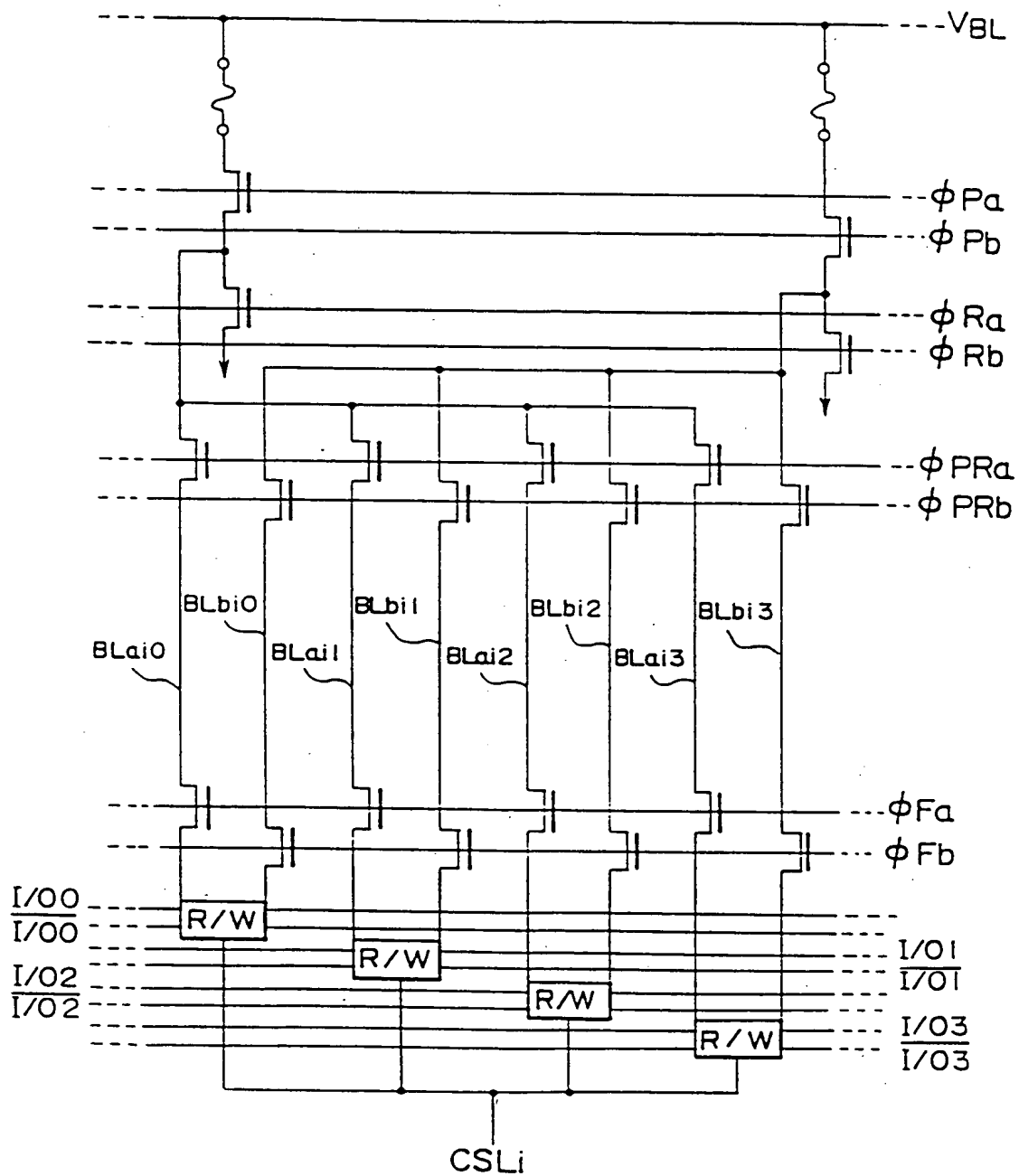


FIG. 48

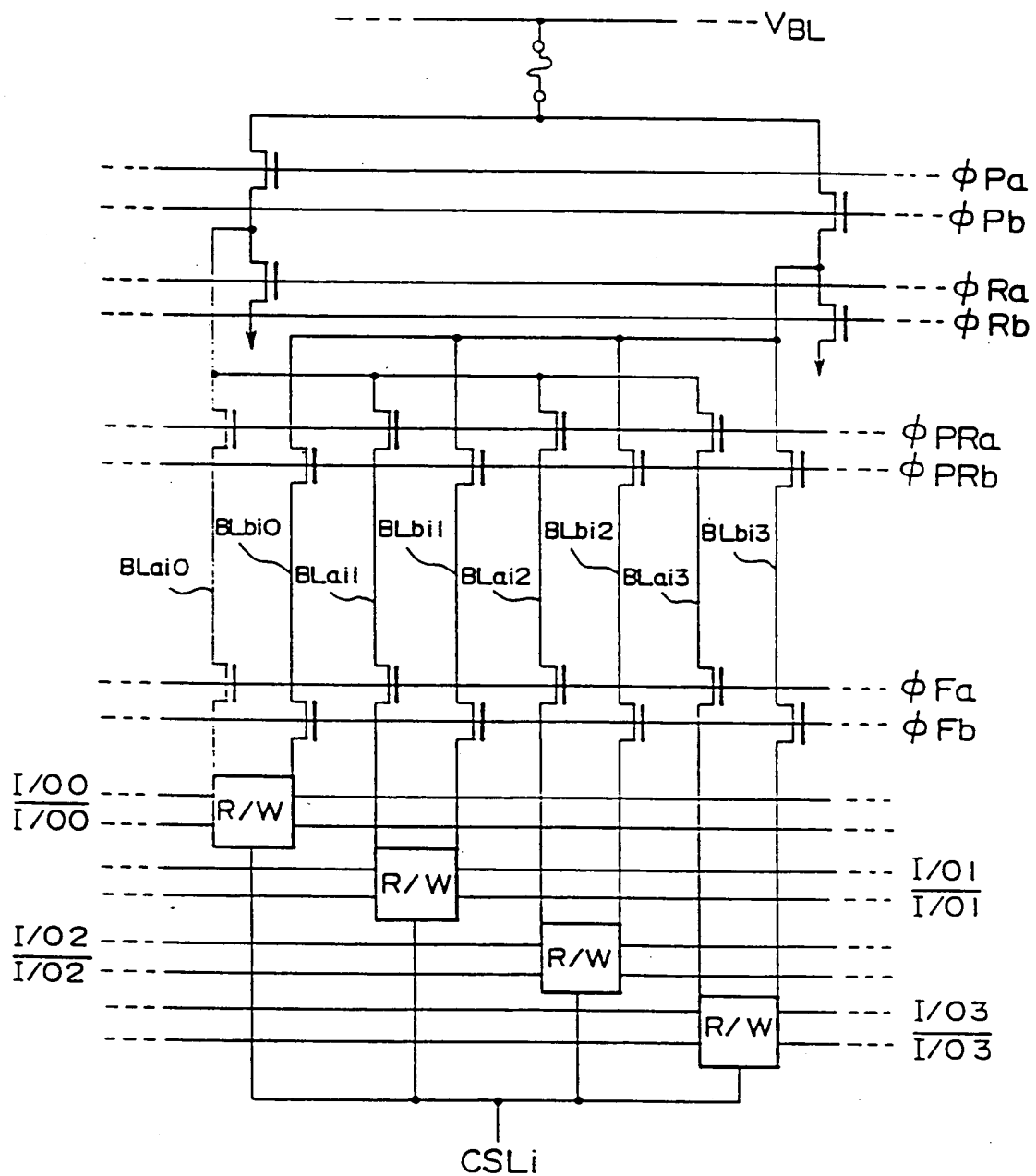


FIG.49

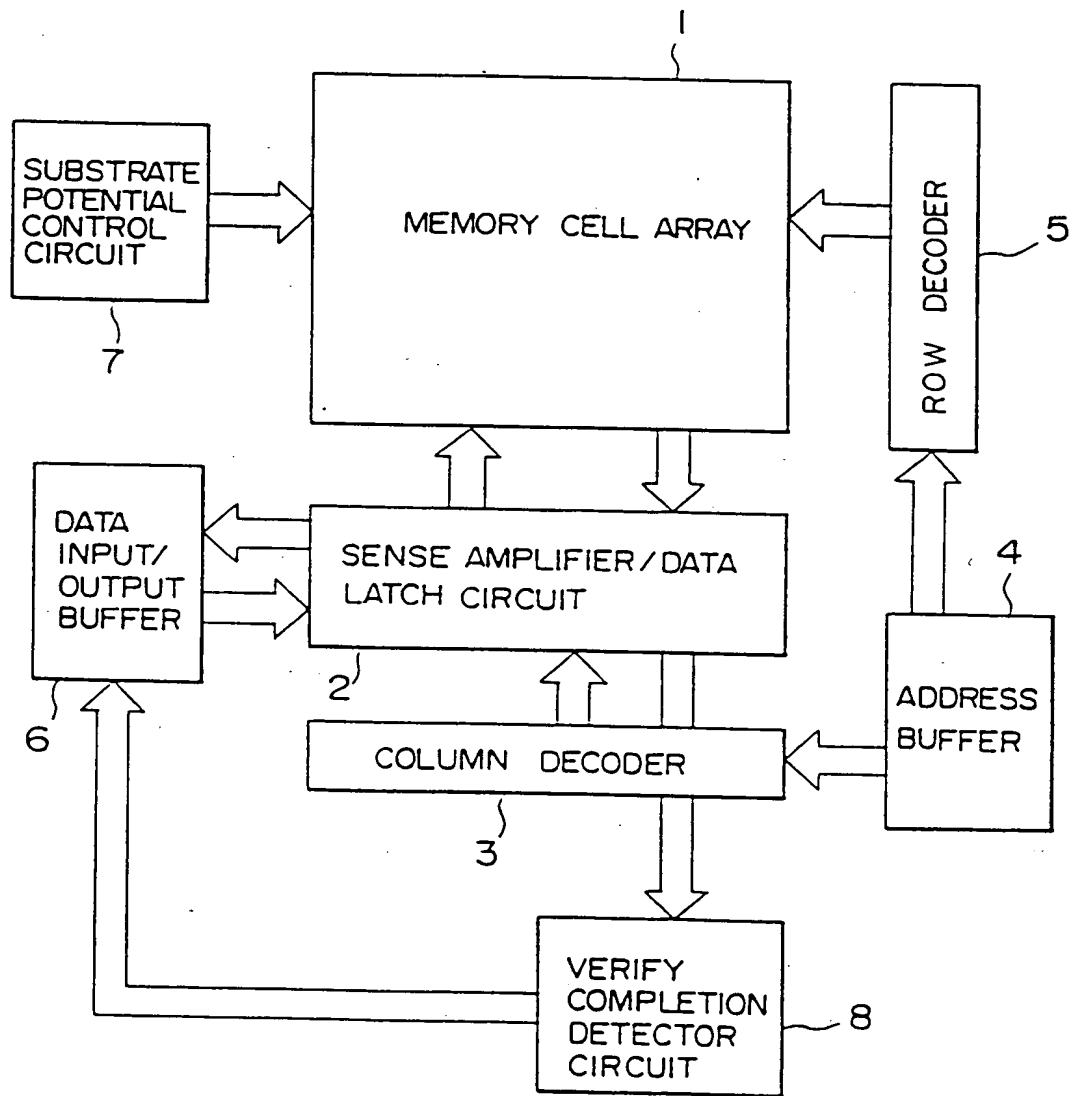


FIG. 50

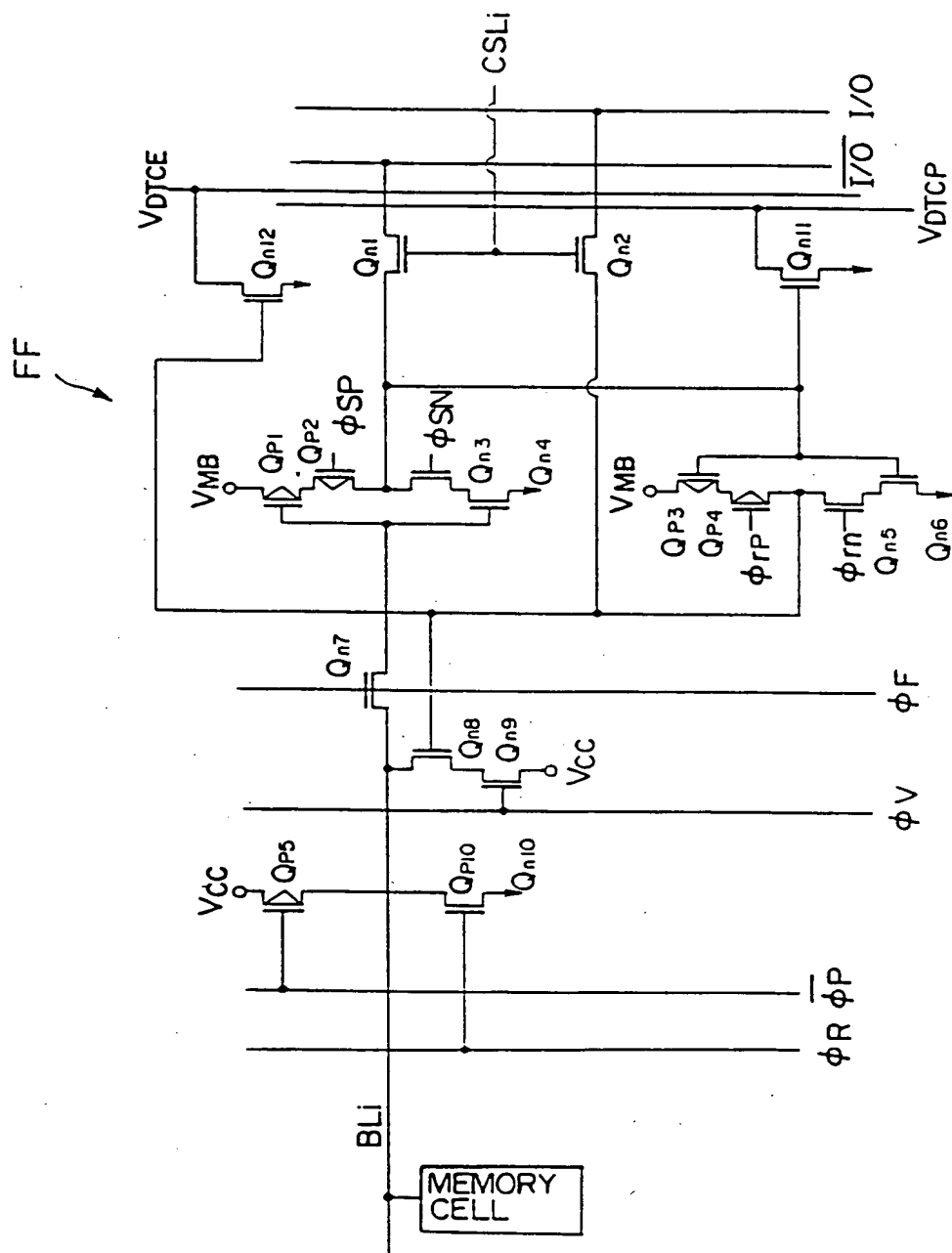


FIG. 51

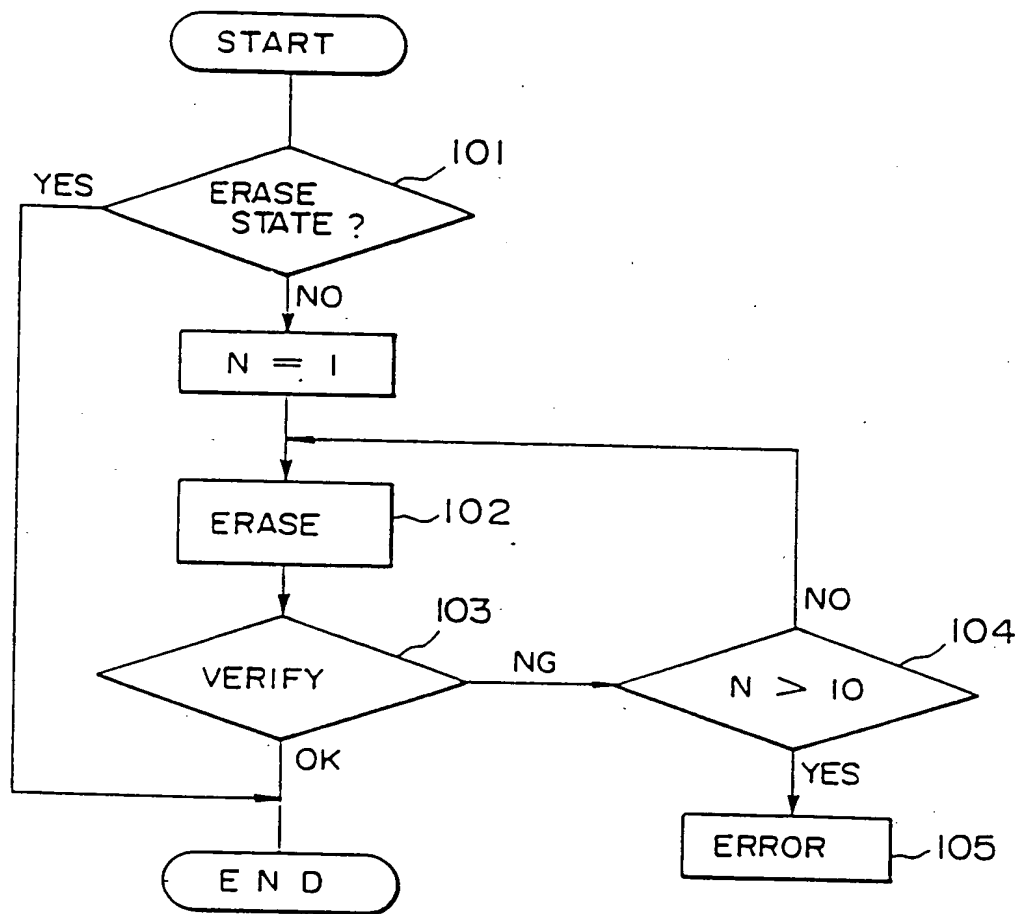


FIG. 52

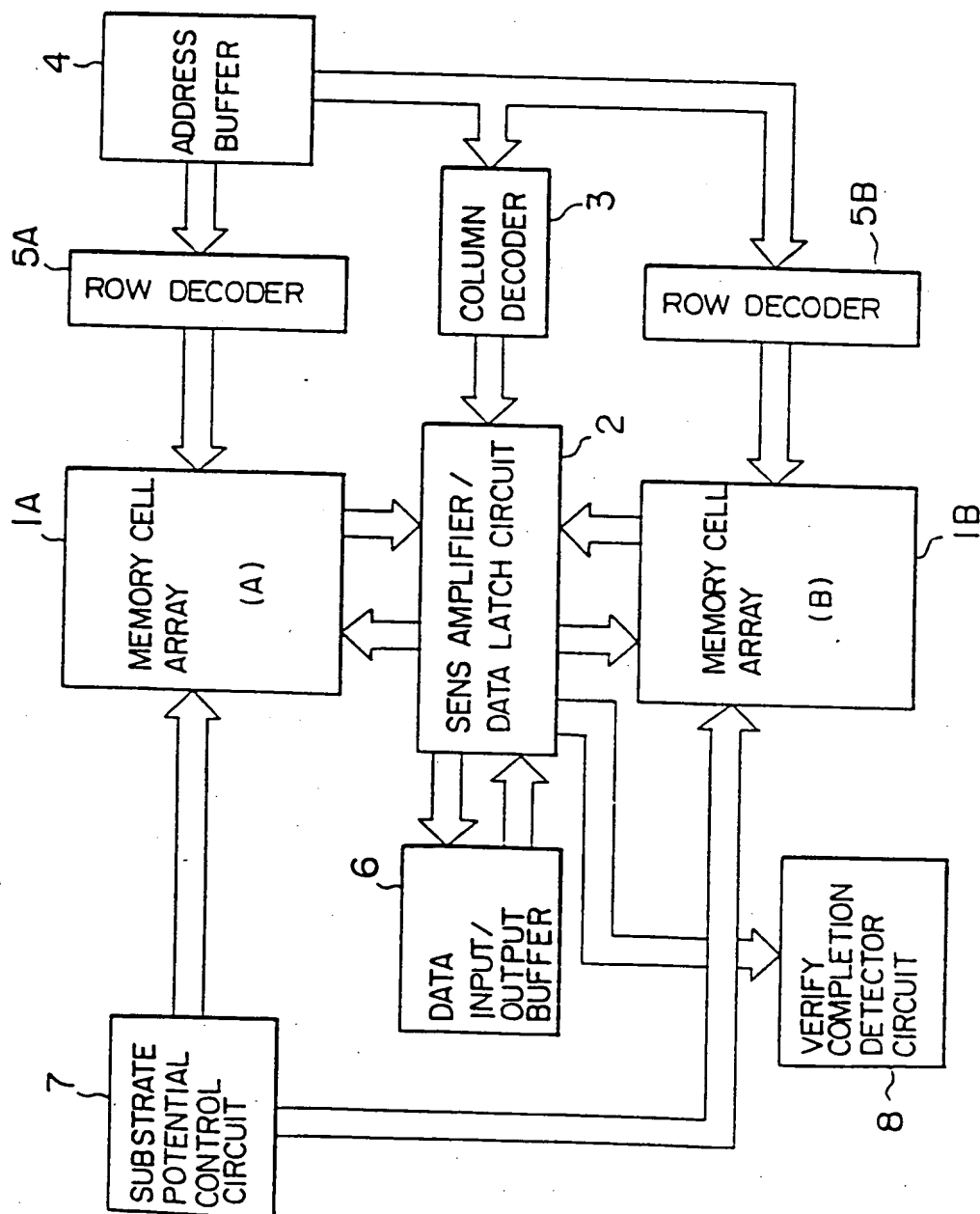


FIG. 53

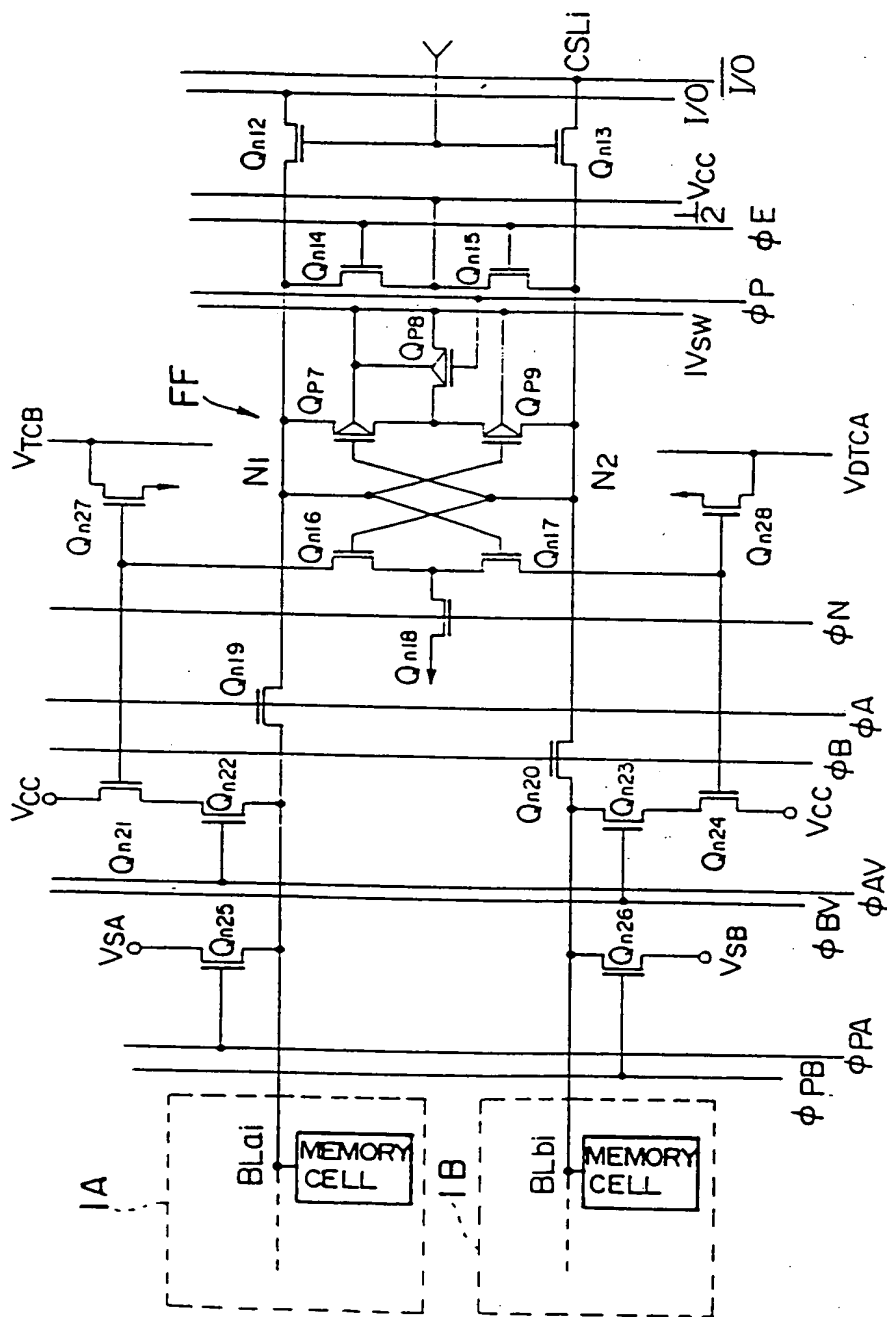


FIG. 54

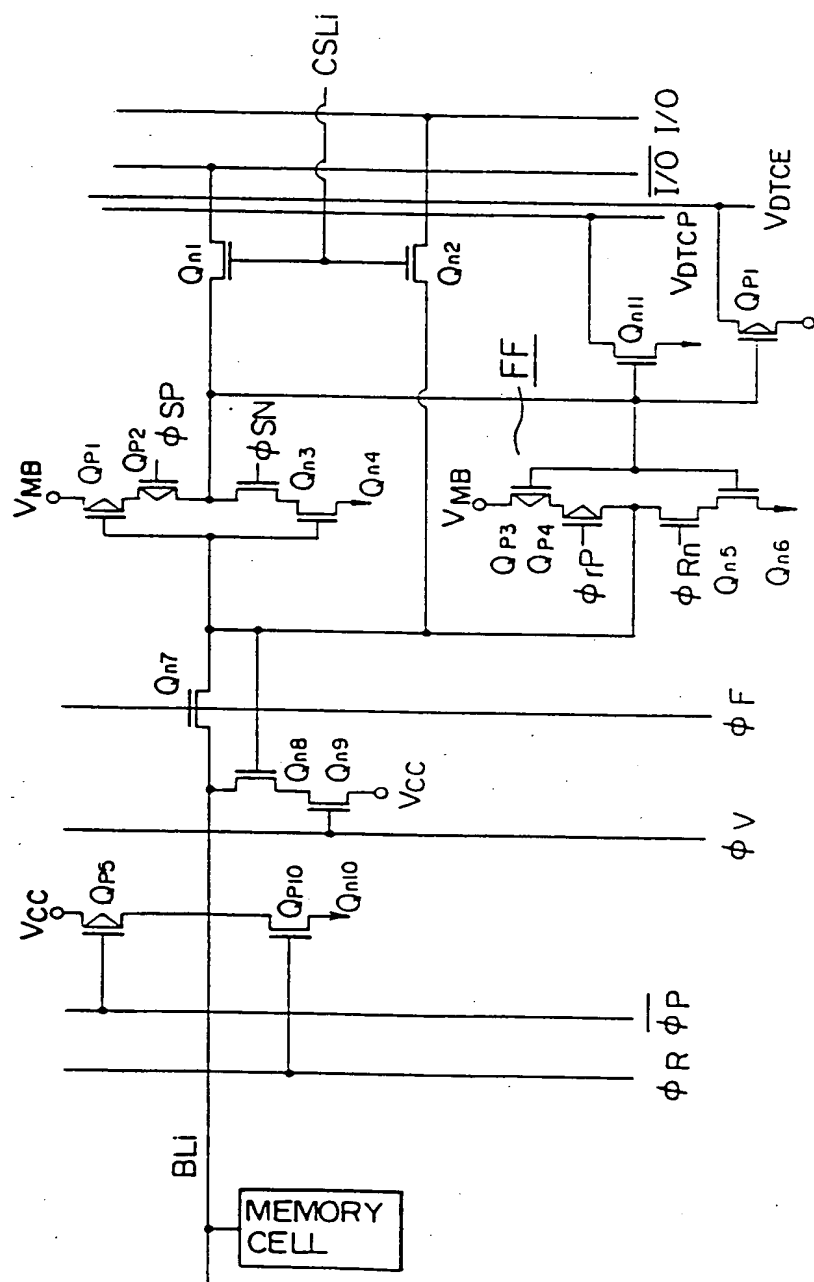


FIG. 55

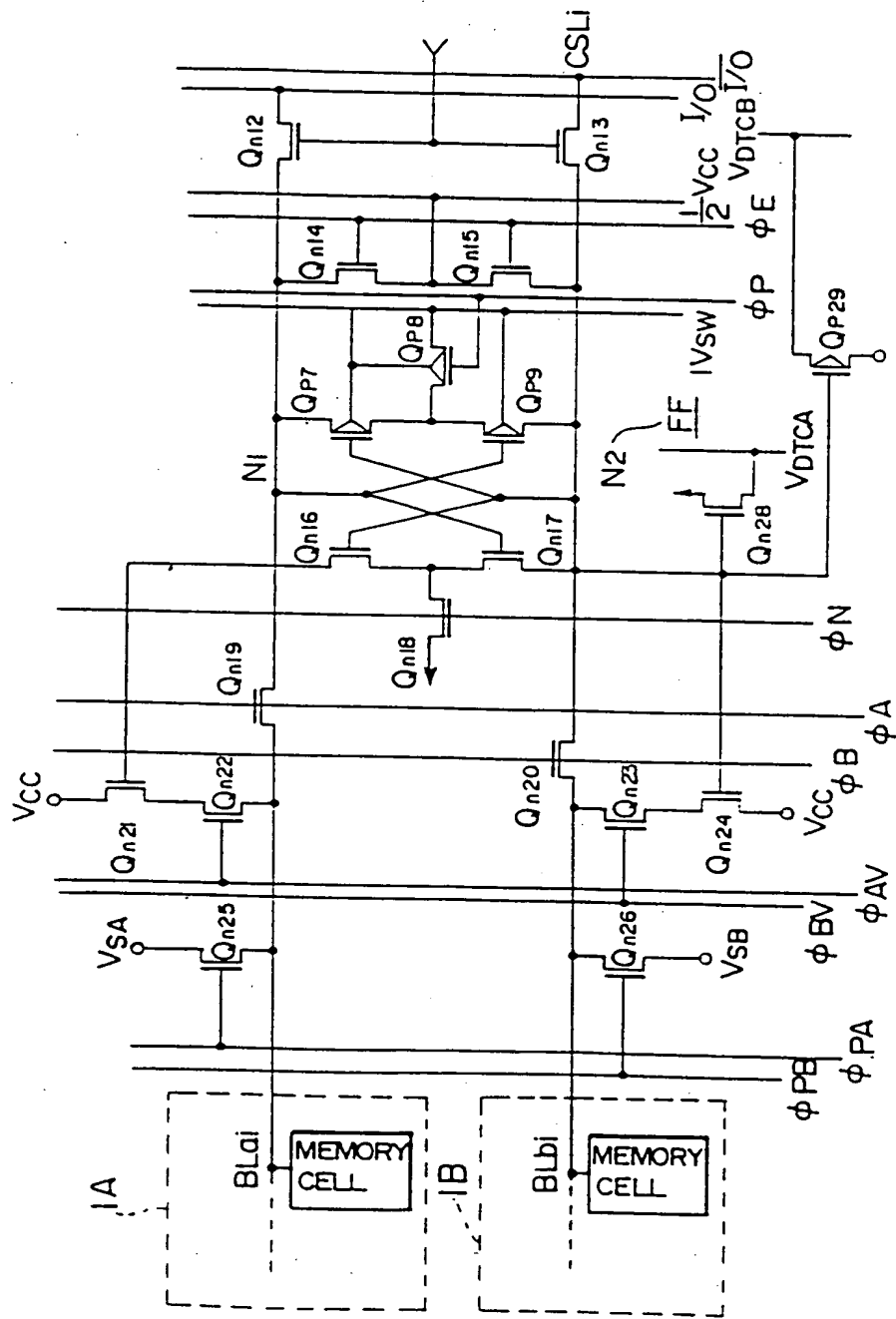


FIG. 56

TO CELL WELL)

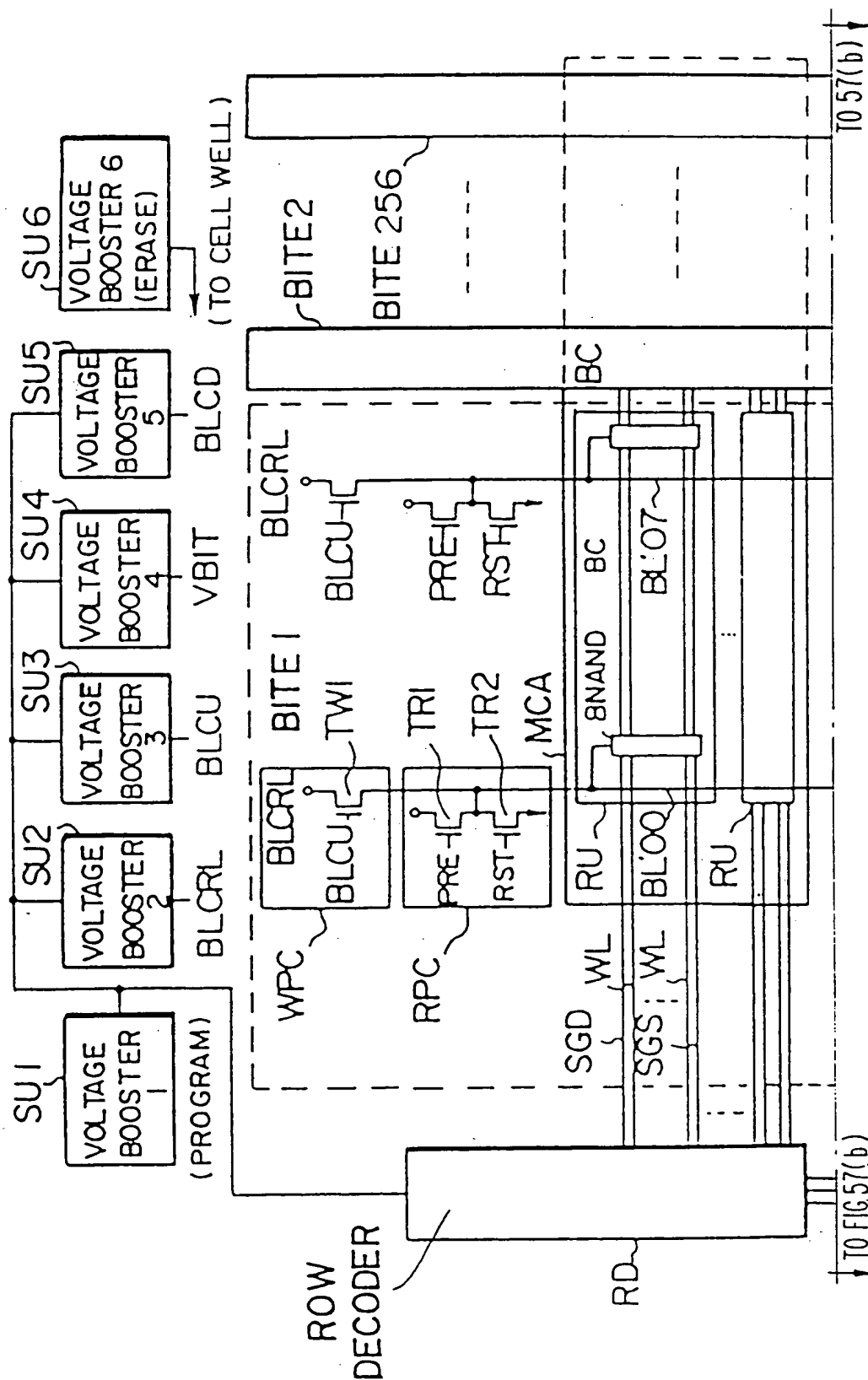


FIG. 57(b)

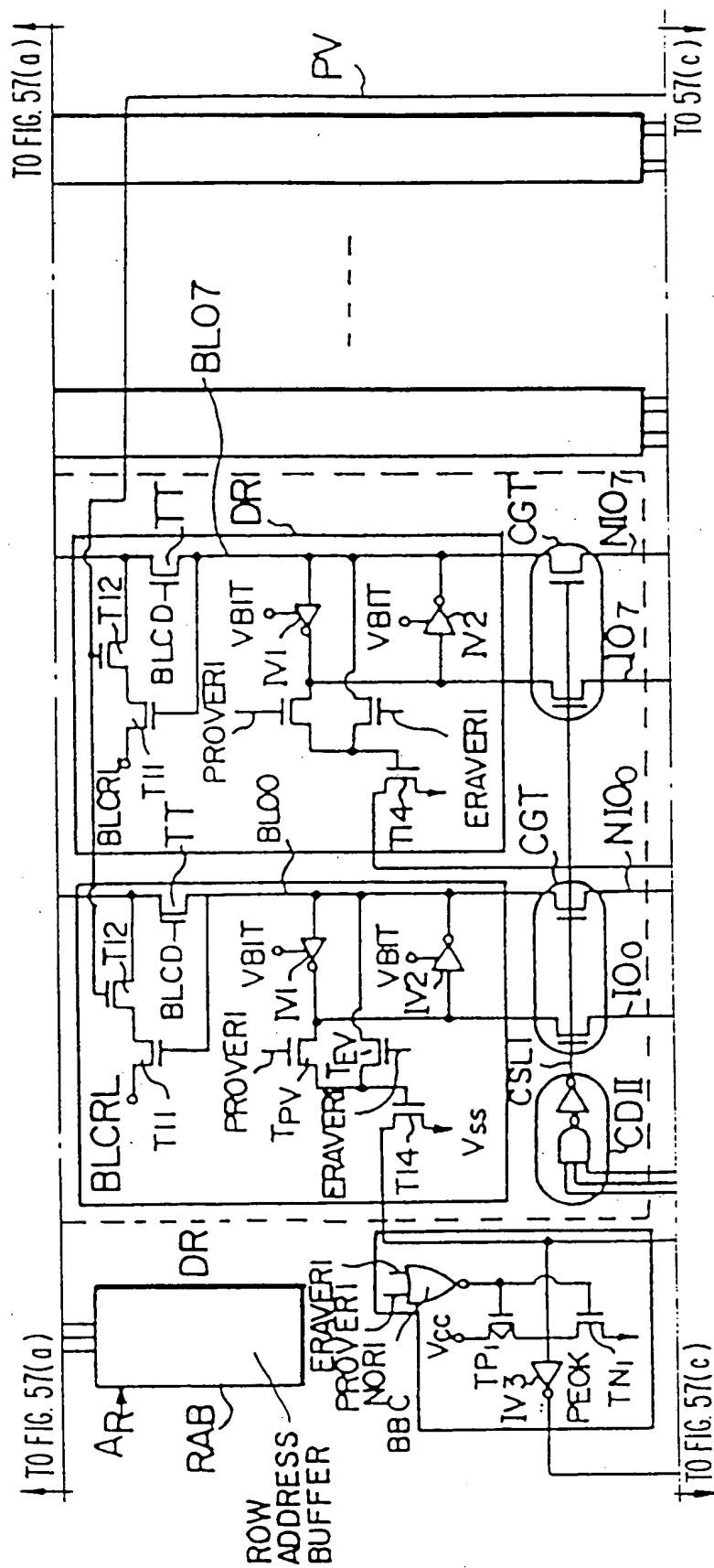
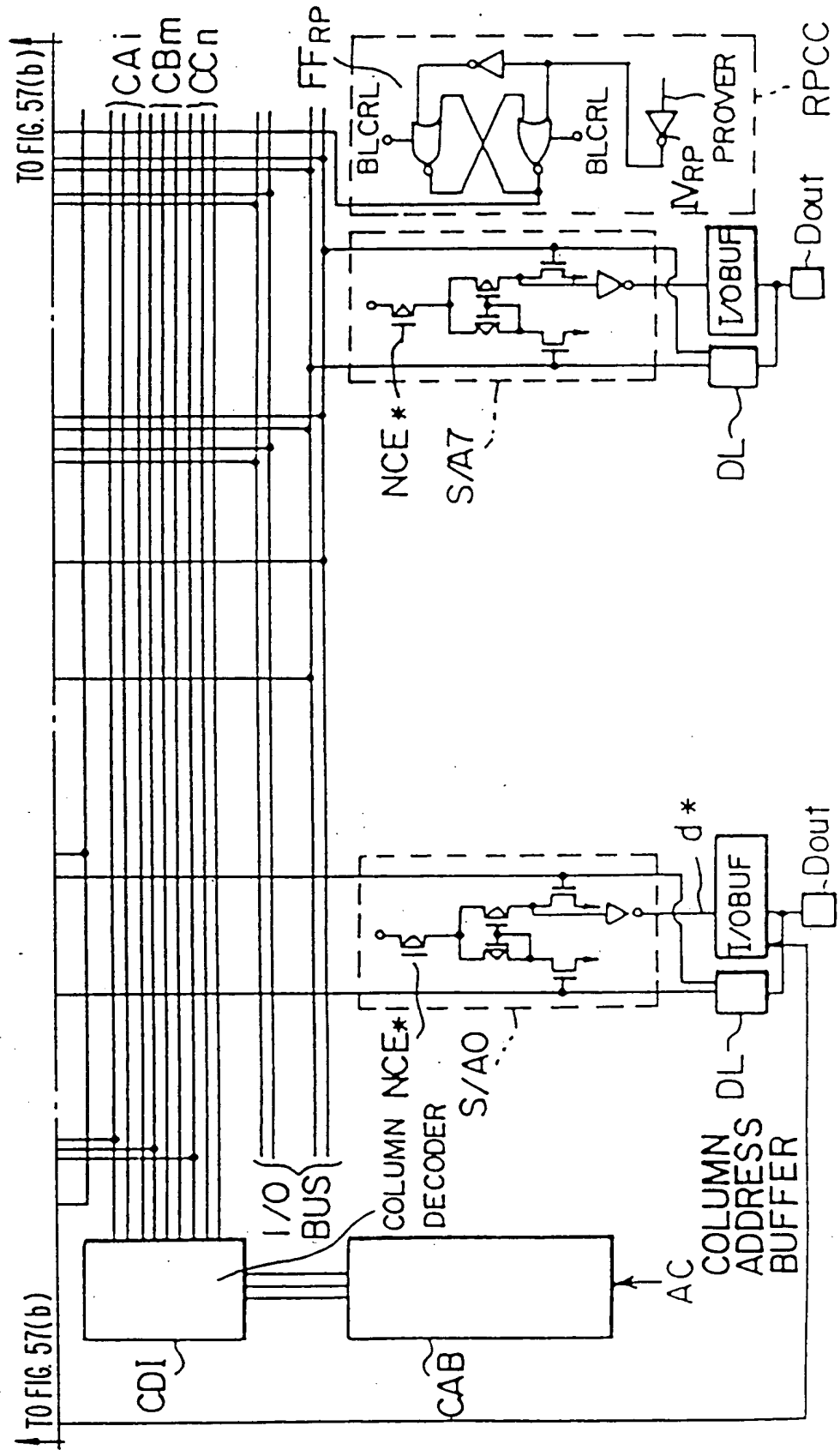


FIG. 57(c)



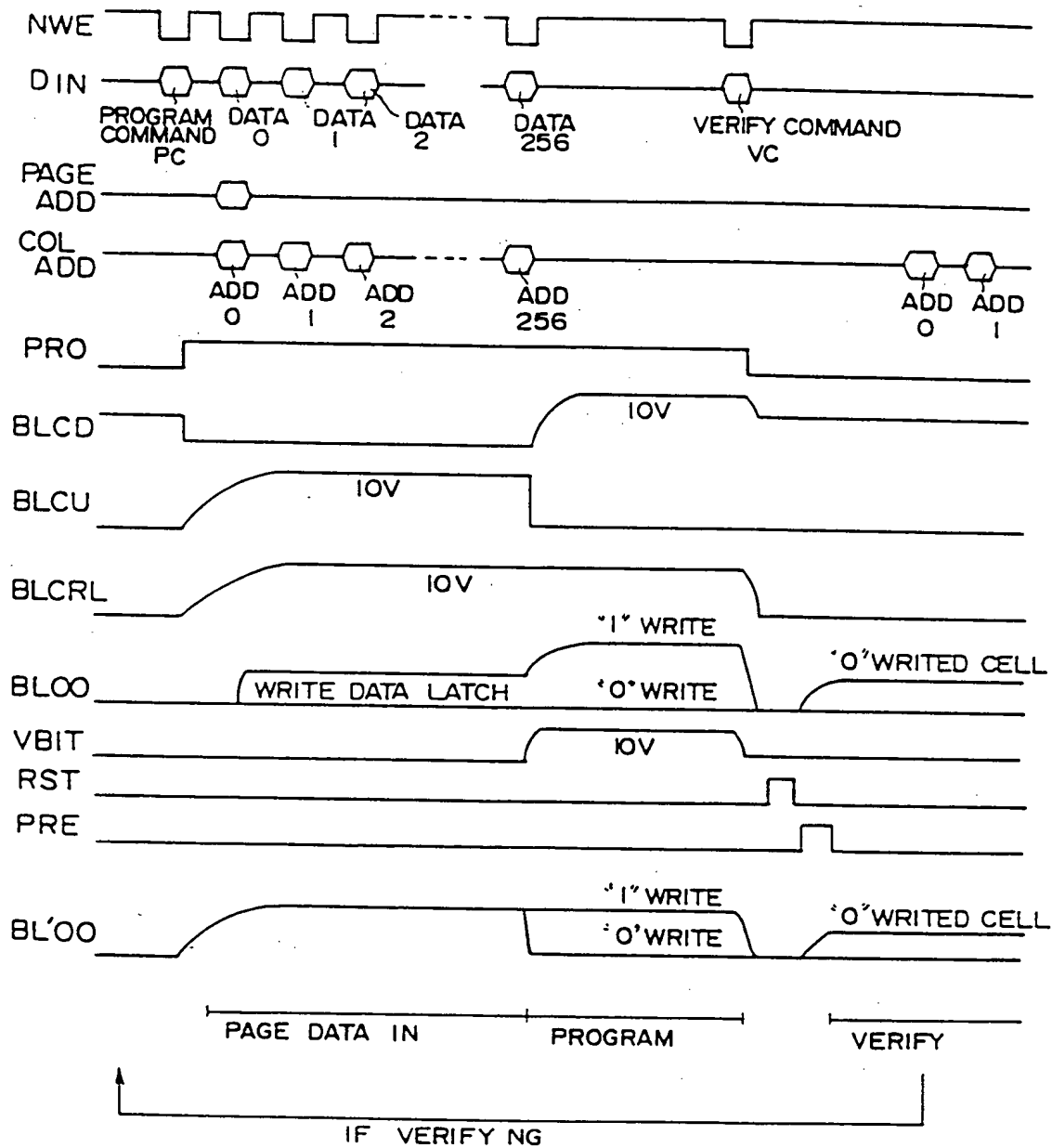


FIG. 58

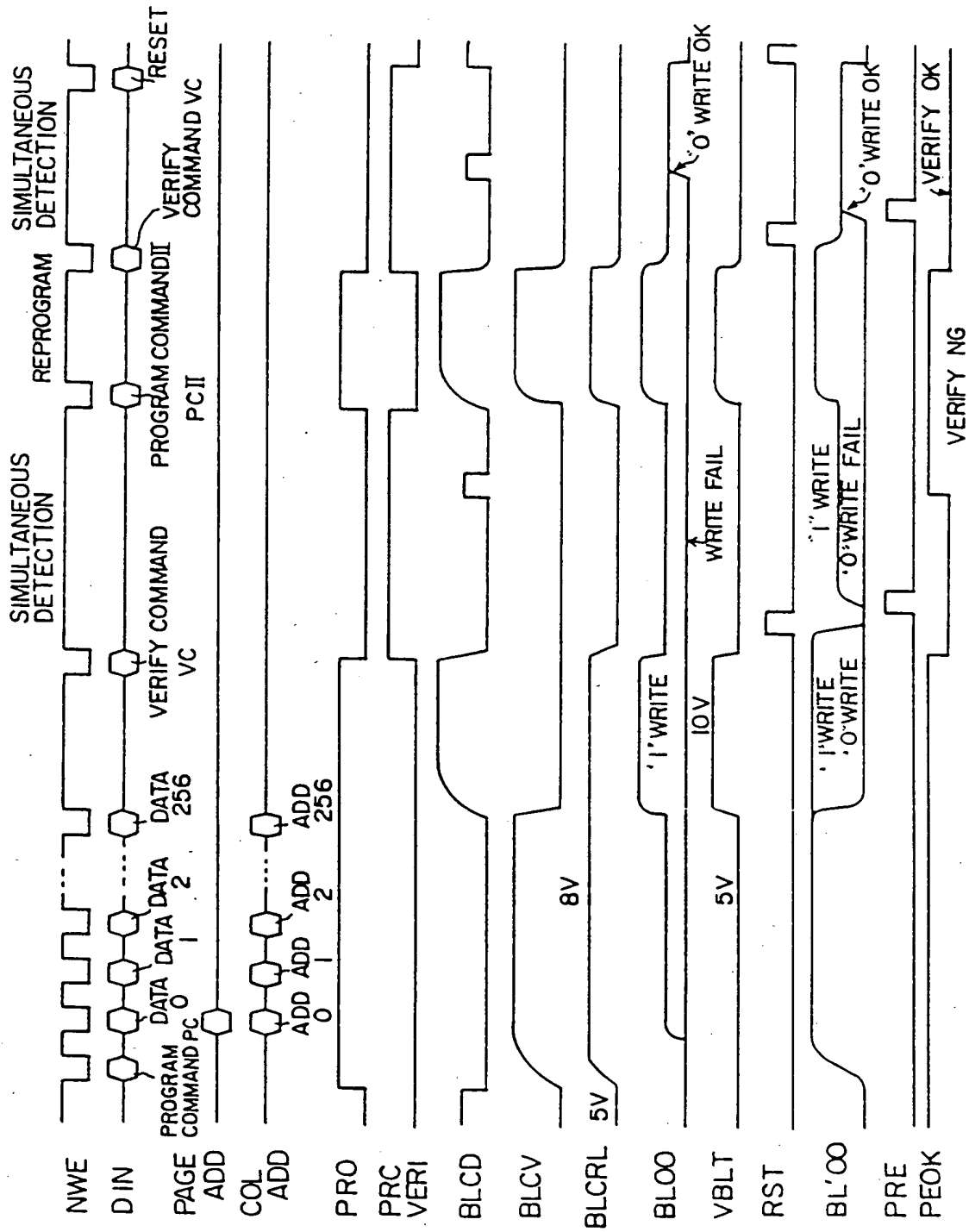


FIG. 59

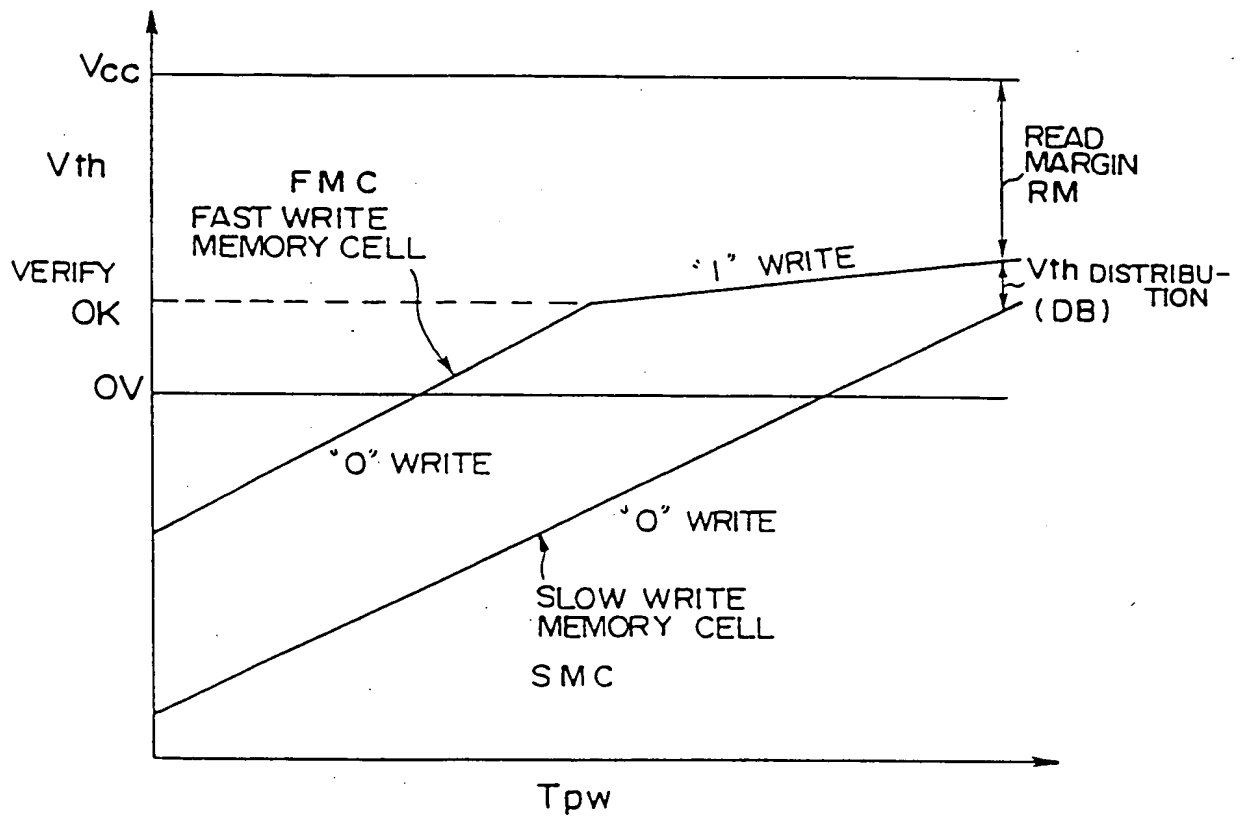


FIG. 60

(ERASE FLOW CHART)

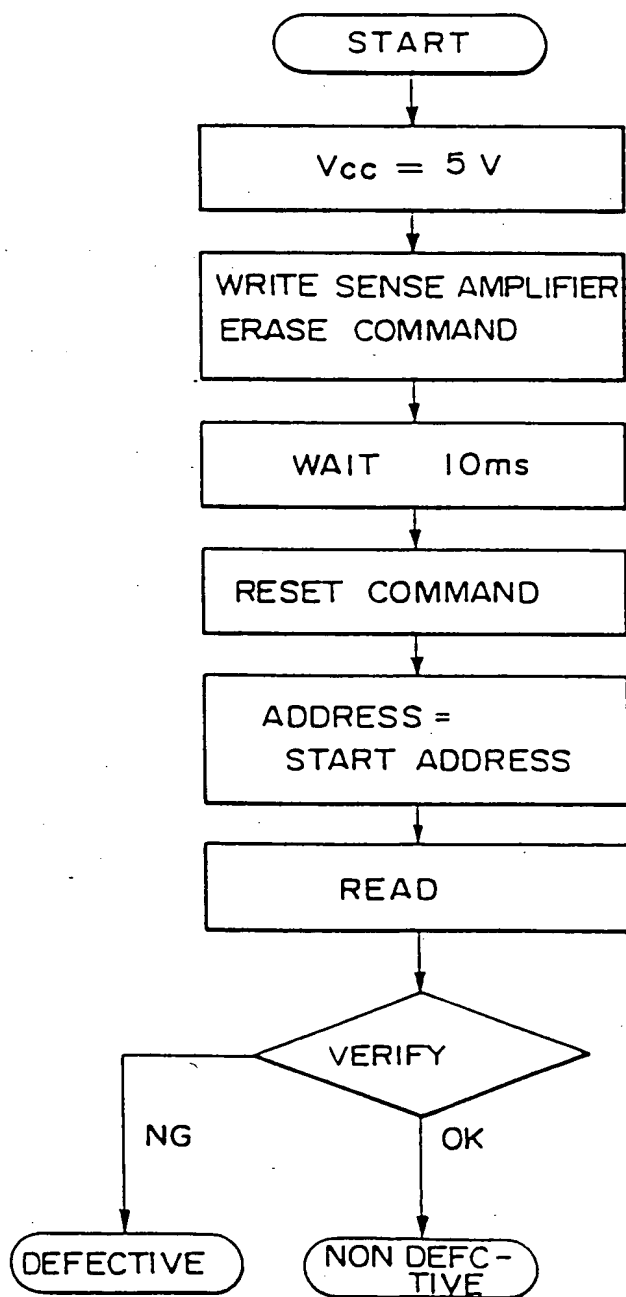


FIG. 61

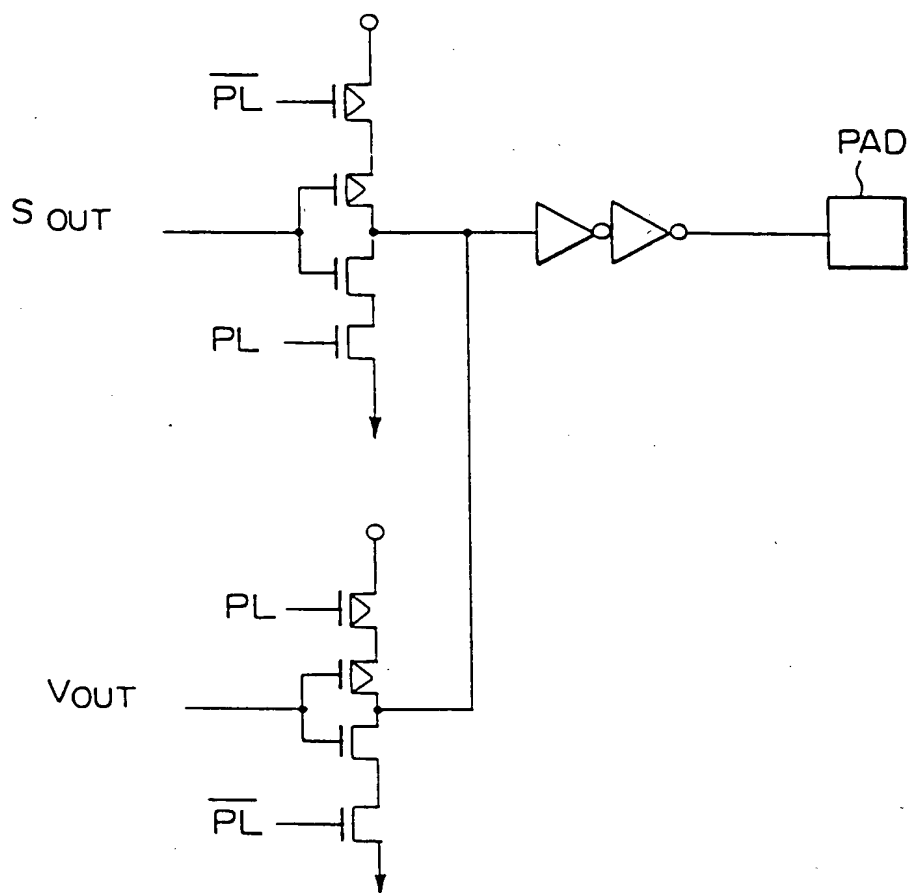


FIG.62

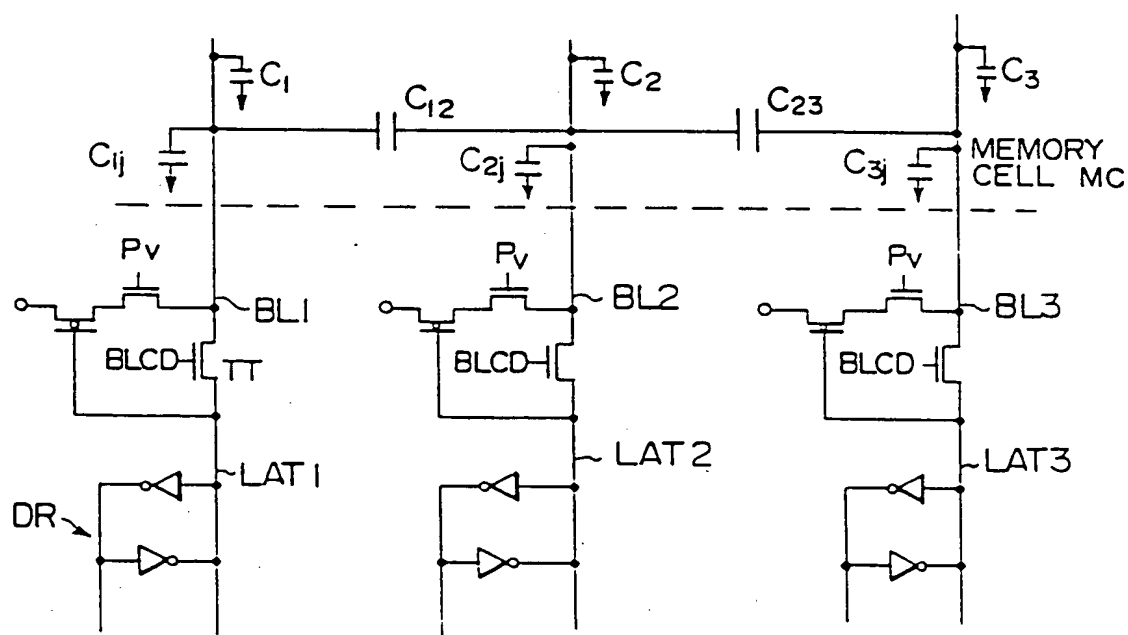


FIG. 63

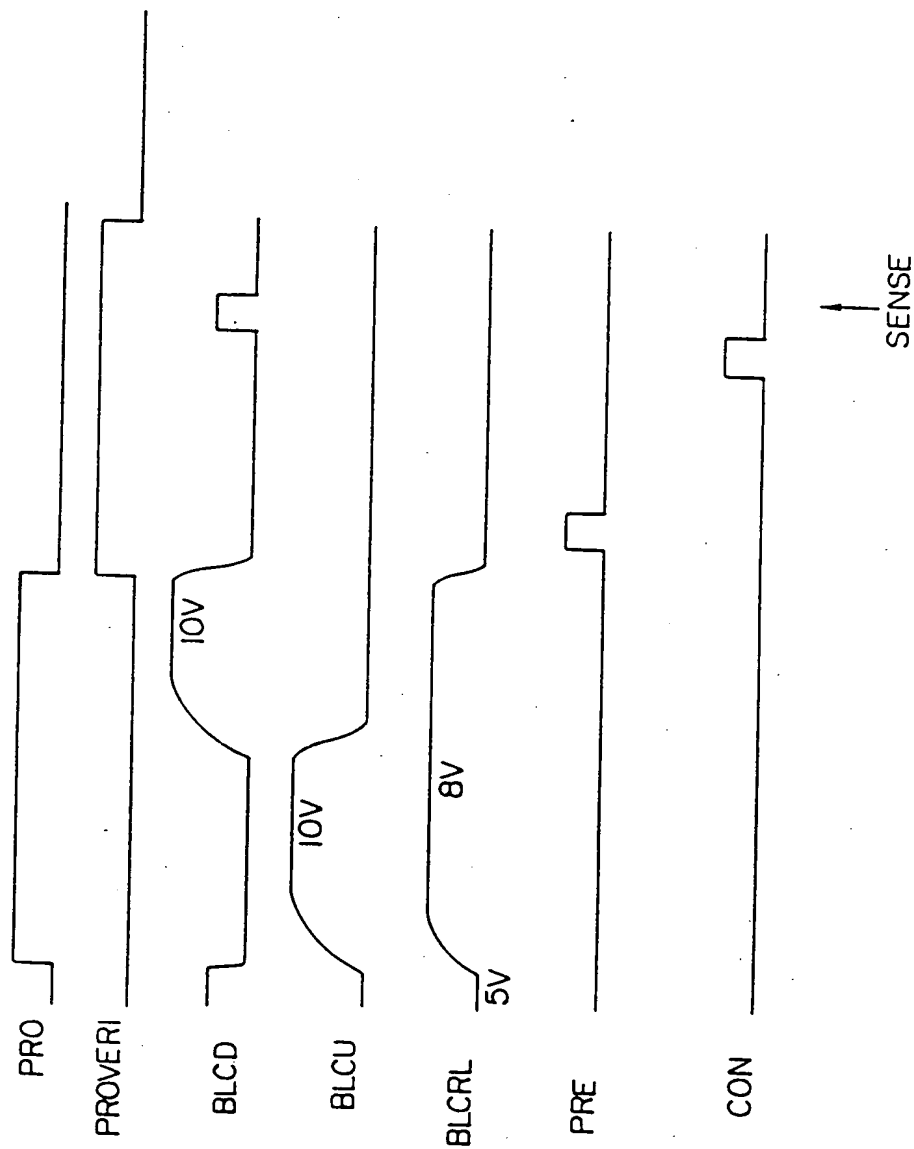


FIG. 64

FIG. 65(a)

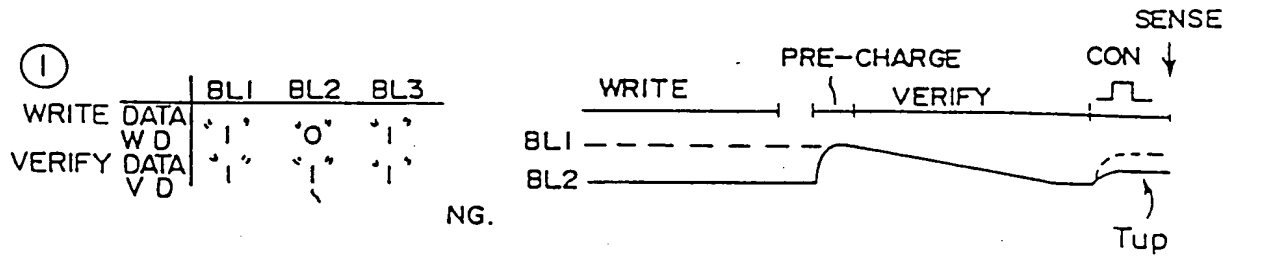


FIG. 65(b)

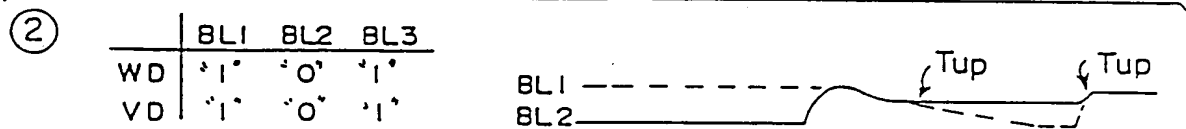


FIG. 65(c)

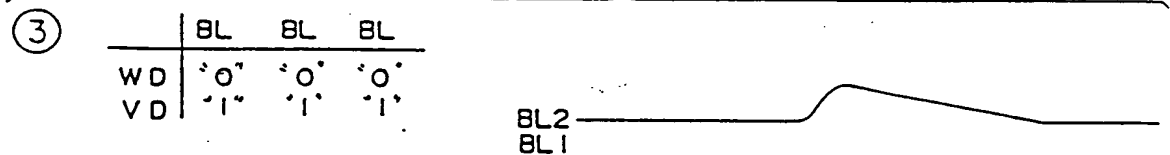


FIG. 65(d)

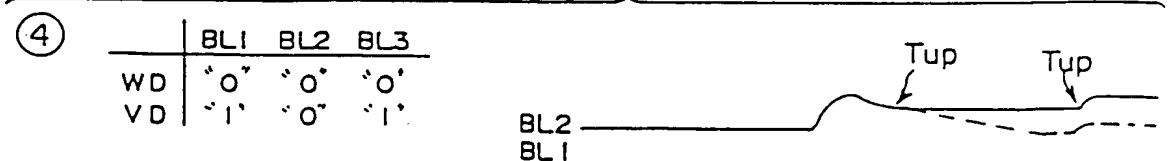


FIG. 65(e)

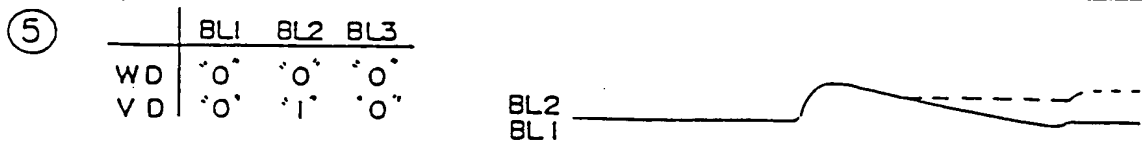


FIG. 65(f)

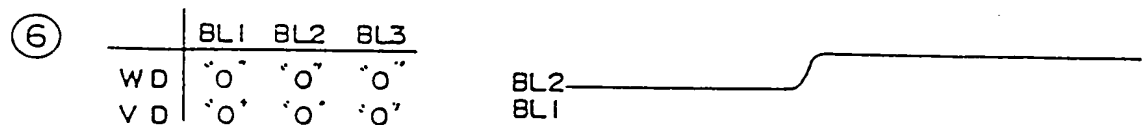


FIG. 65(g)

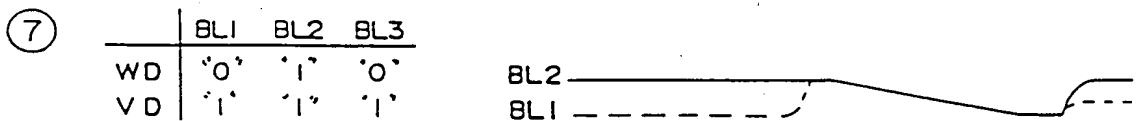


FIG. 65(h)

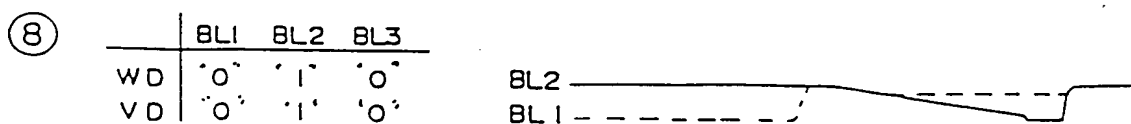


FIG. 66(a)

	BL1	BL2	BL3
WD	'1'	'0'	'1'
VD	'1'	'1'	'1'

FIG. 66(b)

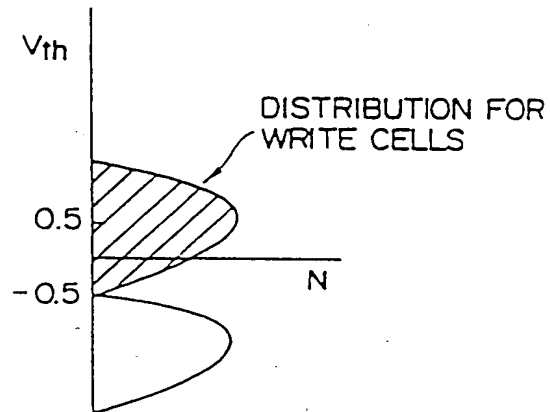
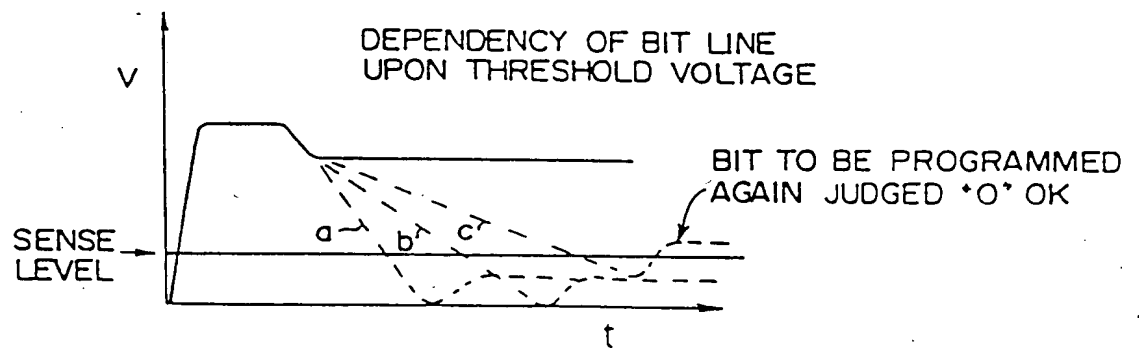


FIG. 66(c)



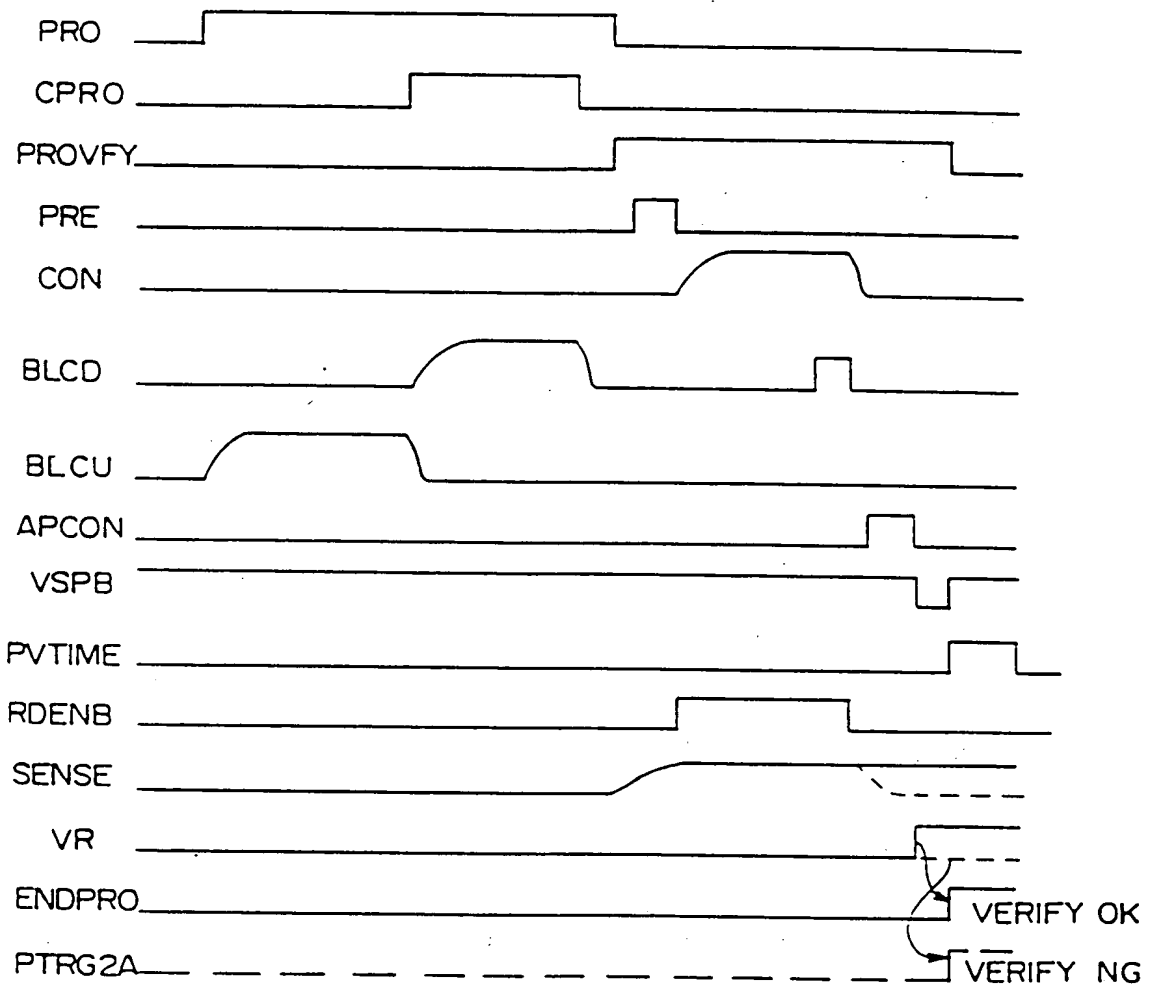


FIG. 67

FIG. 68(a)

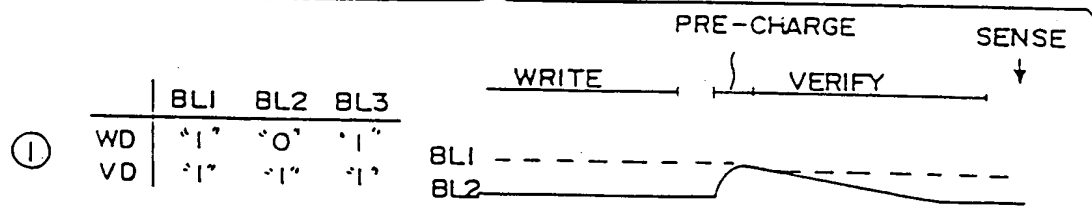


FIG. 68(b)

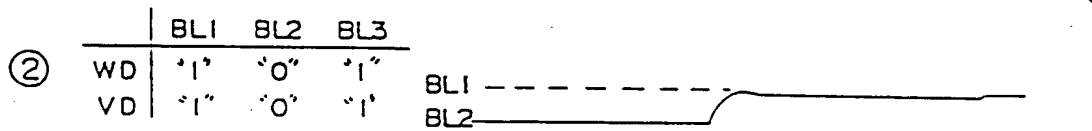


FIG. 68(c)

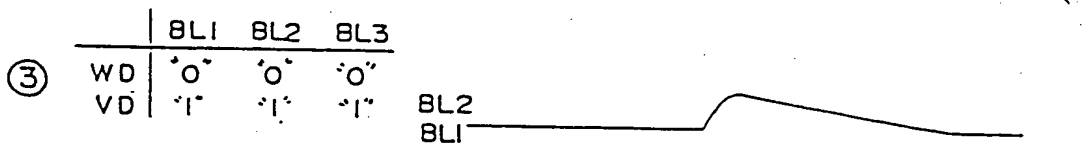


FIG. 68(d)



FIG. 68(e)

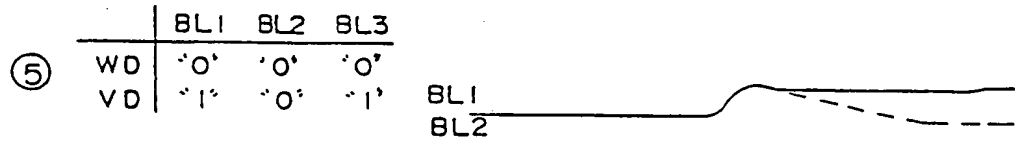


FIG. 68(f)

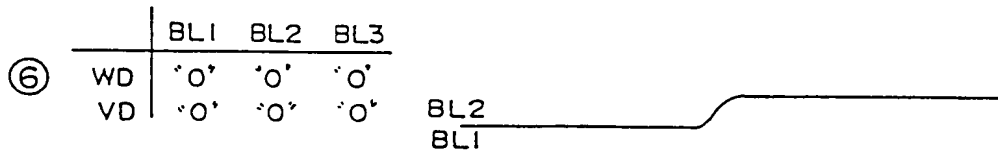


FIG. 68(g)

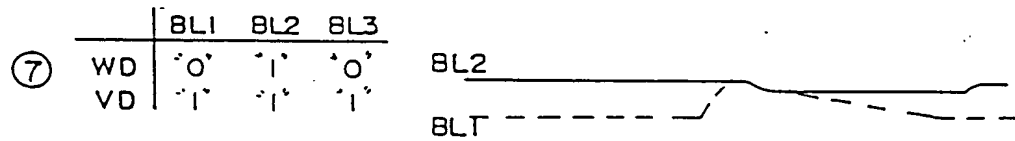


FIG. 68(h)

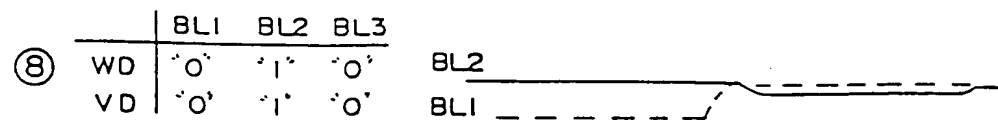


FIG. 69(a)

	BL1	BL2	BL3
WD	1	0	1
VD	1	1	1

FIG. 69(b)

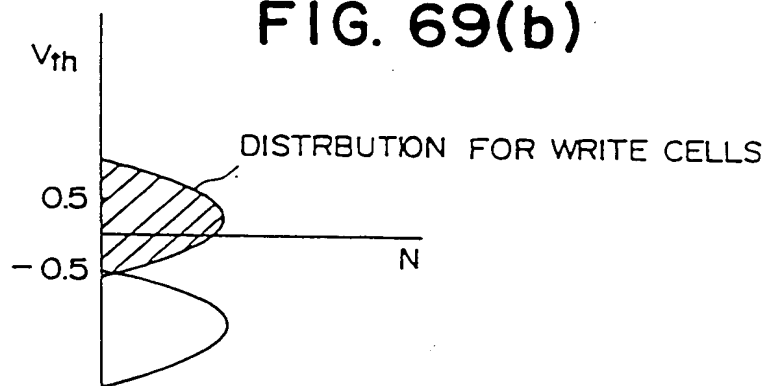


FIG. 69(c)

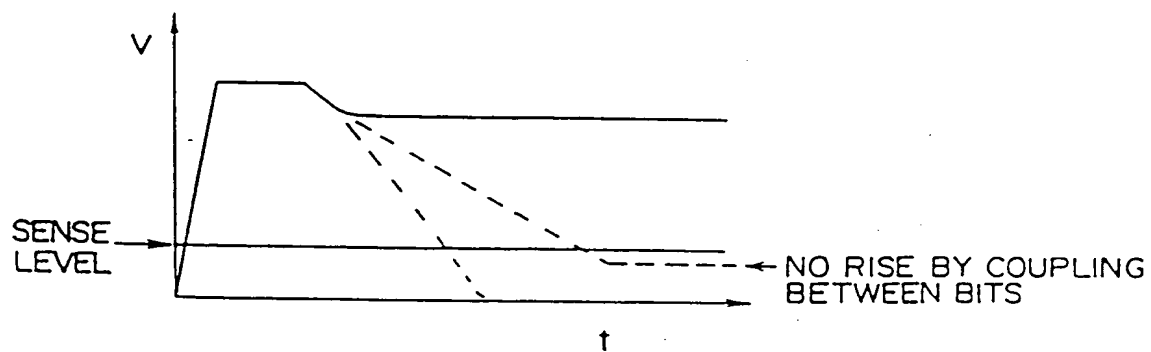


FIG. 70(a)

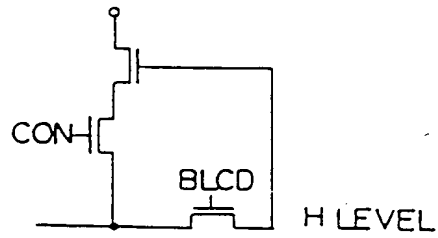


FIG. 70(b)

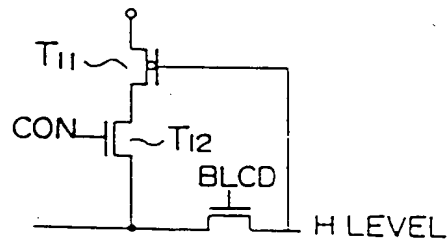
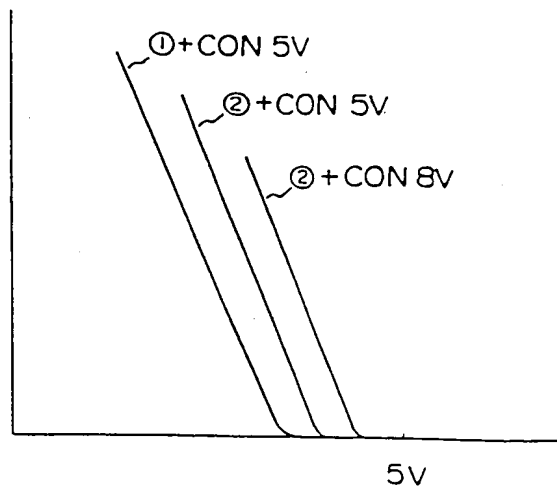


FIG. 70(c)



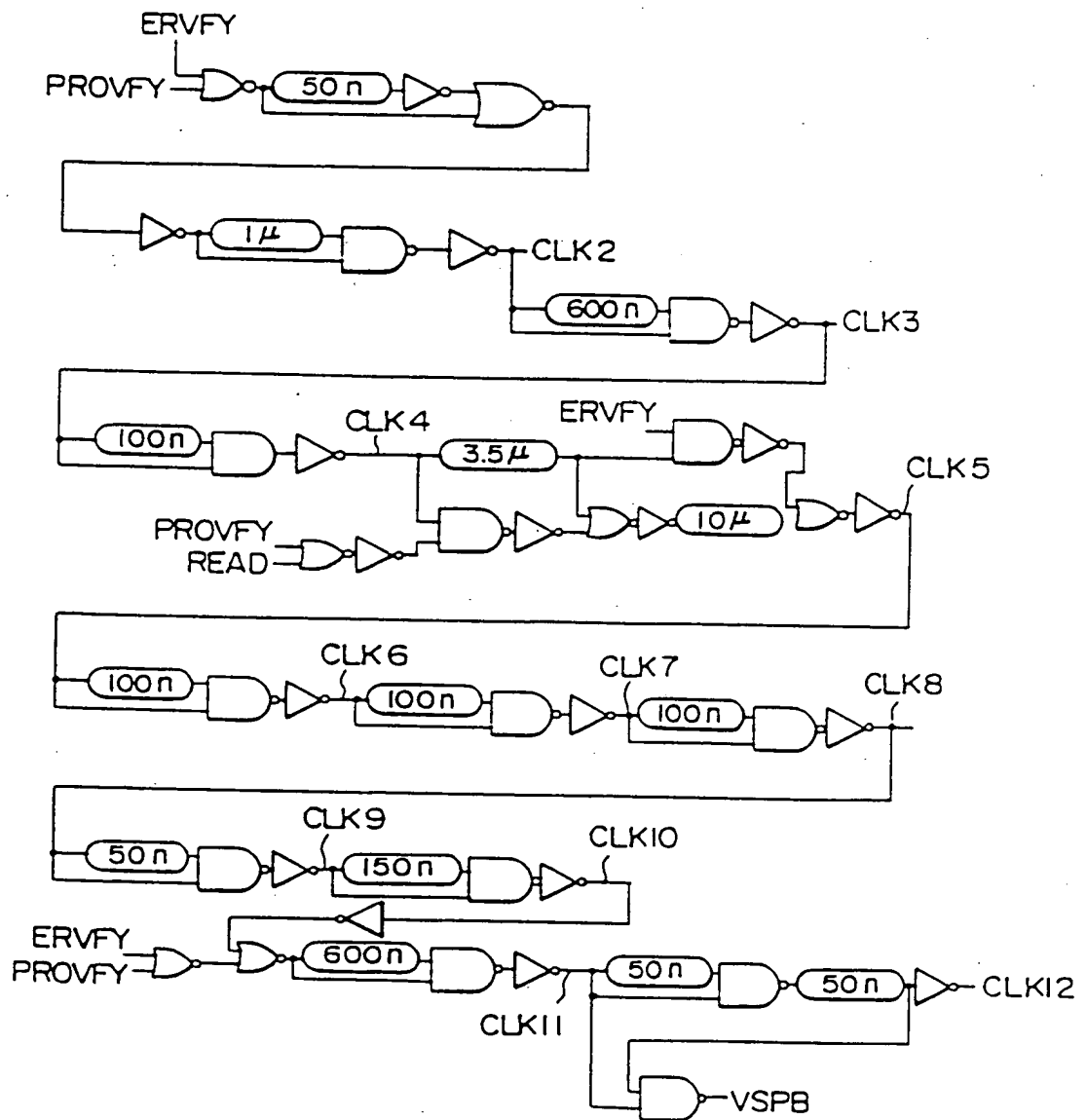


FIG. 71

000001-444444

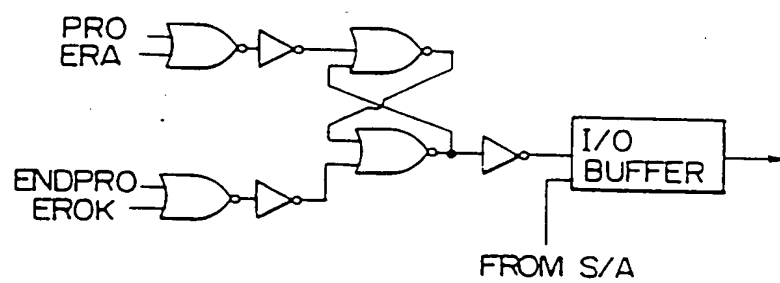


FIG. 73

FIG. 74(a)

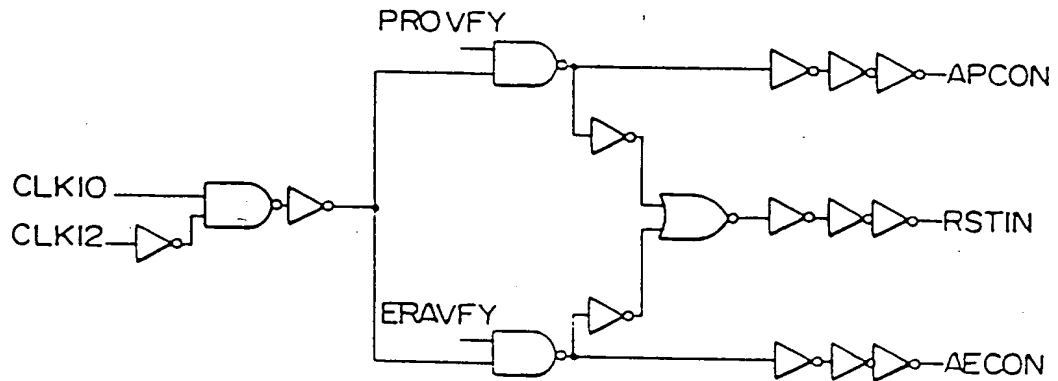


FIG. 74(b)

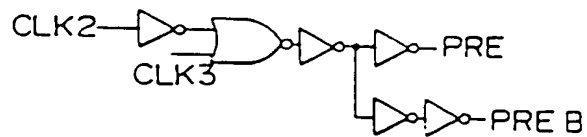
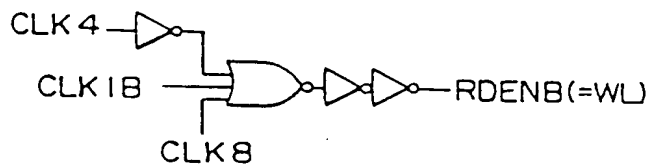


FIG. 74(c)



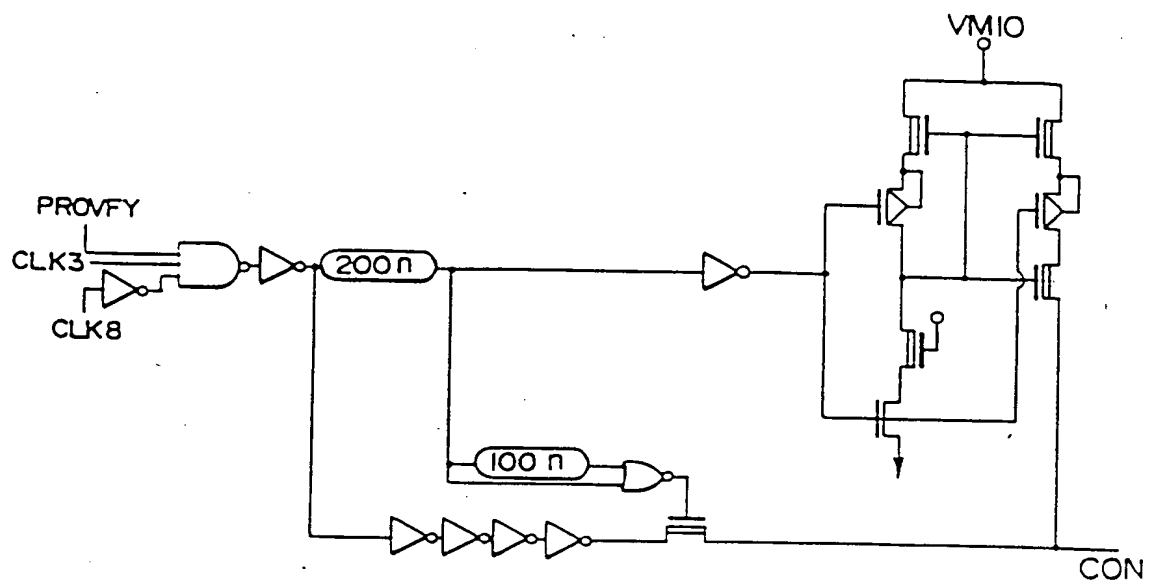


FIG. 75

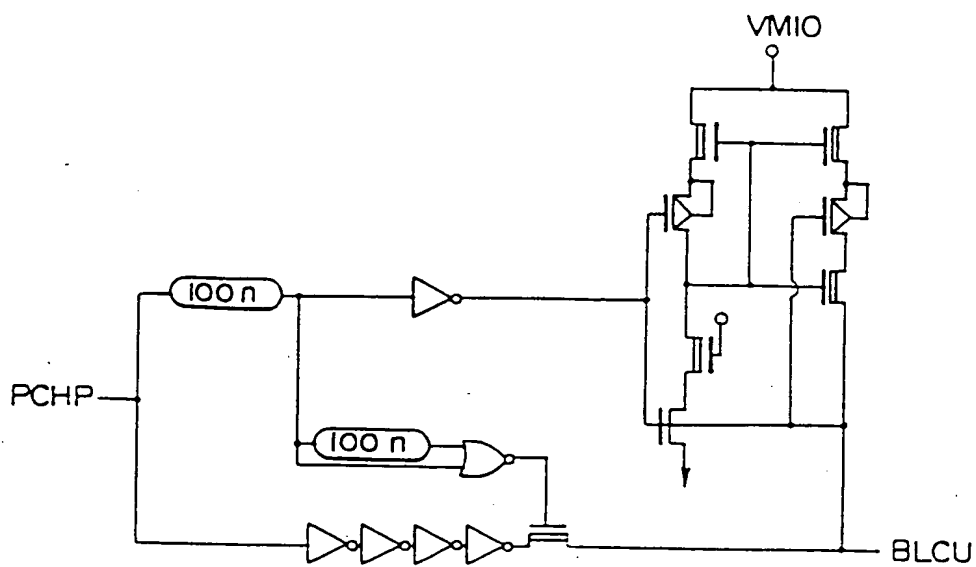


FIG. 76

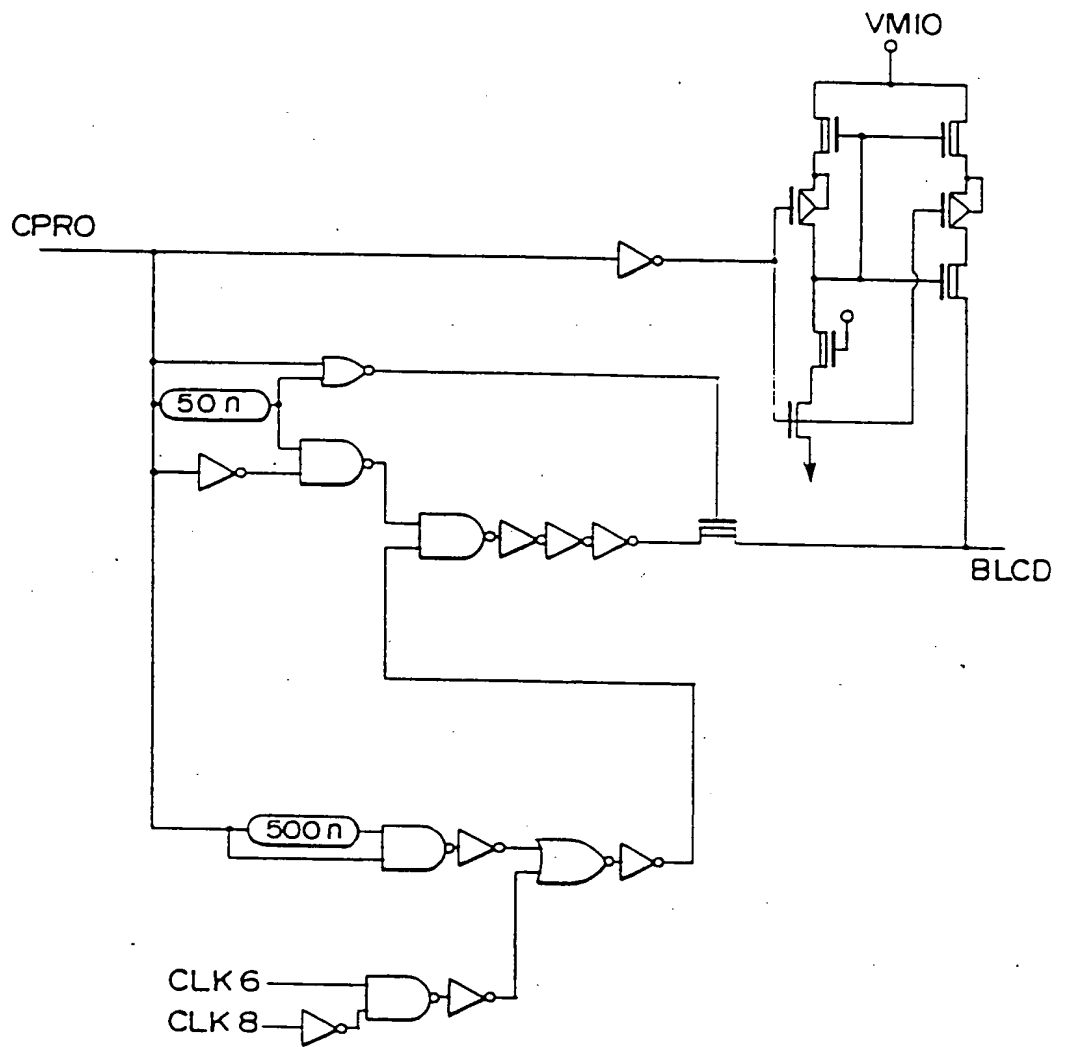


FIG.77

FIG. 78(a)

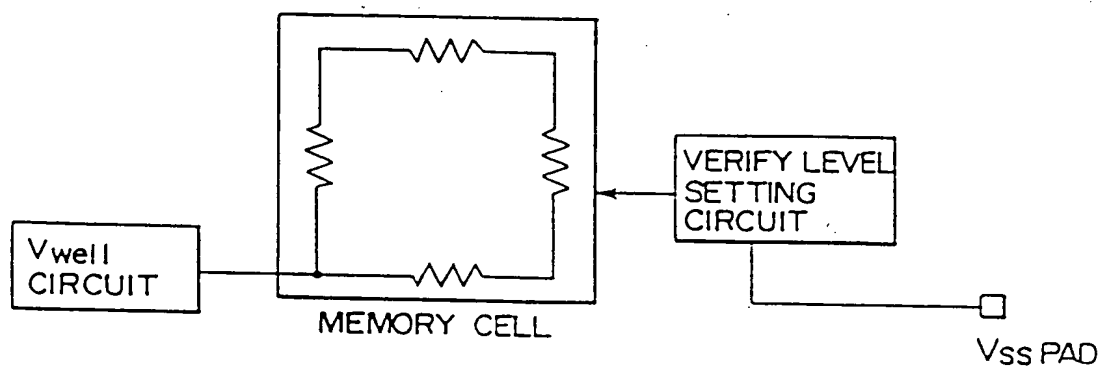
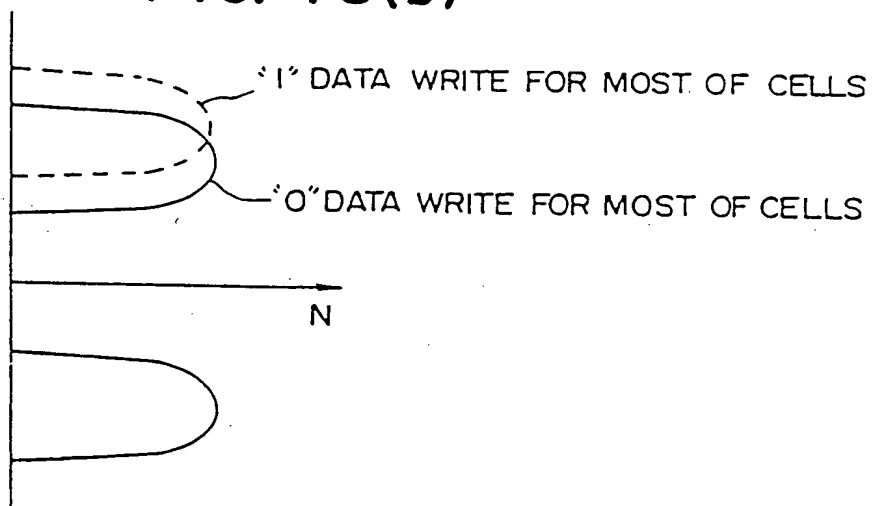


FIG. 78(b)



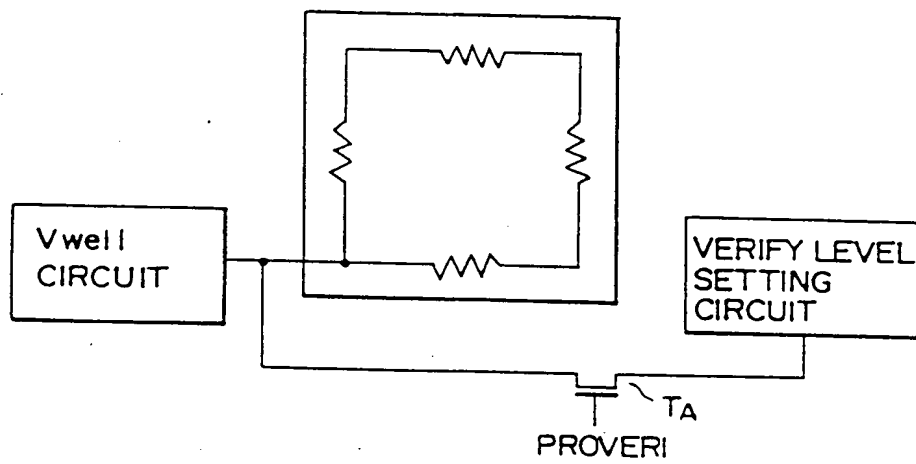


FIG.79

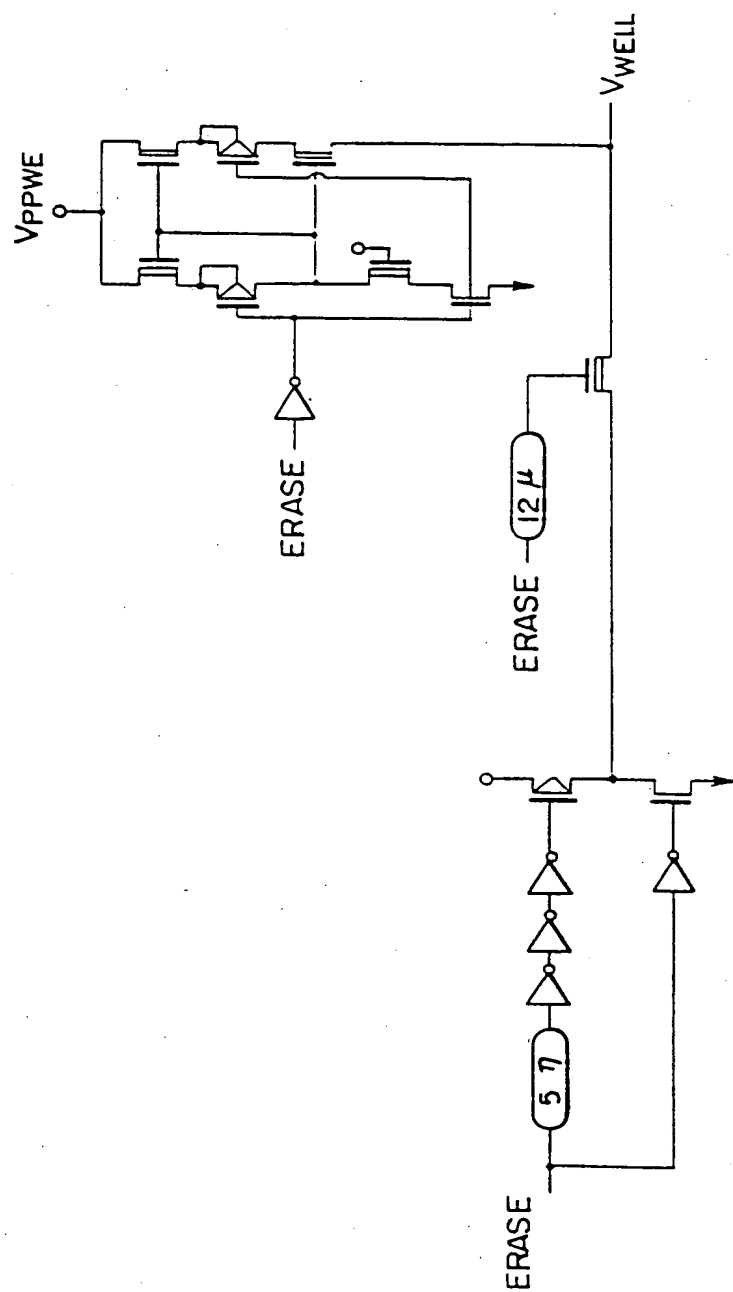


FIG. 81

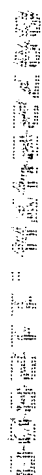


FIG. 82

WRITE DATA	0	0	1	1
VERIFY DATA	0	1	0	1
OUTPUT DATA AFTER COMPAR- ISON	0	1	1	0

FIG. 83

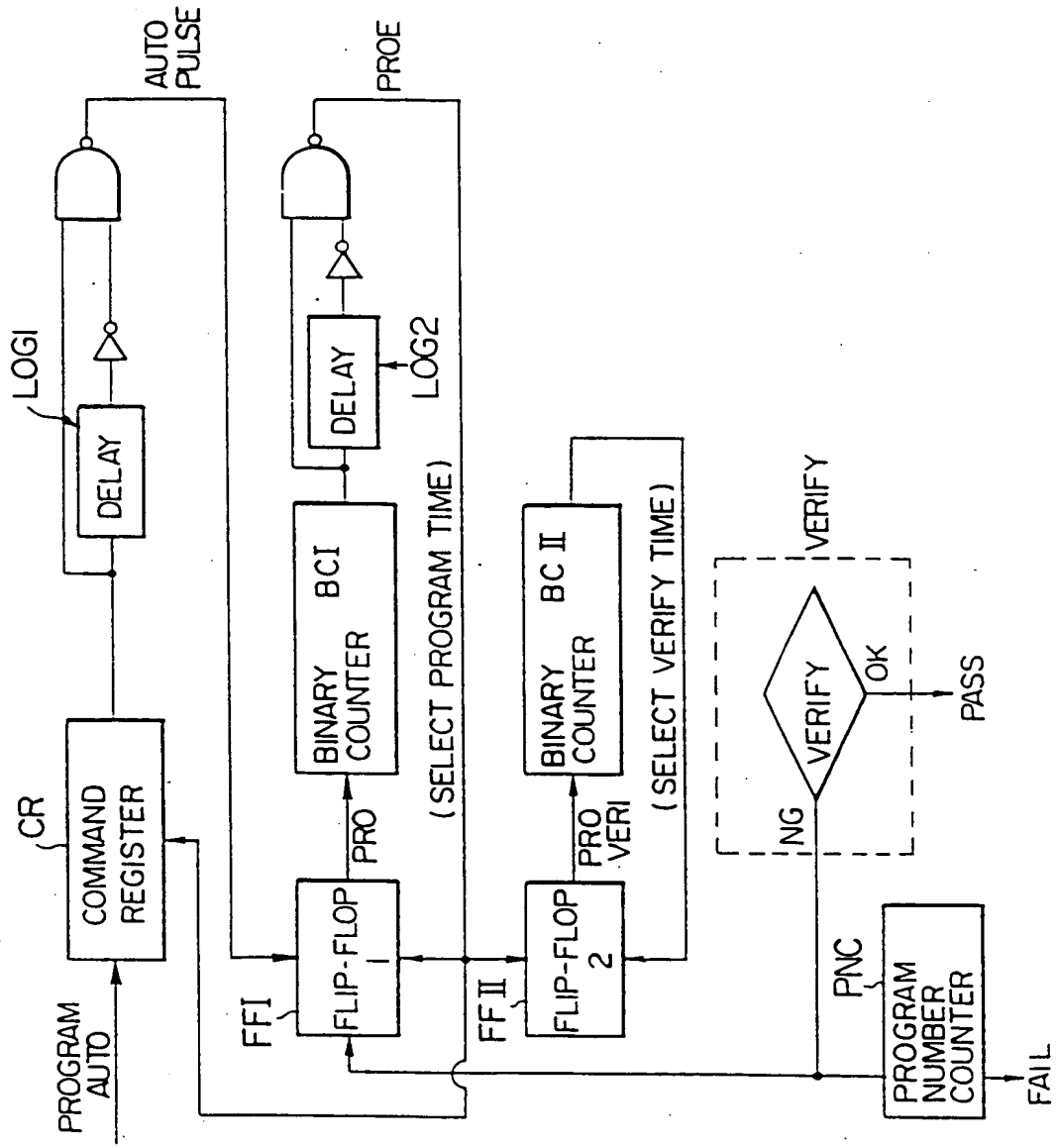


FIG. 84

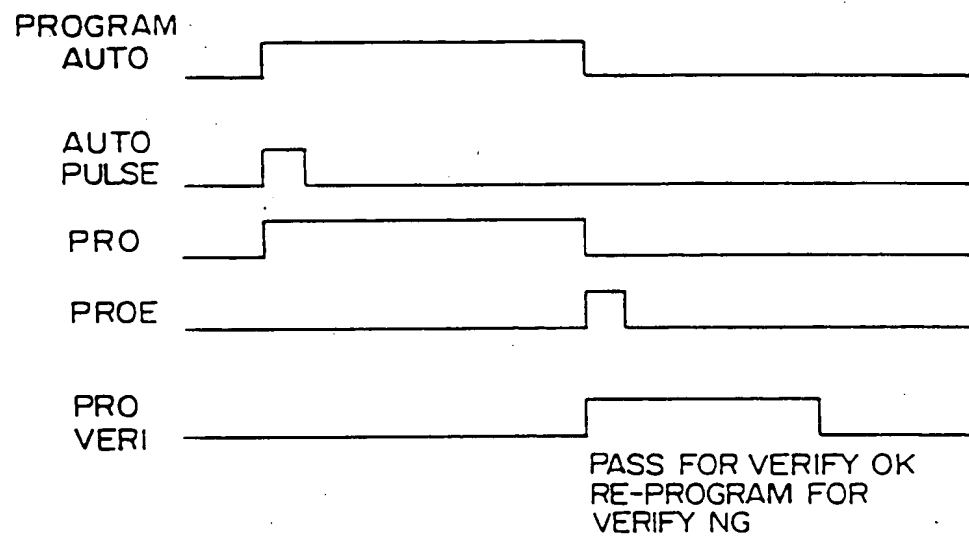


FIG. 85

PROGRAM & PROGRAM VERIFY OPERATIONS

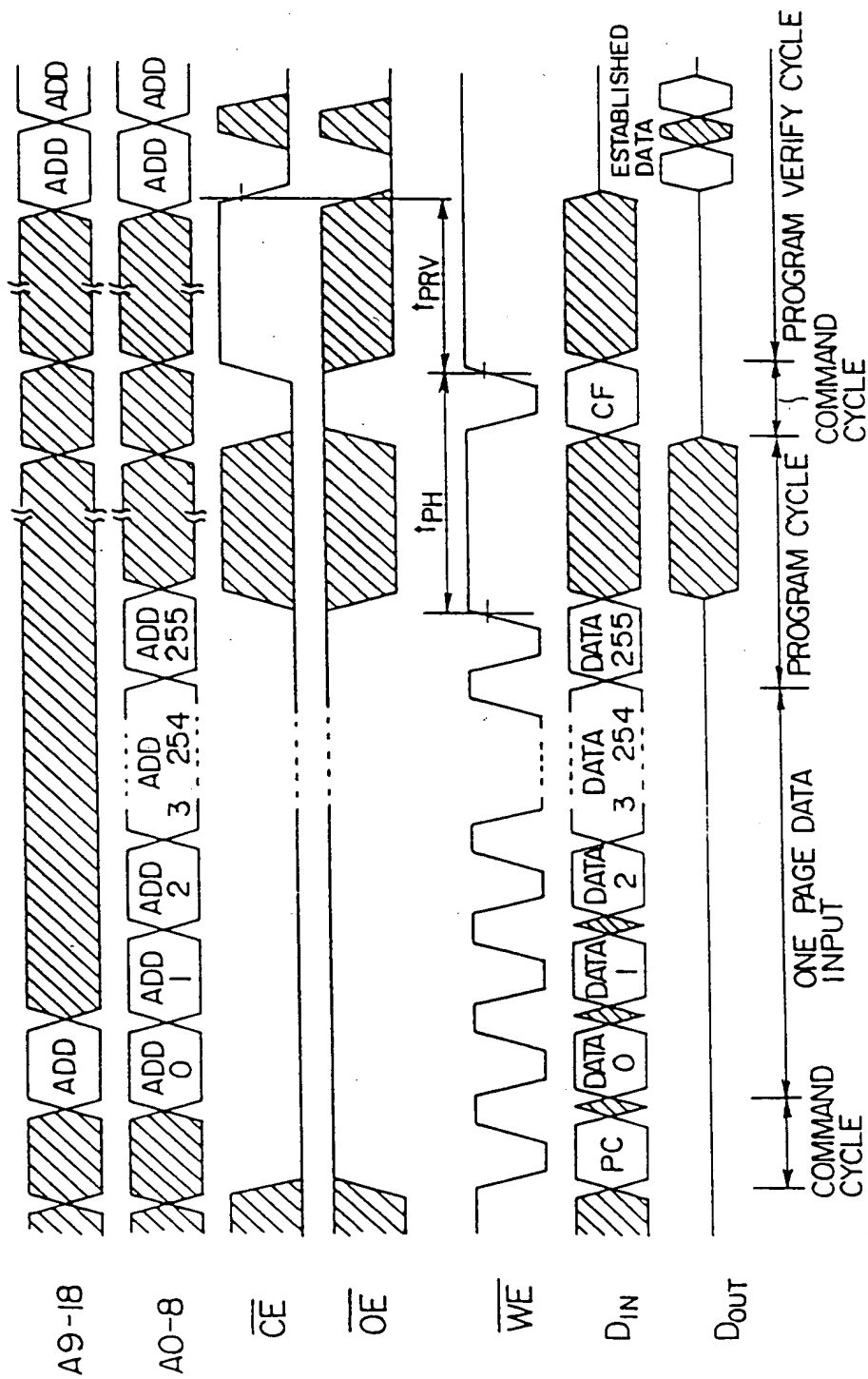


FIG. 86

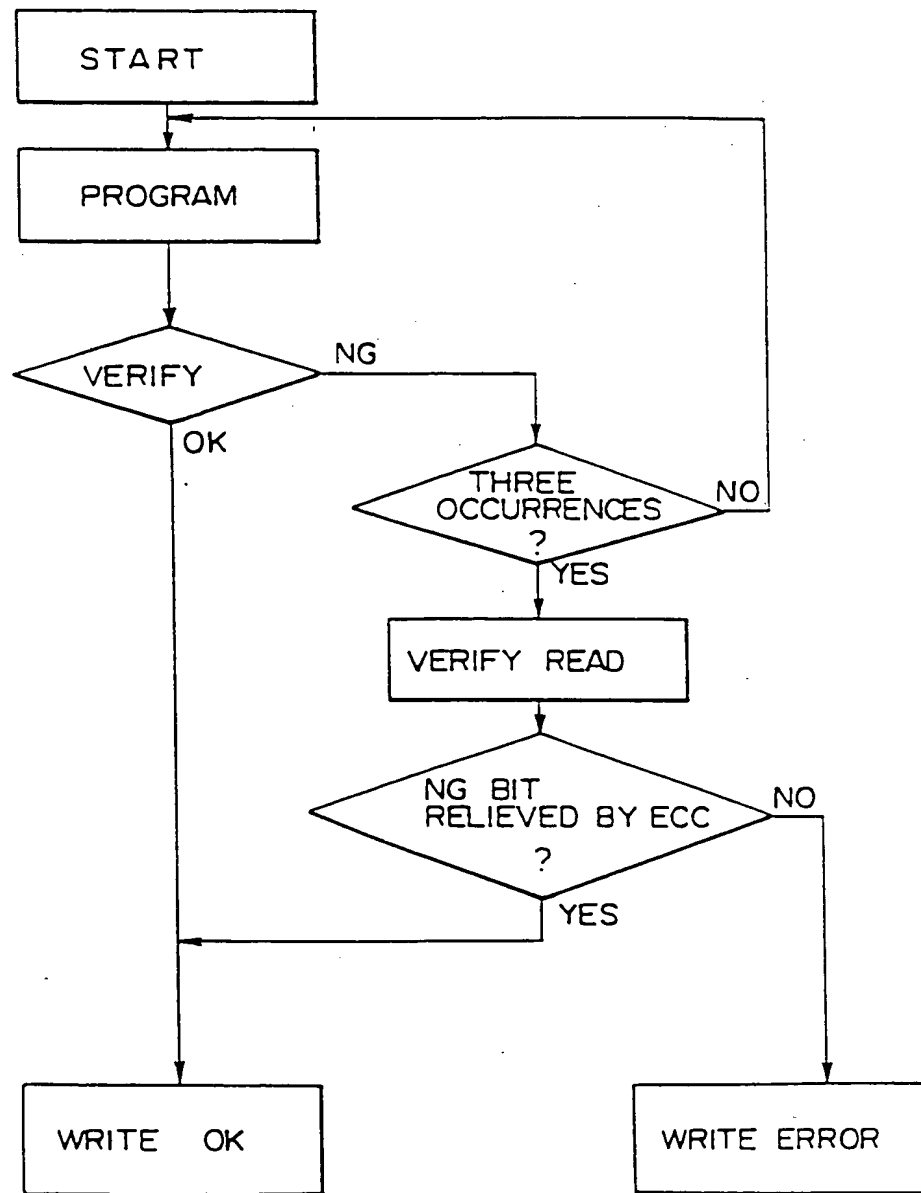


FIG. 87

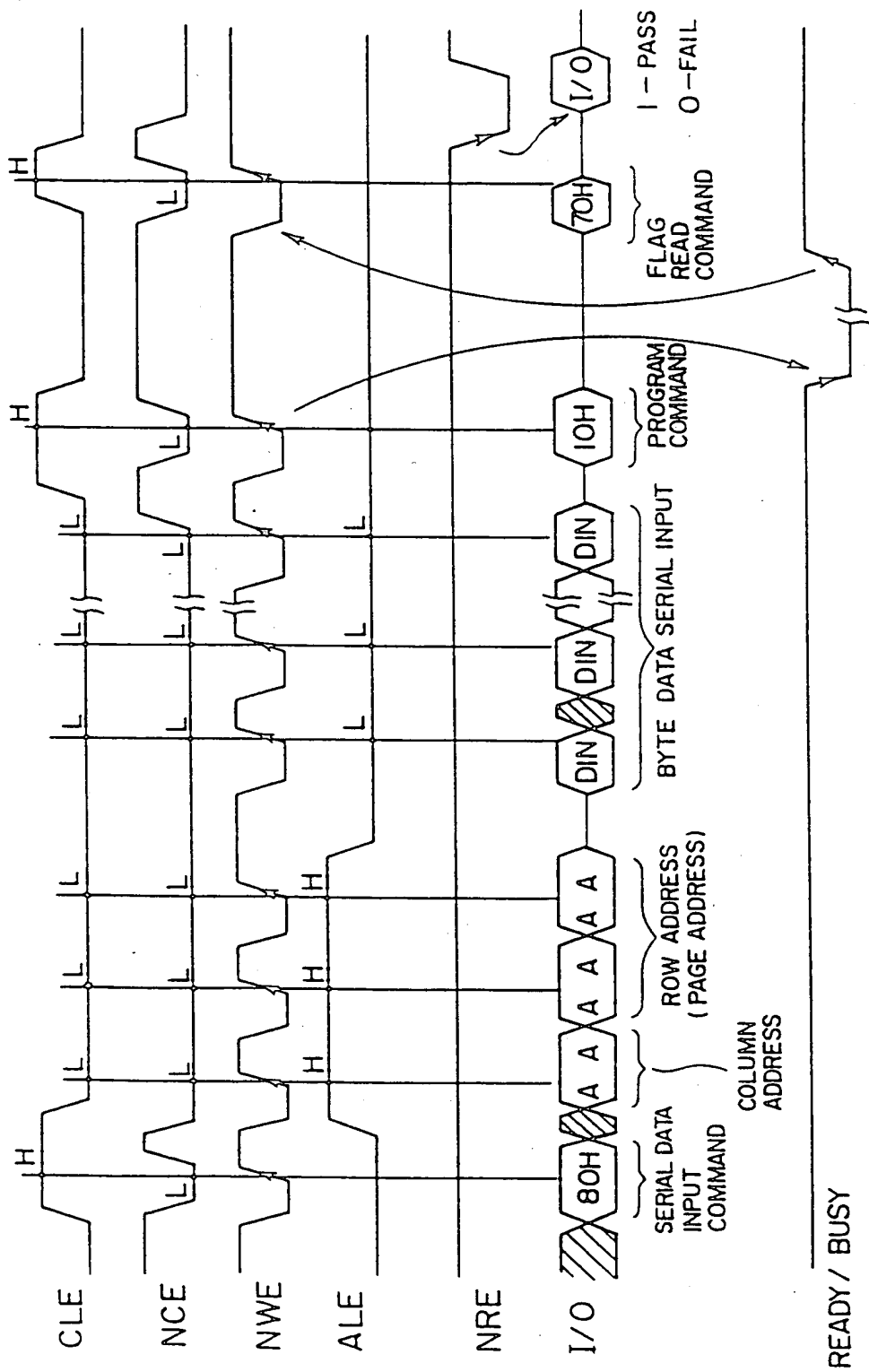


FIG. 88

FIG. 89

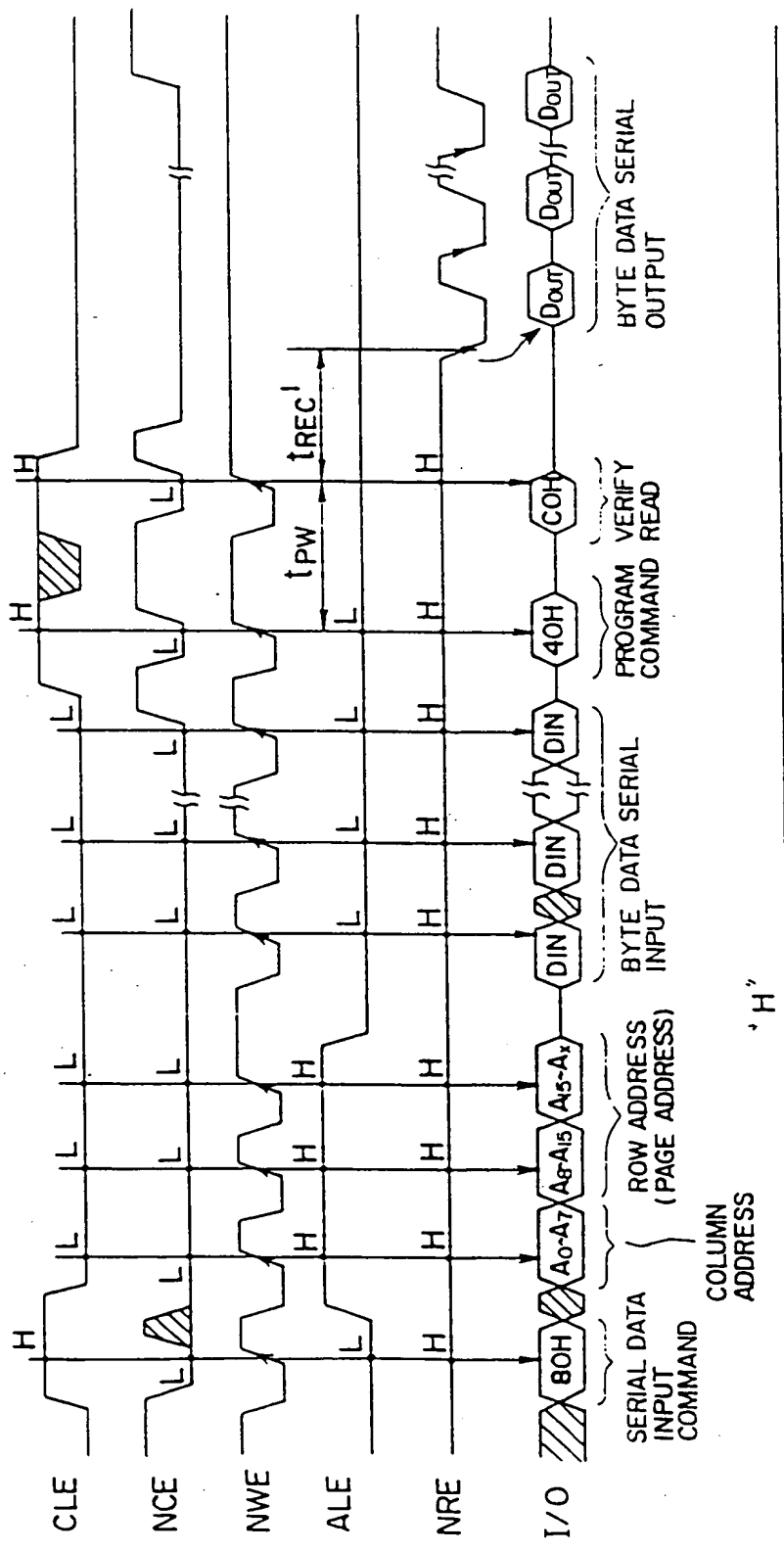
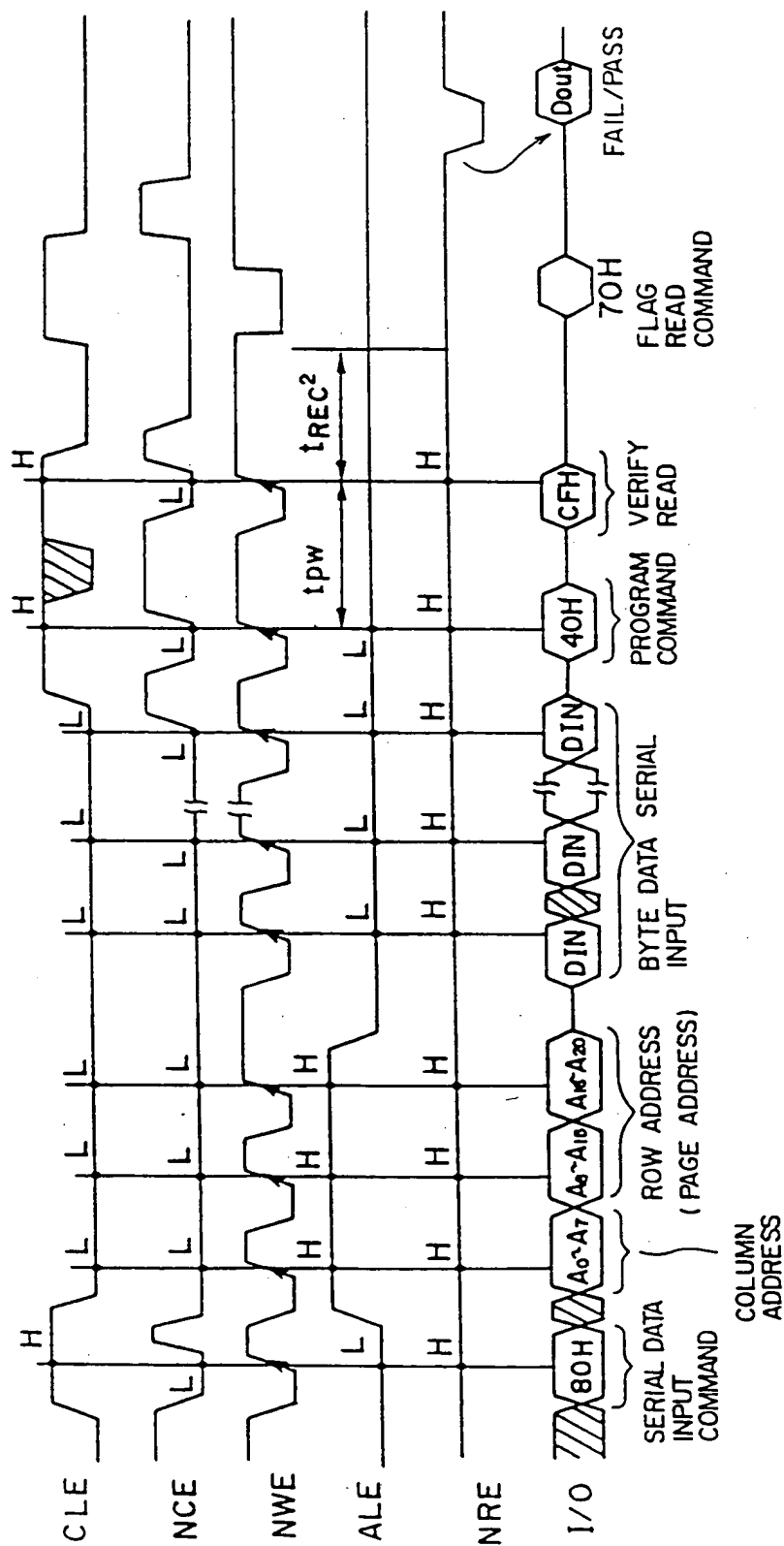


FIG. 89



·H·

READY / BUSY

FIG. 91

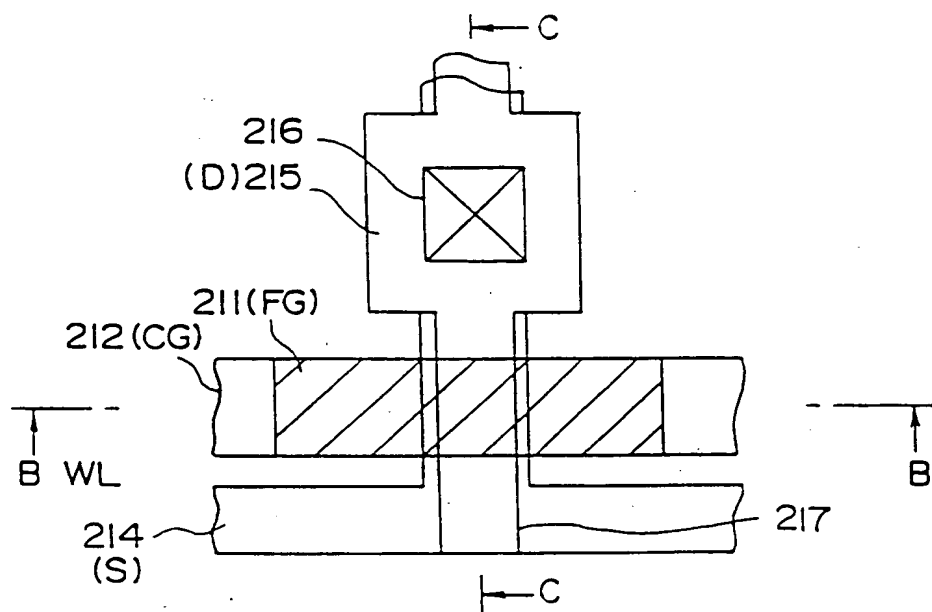


FIG. 92

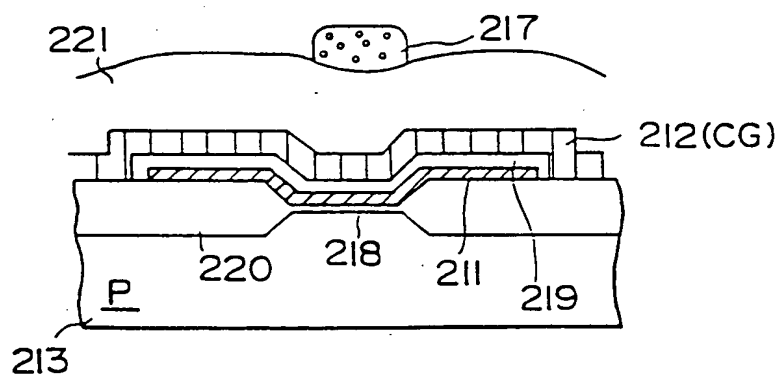


FIG. 93

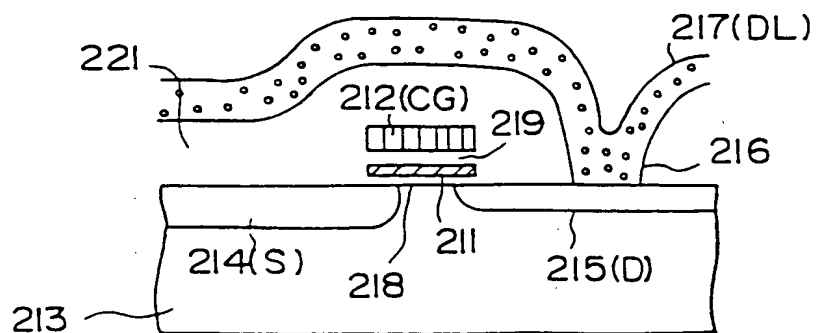


FIG. 94

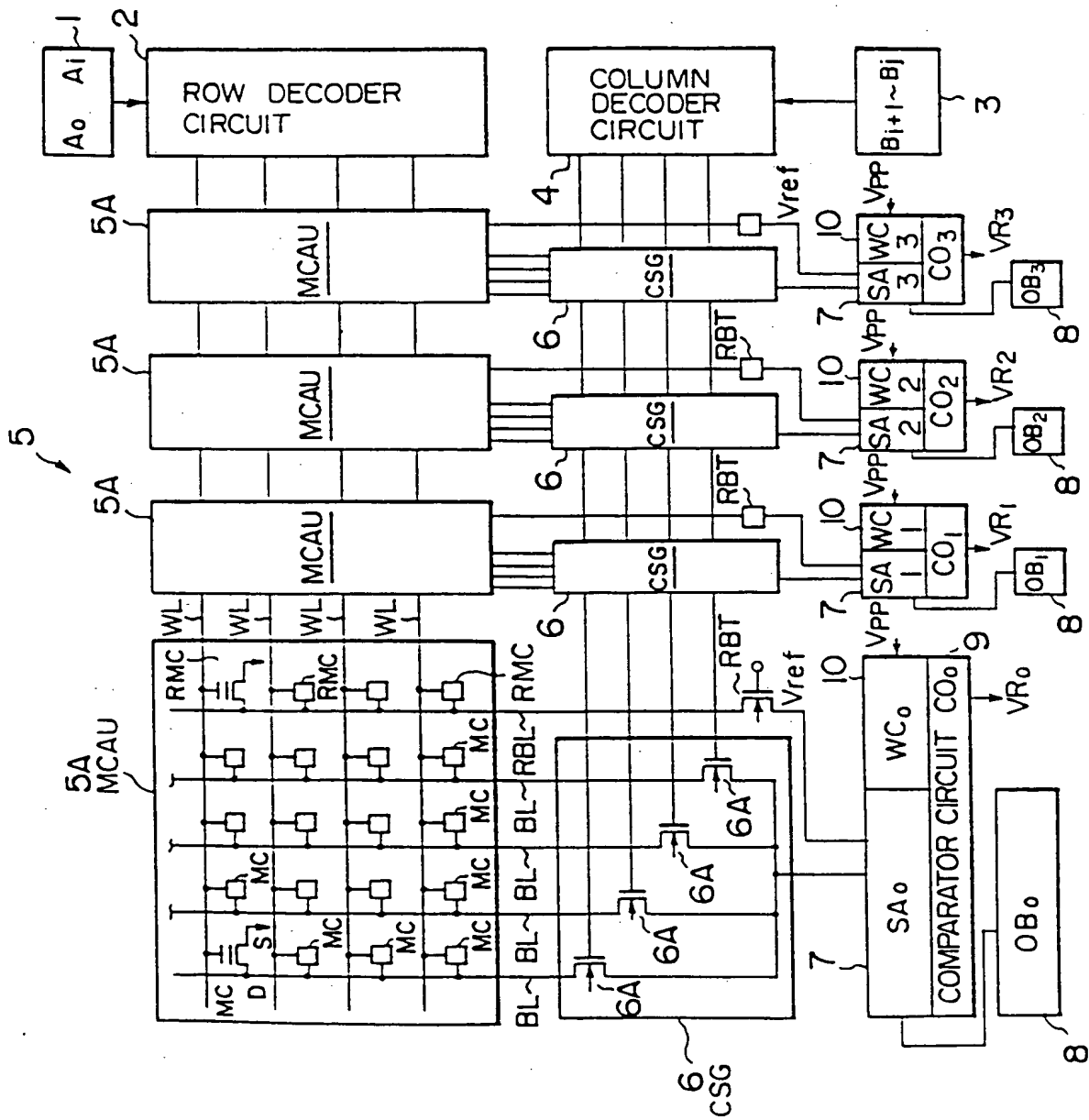


FIG. 95

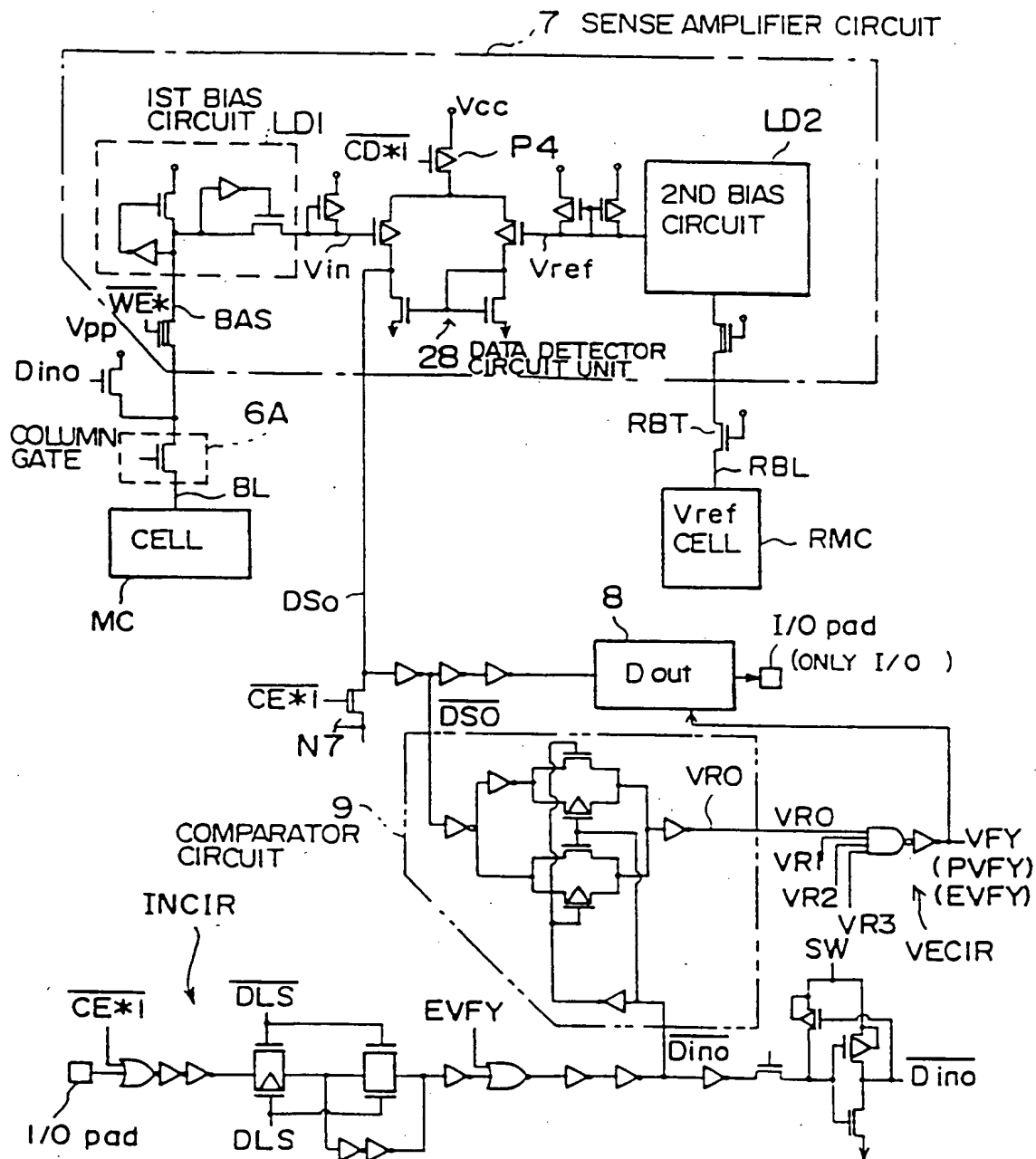


FIG. 96

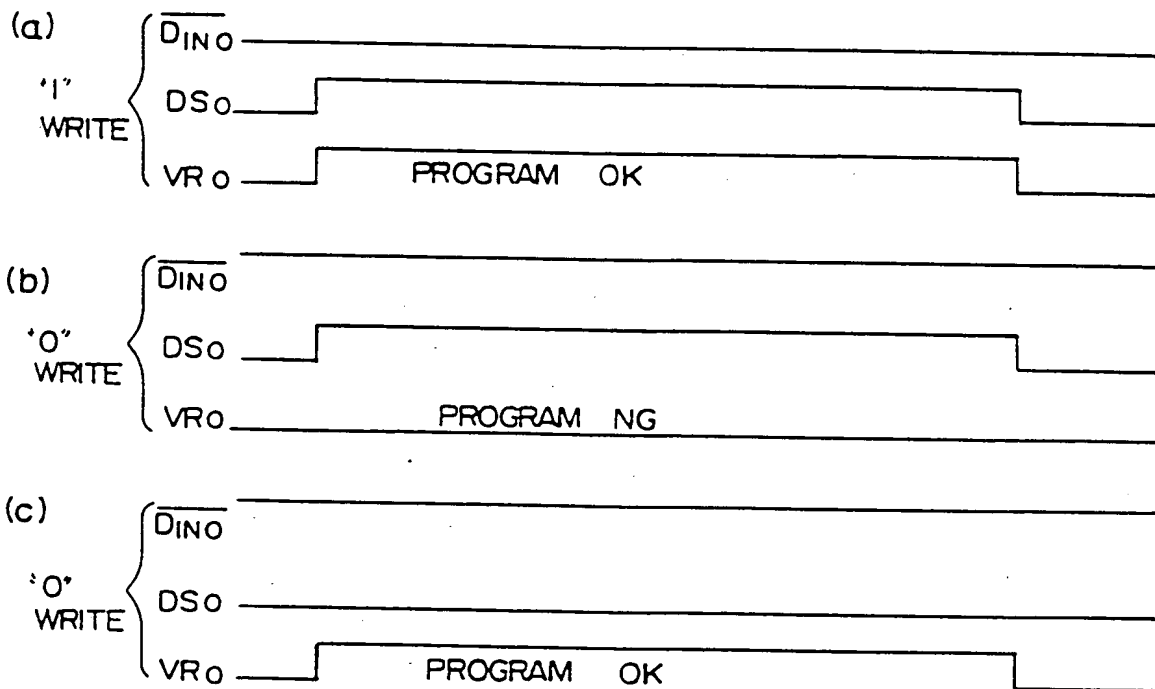


FIG. 97

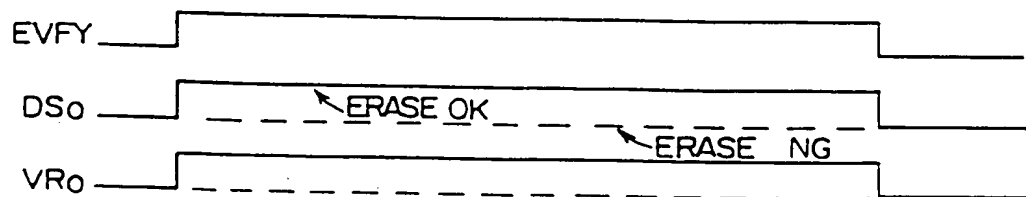


FIG. 98

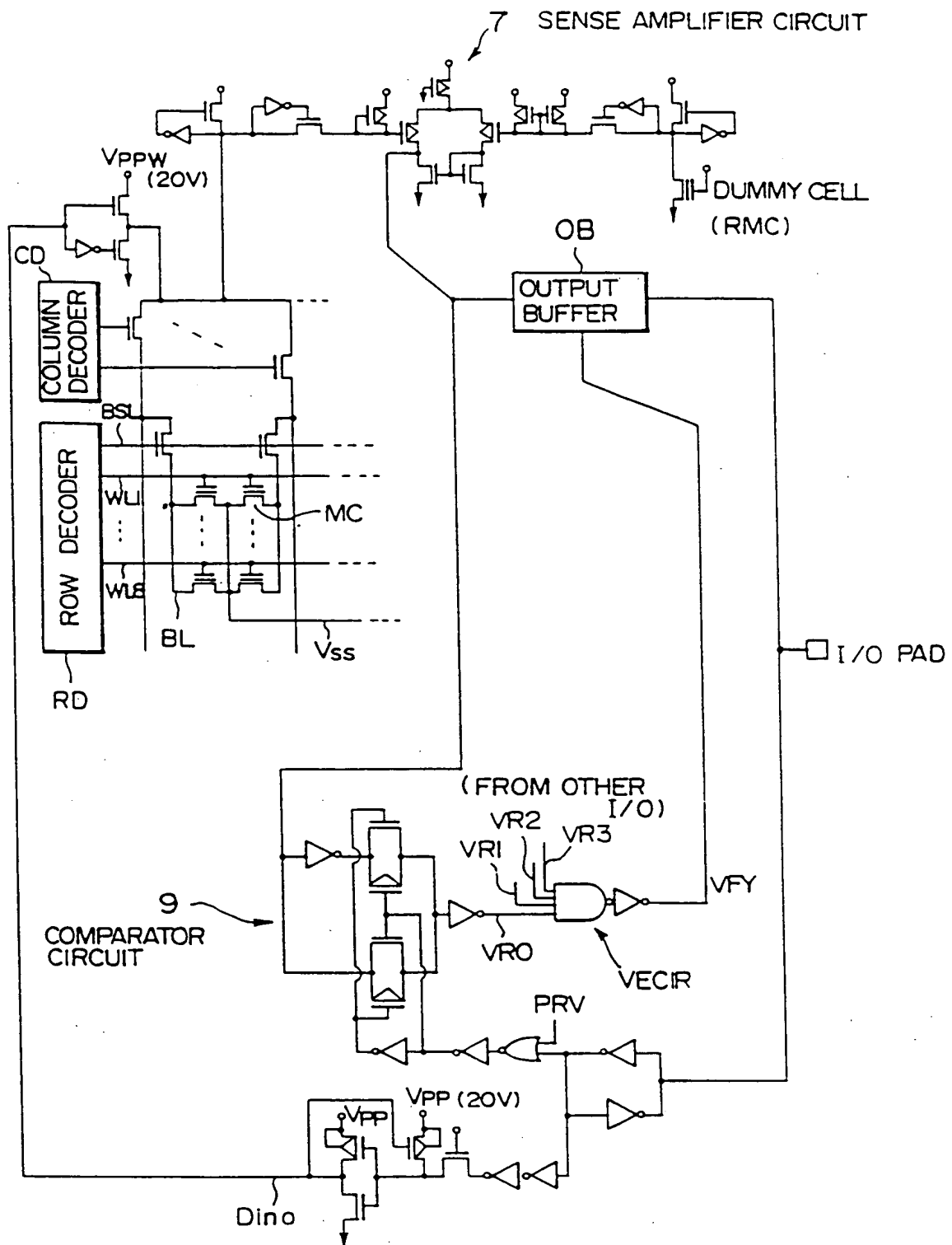


FIG. 99

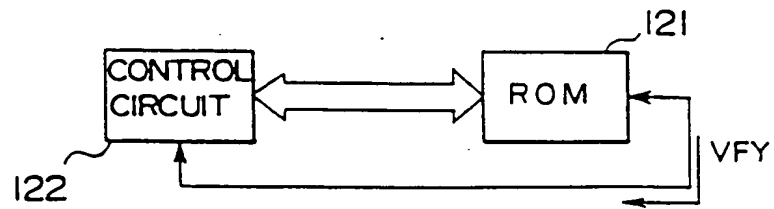


FIG.100

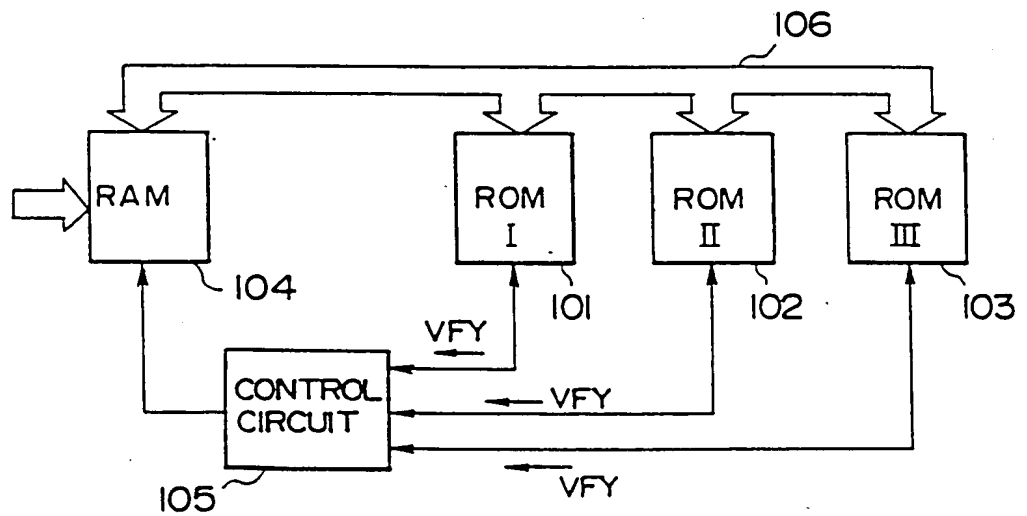


FIG.101

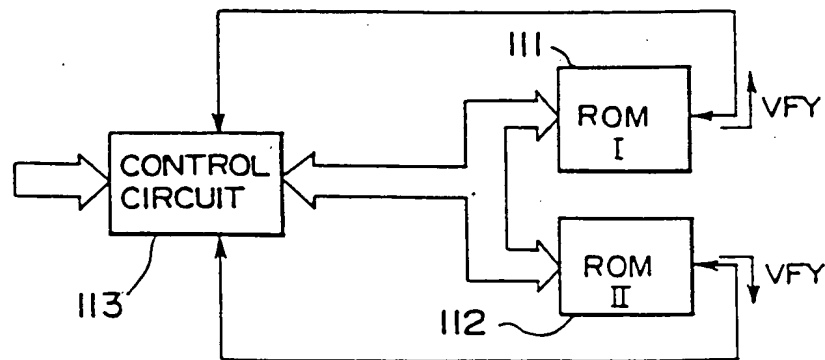


FIG.102

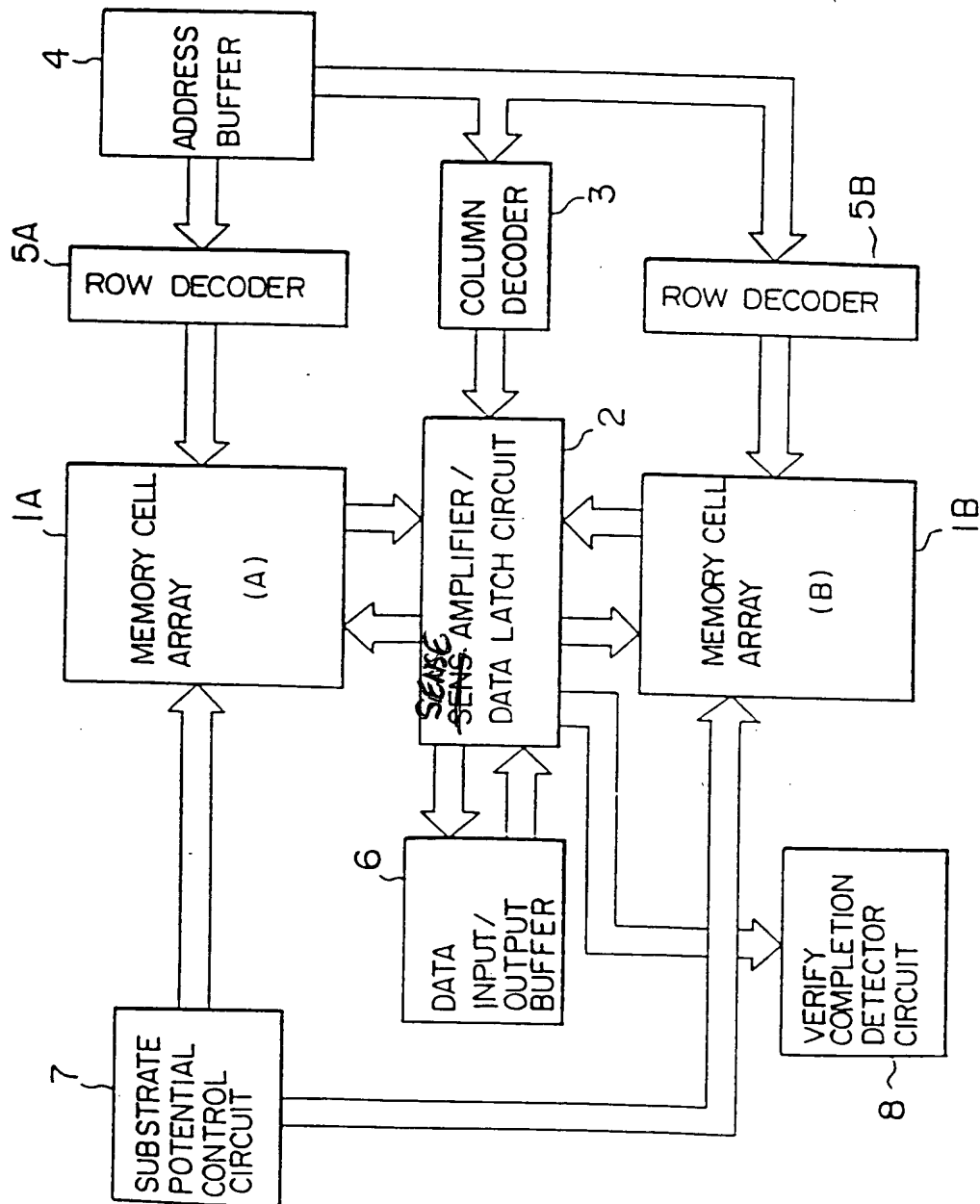


FIG. 53